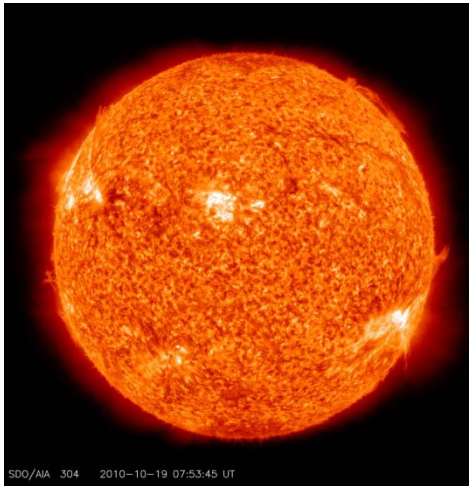


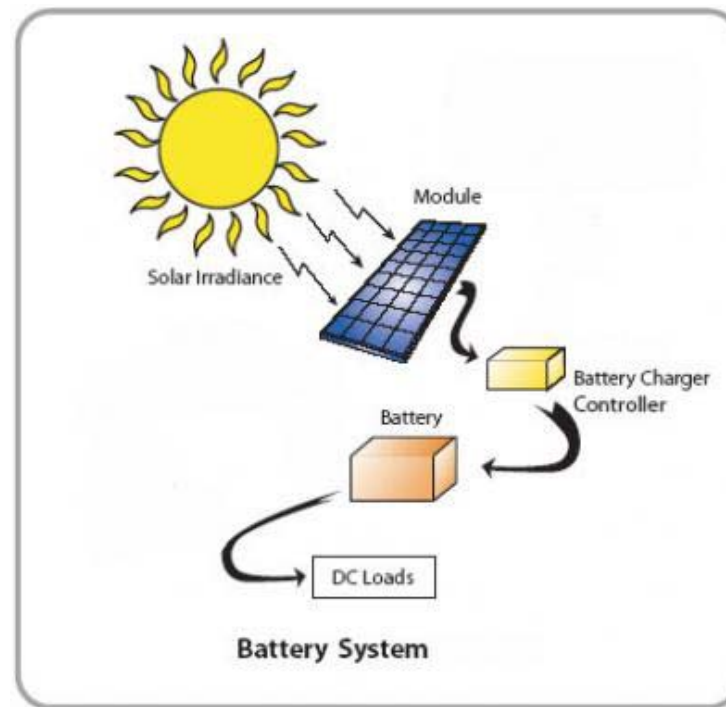
Photovoltaic and Nano



Outline

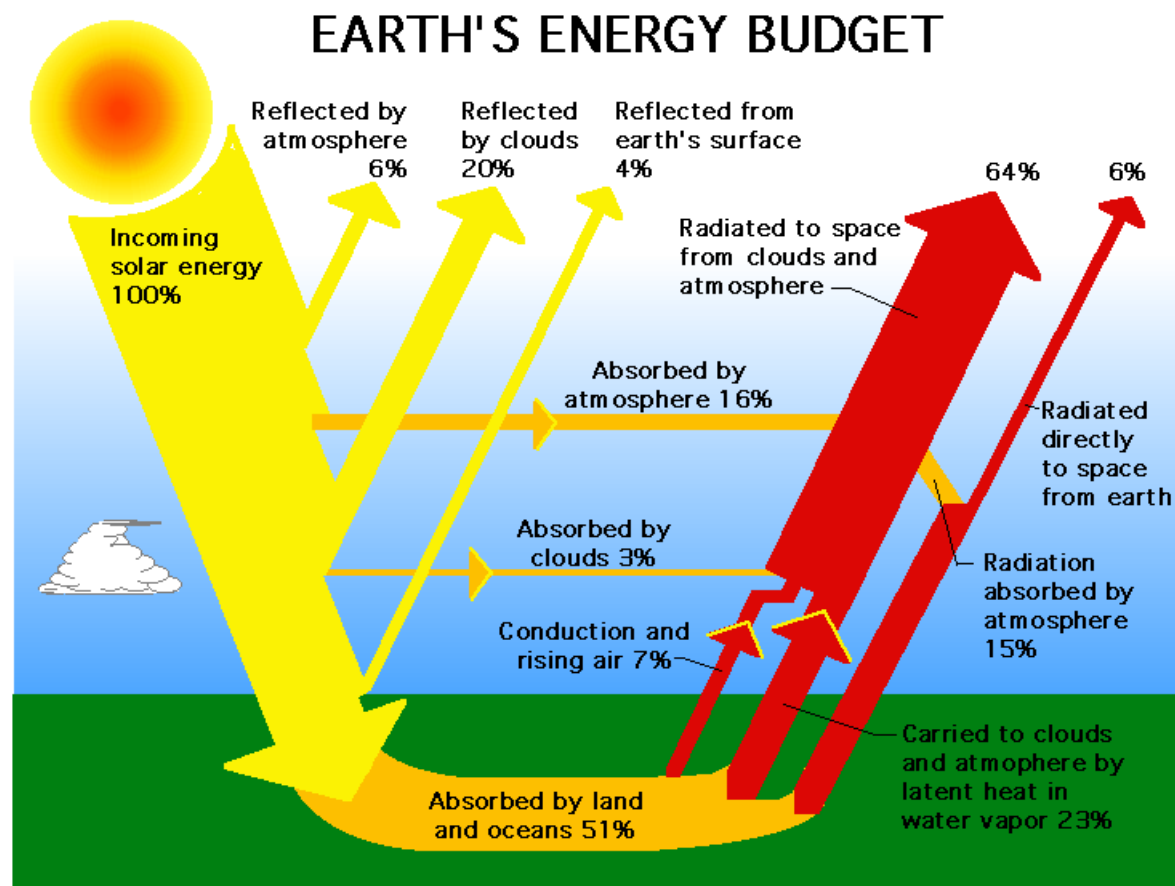
- **Introduction**
 - What is solar energy
 - Evolution of solar cells
 - Solar cell development
 - Principle & analysis
- **Si solar cell**
- **CIGS/CZTS solar cell**
- **Organic solar cell**
 - Small-molecule solar cell
 - BHJ solar cell
- **Why “nano” can help in solar cell**

What Is Solar Energy?



Solar Energy

The radiant solar Energy is from nuclear energy and the temperature of the Sun is $\sim 6000\text{K}$

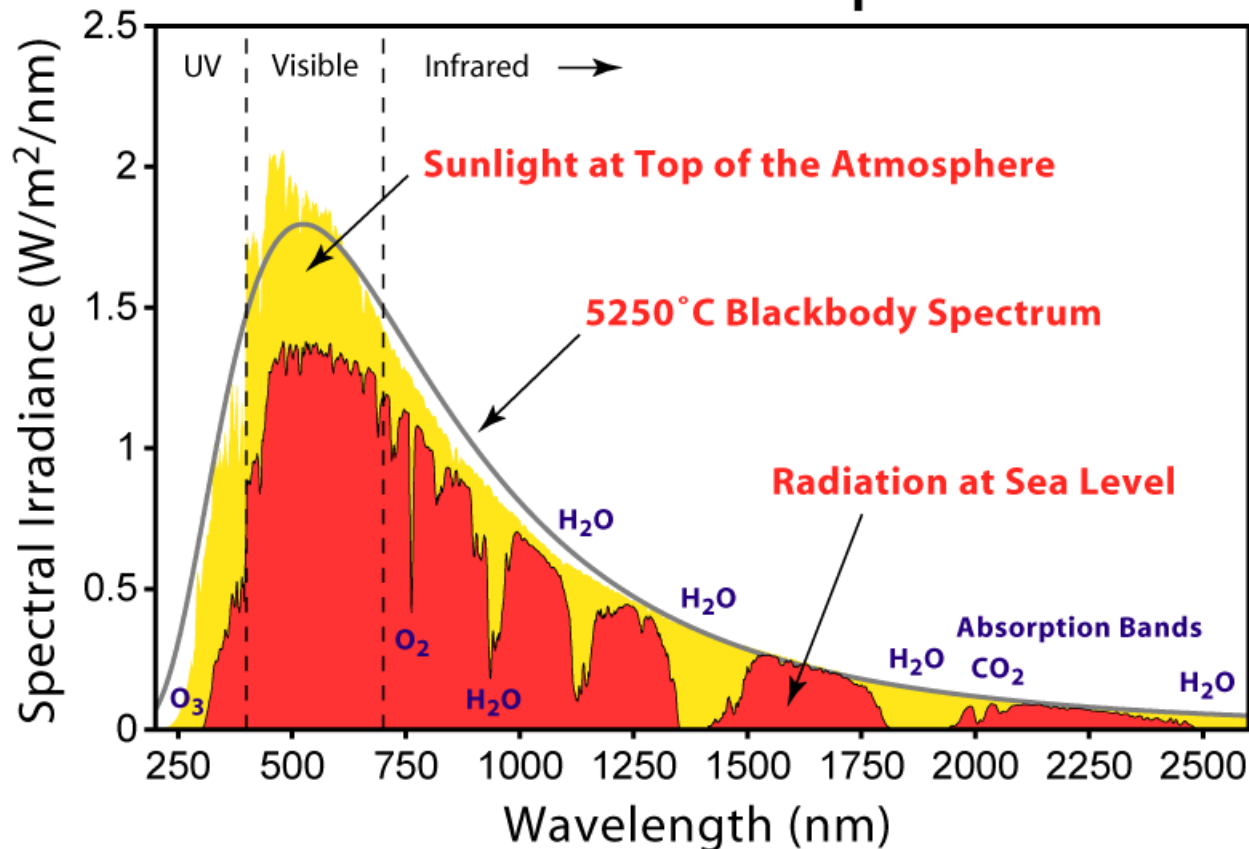


Source: NASA

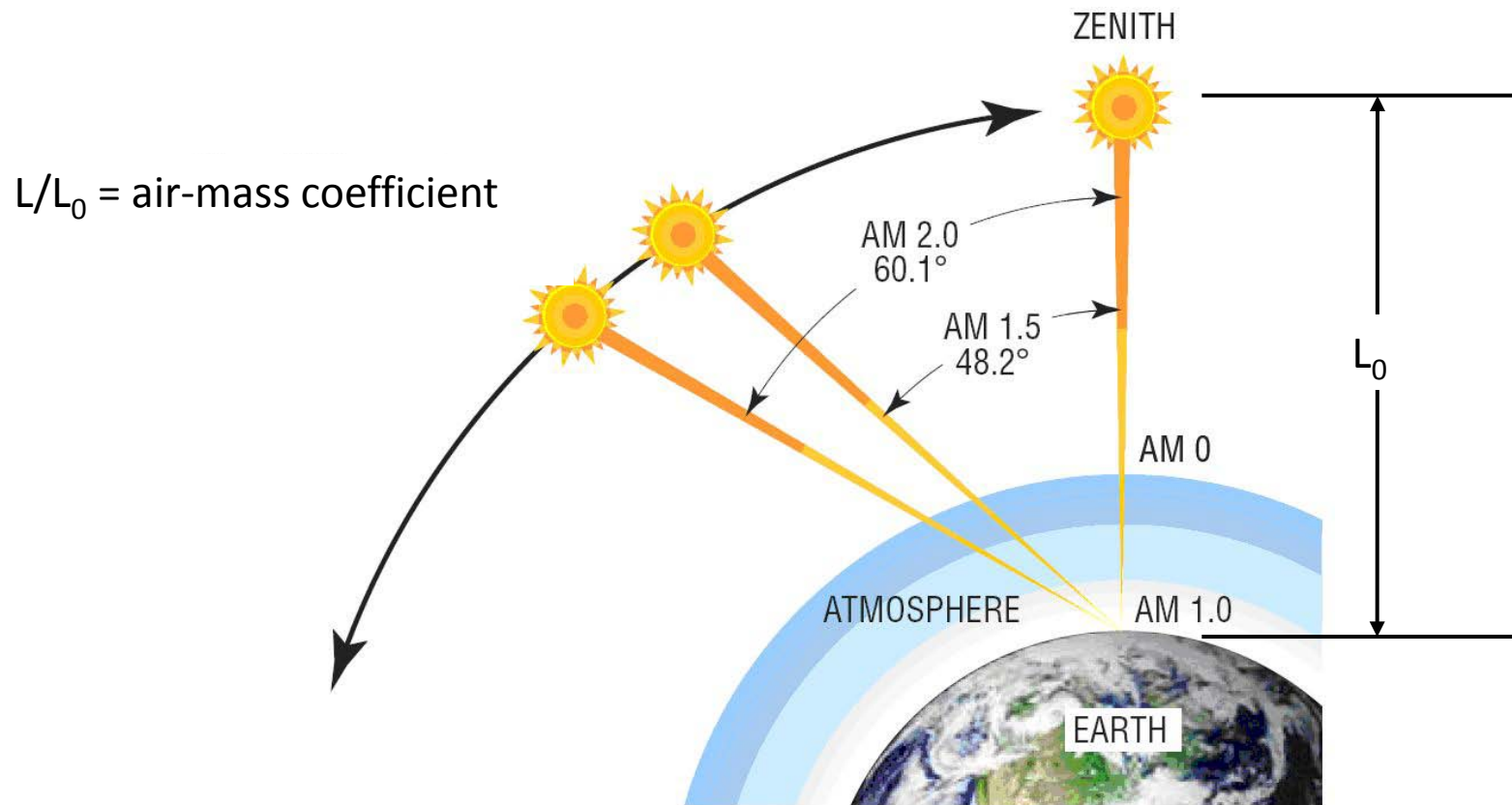
Solar Radiation

① UV (<400 nm) ② Visible (400-800 nm) ③ Infrared (>800 nm)

Solar Radiation Spectrum



Air Mass



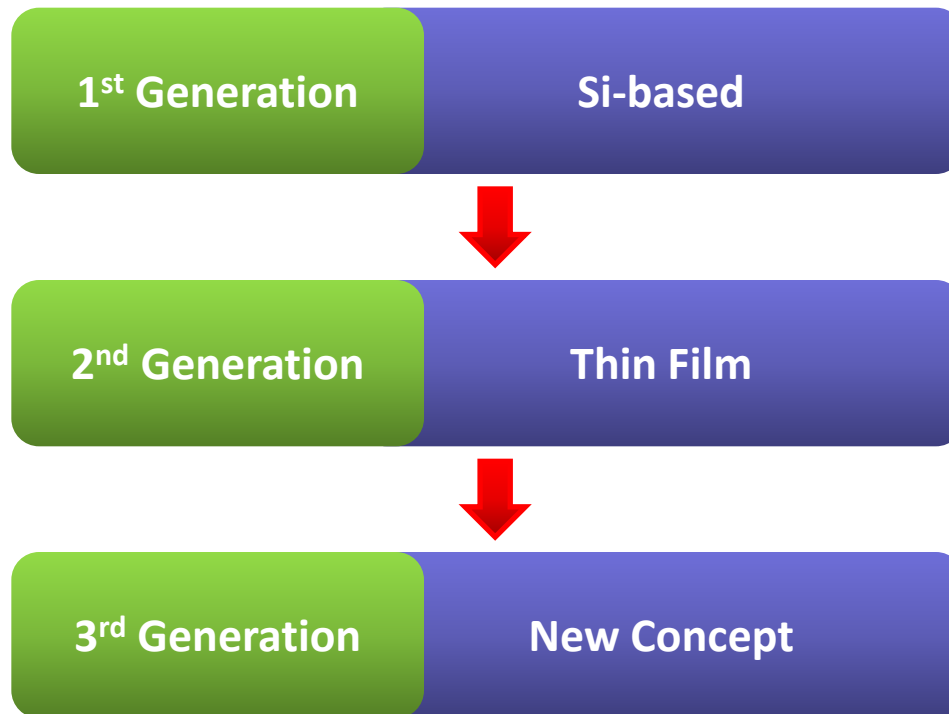
Source: Newport company

The energy spectrum AM 1.5 ➡ standard spectrum for measuring the efficiency of solar cells

Applications



Evolution of Solar Cells

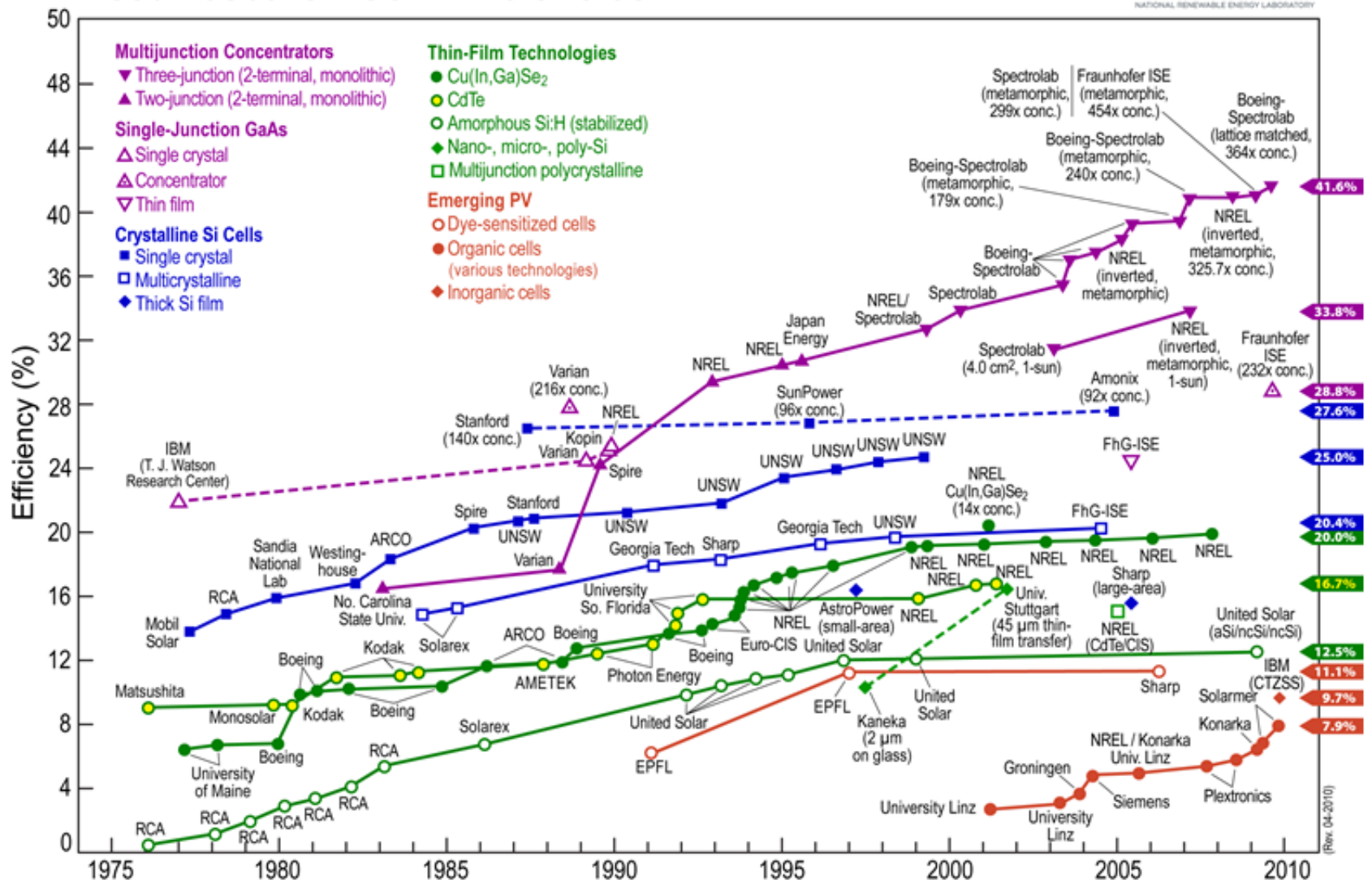


Categories & Efficiency

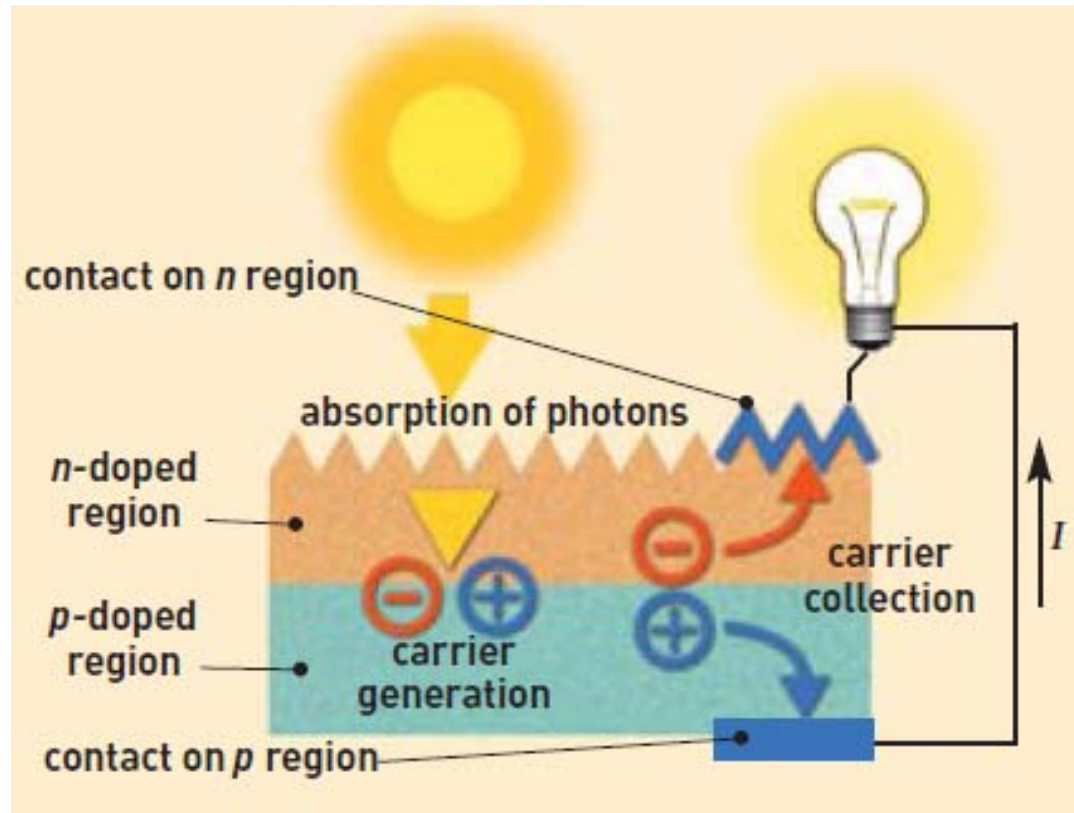
Categories of solar cells			Efficiency
Si-based	Crystalline	Single crystalline	12-20%
		Poly crystalline	10-18%
	Amorphous	Si, SiGe, SiC	6-9%
Thin Film	Single crystalline	GaAs, InP	18-30%
	Poly crystalline	CdS, CdTe, Cu(In, Ga)Se ₂	10-20%
New Concept	Nano & Organic	P3HT:PCBM, CuPC/C60, ZnO, TiO ₂	≤7%

Solar Cells Developments

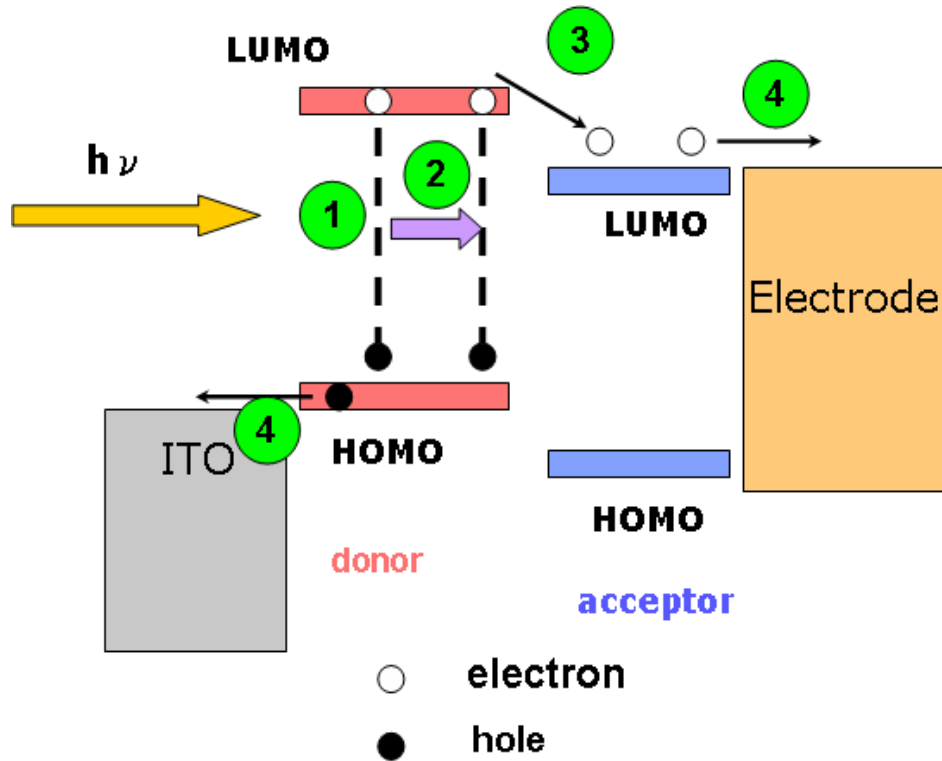
Best Research-Cell Efficiencies



How Does a Photovoltaic Solar Cell Work?



Basic Principle of Photovoltaic Device



η_A : absorption efficiency

η_{ED} : exciton diffusion efficiency

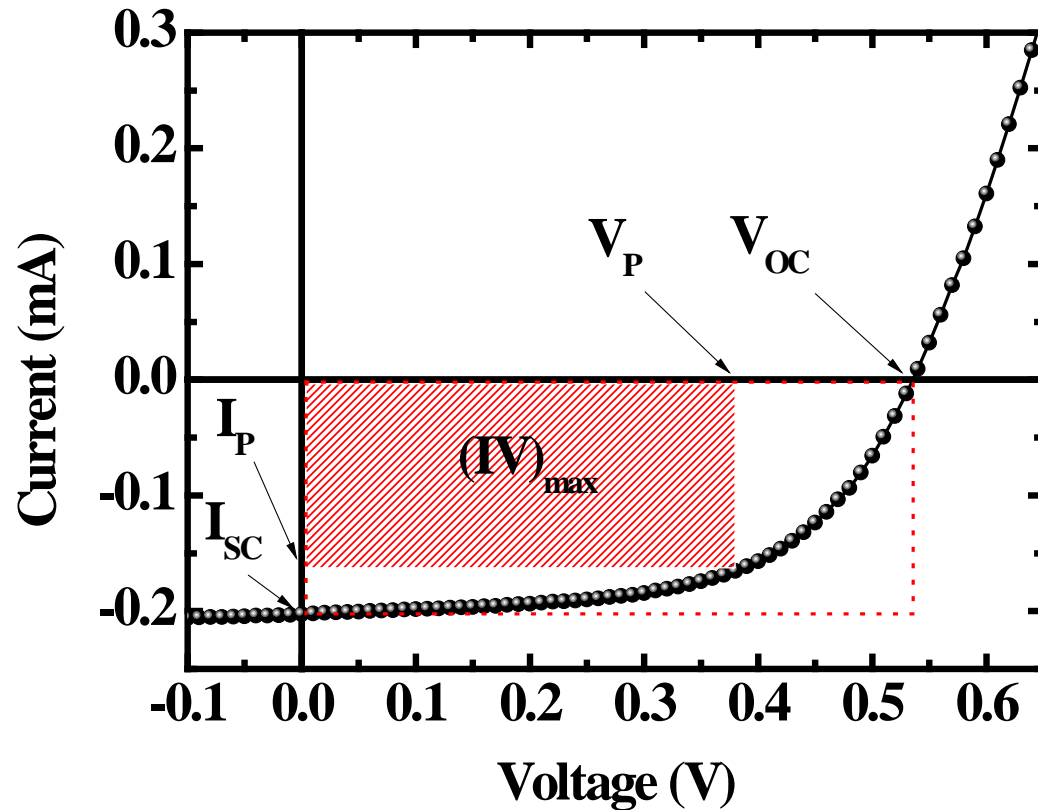
η_{CT} : charge transfer efficiency

η_{CC} : carrier collection efficiency

External Quantum Efficiency(EQE): $\eta_{ext} = \eta_A \times \eta_{ED} \times \eta_{CT} \times \eta_{CC}$

- ① Absorption of a photon leading to the formation of an excited state, the electron-hole pair (exciton).
- ② Exciton diffusion to a region (organic/organic interface or organic/metal interface).
- ③ The charge separation occurs.
- ④ Charge transport to the anode (hole) and the cathode (electron), to supply a direct current for the consumer load.

Basic Principle of Photovoltaic Device

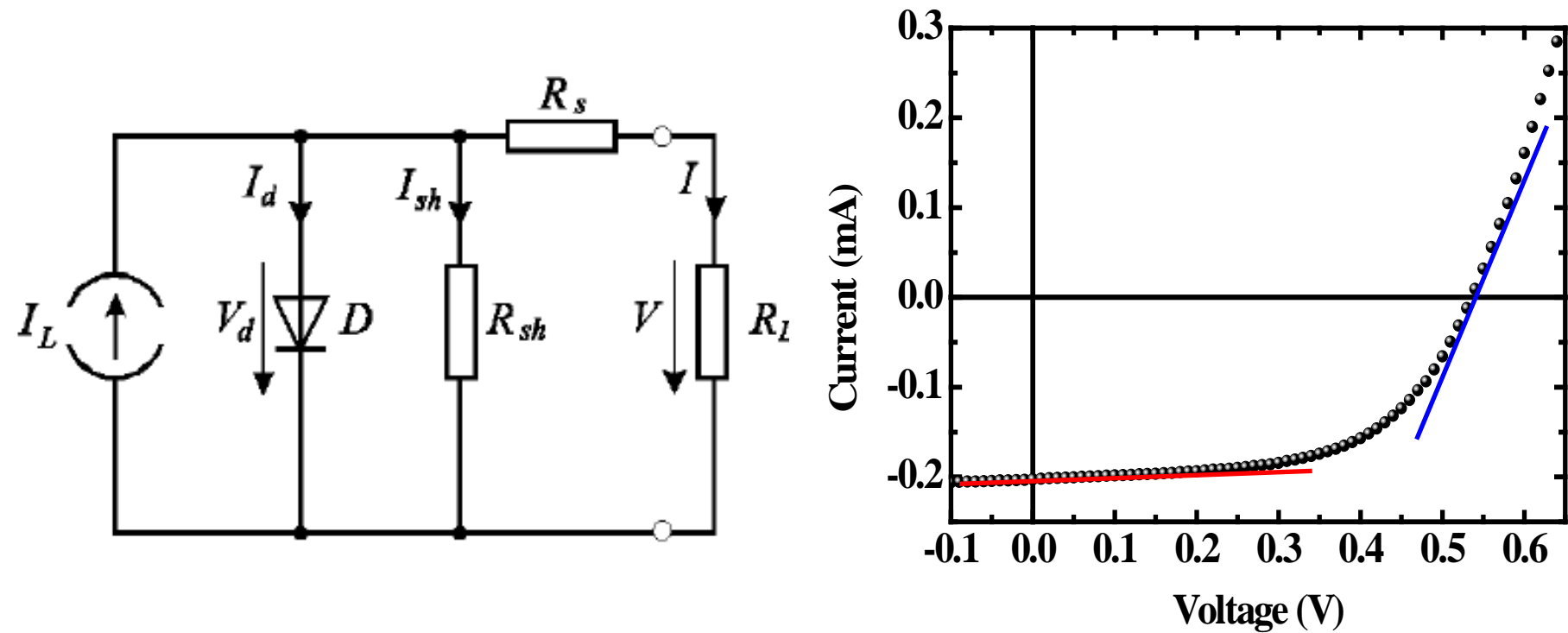


$$FF \equiv \frac{(IV)_{\max}}{I_{\text{SC}} V_{\text{OC}}}$$

$$P_{\max} = (IV)_{\max} = V_{\text{OC}} \cdot I_{\text{SC}} \cdot FF$$

$$\eta(\lambda) \equiv \frac{I_{\text{SC}}(\lambda) \cdot V_{\text{OC}}(\lambda) \cdot FF(\lambda)}{P_{\text{light}}}$$

Basic Principle of Photovoltaic Device



R_s (series resistance): mobility of the specific charge carriers in the respective transport medium

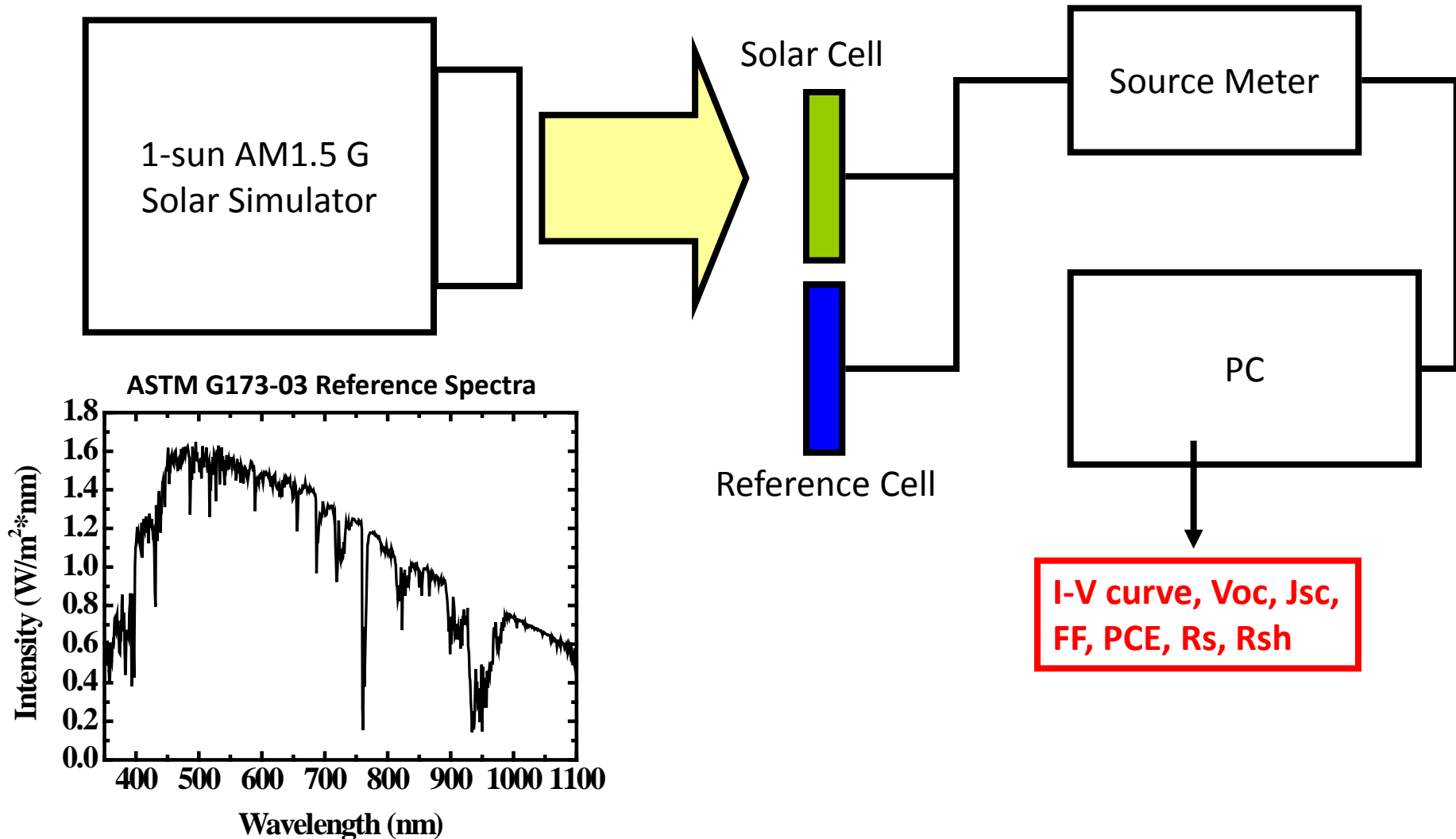
R_{sh} (shunt resistance): recombination of charge carriers near the interface

Analytical Technique

- Measurement of power conversion efficiency (PCE)
 - J-V characteristics (V_{oc} , J_{sc} , Fill factor, R_s , R_{sh})
 - Incident Photo Conversion Efficiency
- Time of flight measurement
- Conductive Atomic Force Microscopy
- Time-resolved Photoluminescence
- Transmission Electron Microscopy

Analytical Technique

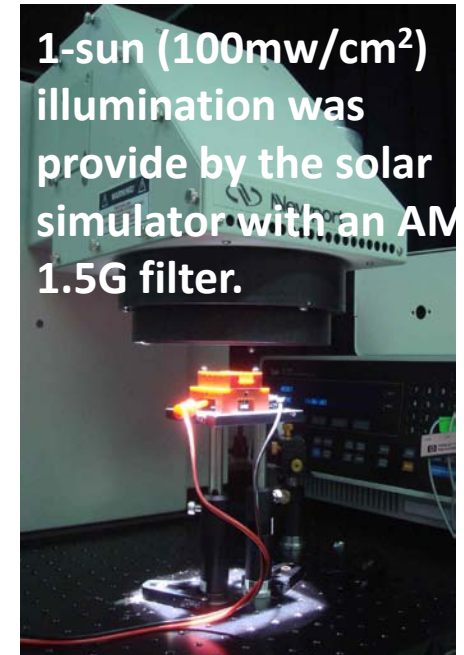
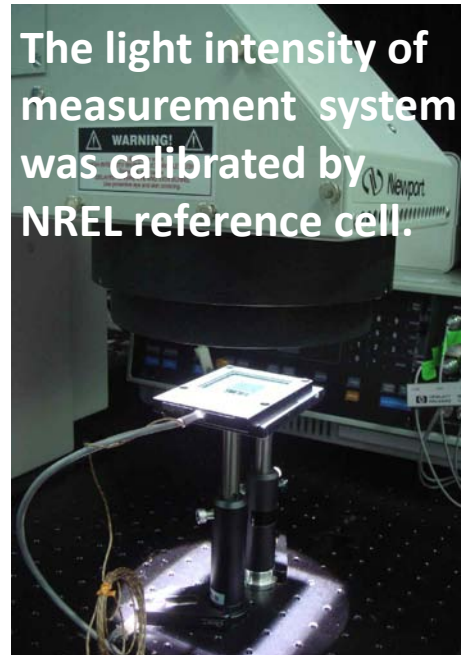
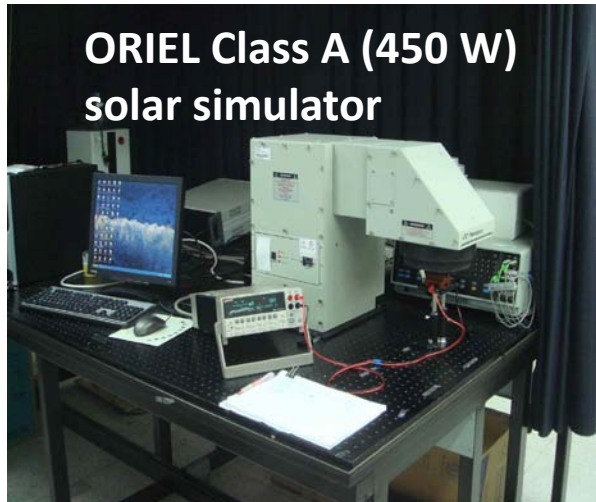
Measurement of power conversion efficiency (PCE)



Analytical Technique

Measurement of power conversion efficiency (PCE)

- *Standard J-V measurement system*



Device was illuminated under AM 1.5G, 1-sun illumination, which was provide by an Oriel class A solar simulator.

(Si-testing cell: active area of $10 \times 10 \text{ cm}^2 < 1 \%$ error)

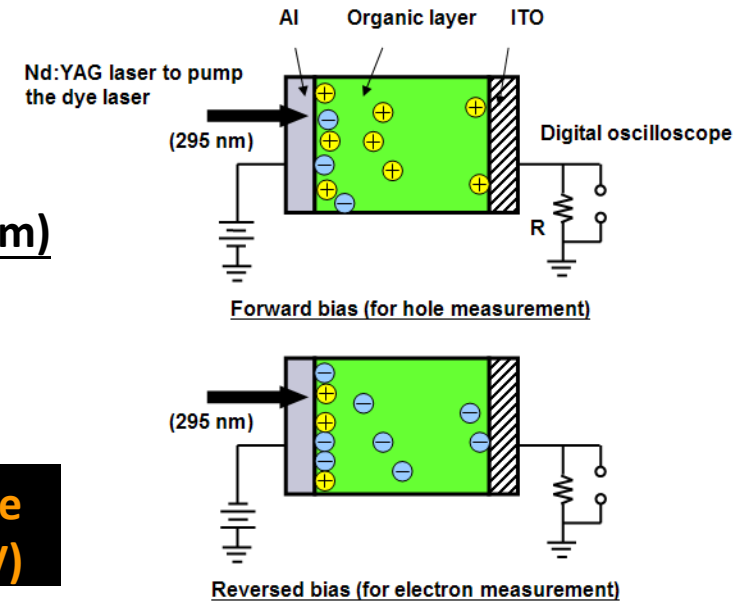
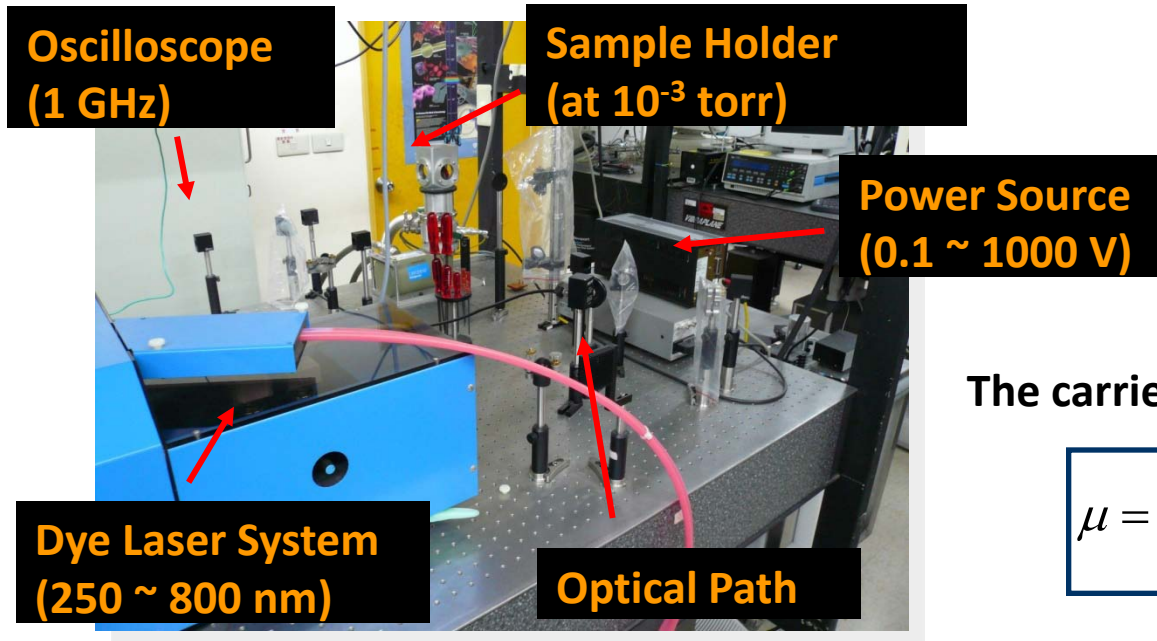
Analytical Technique

Measurement of carrier mobility

- Time-of-Flight (TOF) Measurement**

The sample of TOF is a single layer device with a semi-transparent metal electrode

ITO (100 nm) / Organic material (~ 1 μm) / Al (10 nm)



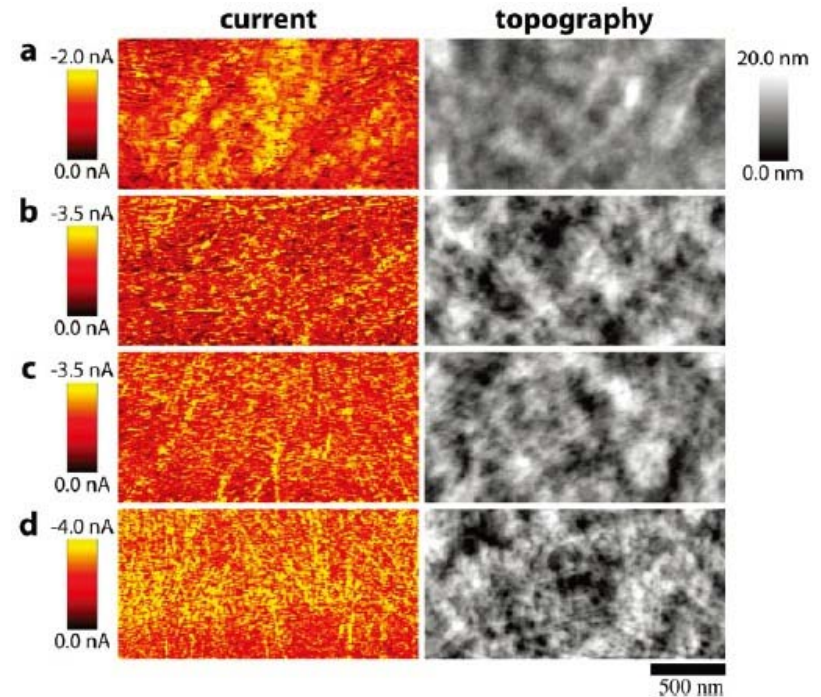
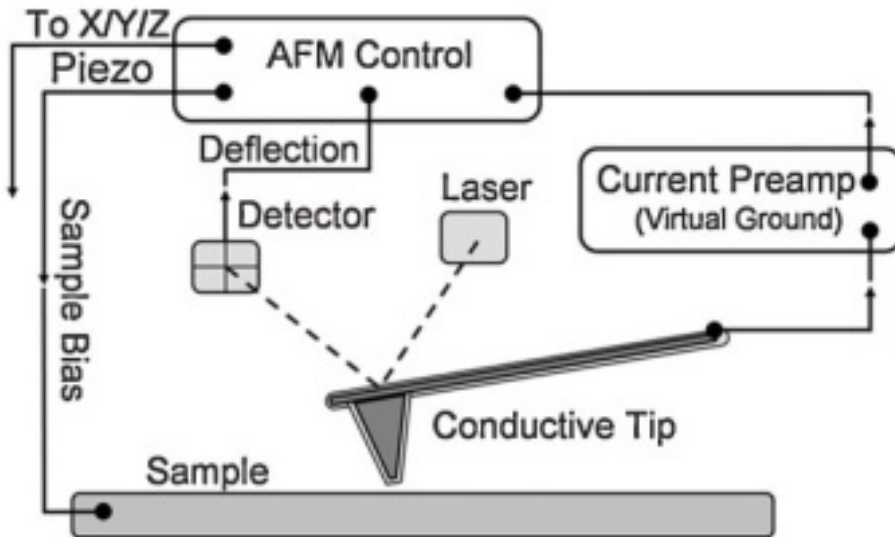
The carrier mobility (μ) is given by

$$\mu = \frac{D}{t_T E}$$

Where D is the thickness of organic layer, t_T is the transit time, and E is the applied electric field.

Analytical Technique

Conductive Atomic Force Microscopy

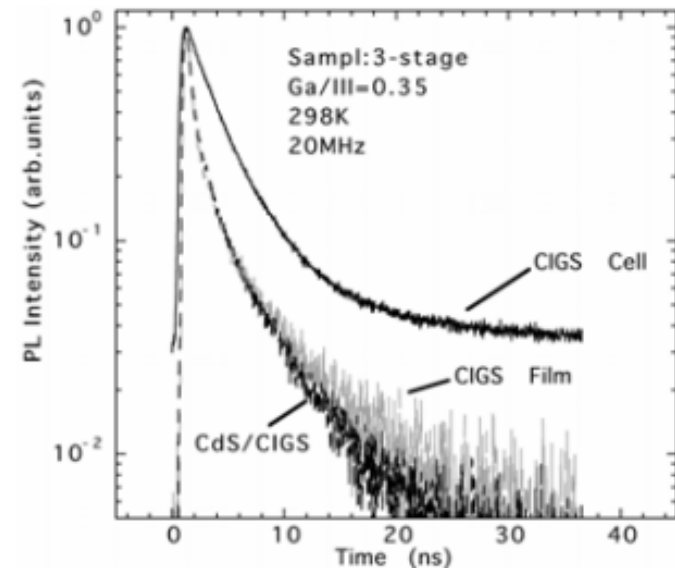
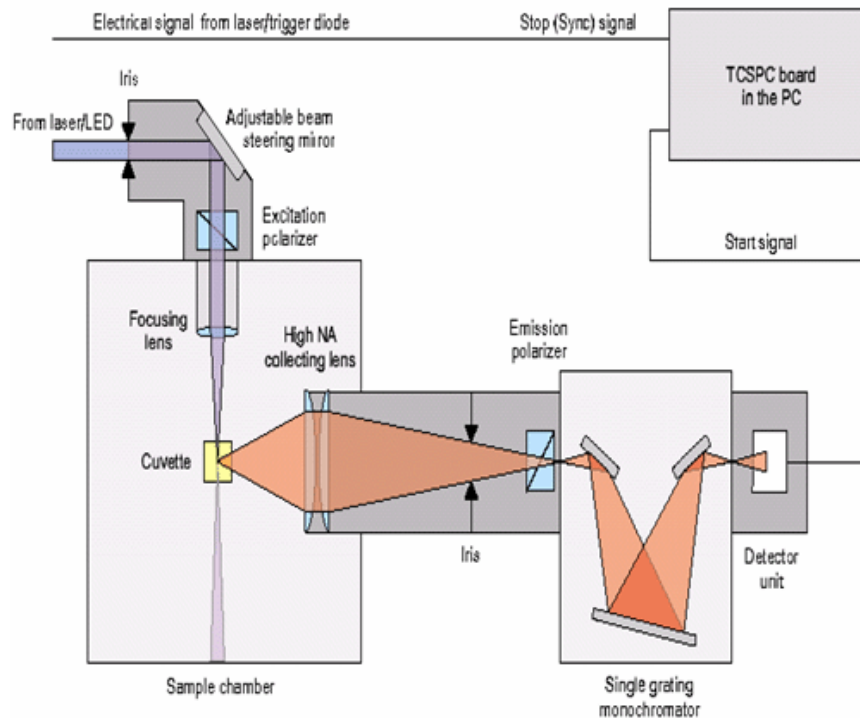


Conductive AFM images of pure P3BT-nw films

- Localized area analysis
- Bias voltage is applied between the conductive tip and the surface.
- The current flowing through the tip is detected with a current preamplifier and recorded as a function of position.

Analytical Technique

Time-resolved Photoluminescence



Typical PL decay curves of NBE-PL of CIGS thin film, CdS/CIGS and CIGS solar cell.

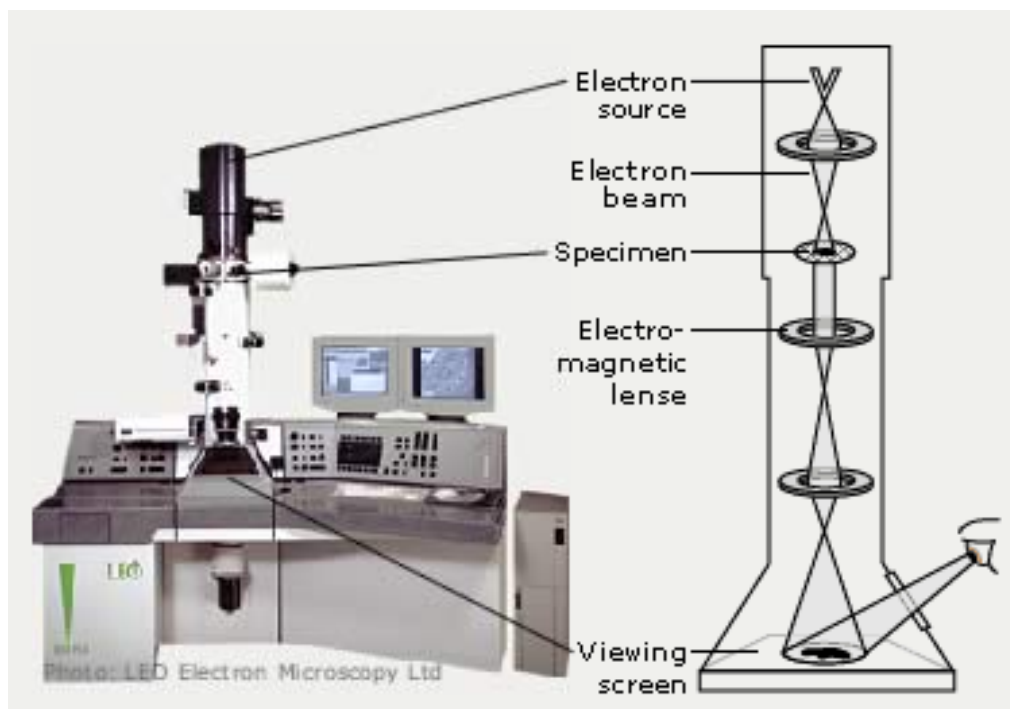
S. Shirakata *et al.*, *physica status solidi (c)* **6**, 1059 (2009).

TRPL is measured by exciting luminescence from a sample with a pulsed light source, and then measuring the subsequent decay in photoluminescence (PL) as a function of time.

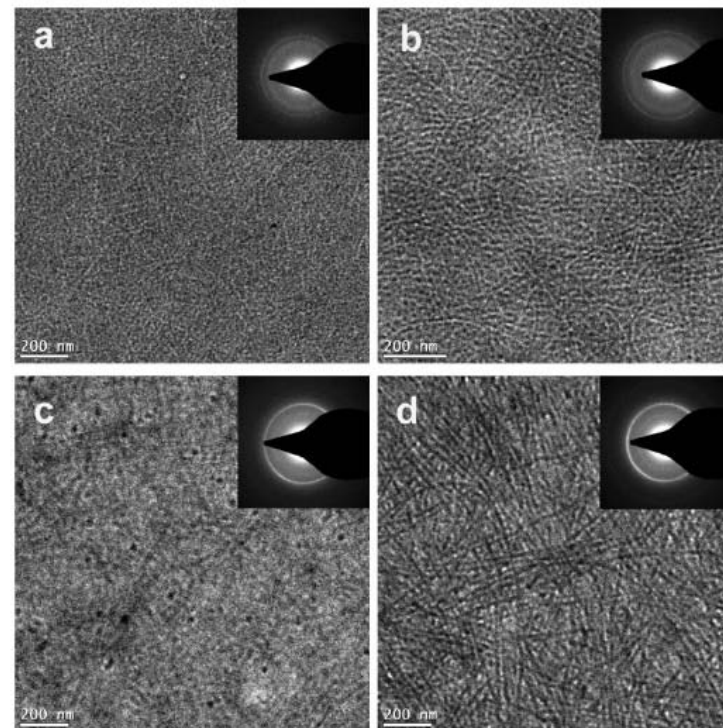
➡ To measure the carrier lifetime

Analytical Technique

Transmission Electron Microscopy

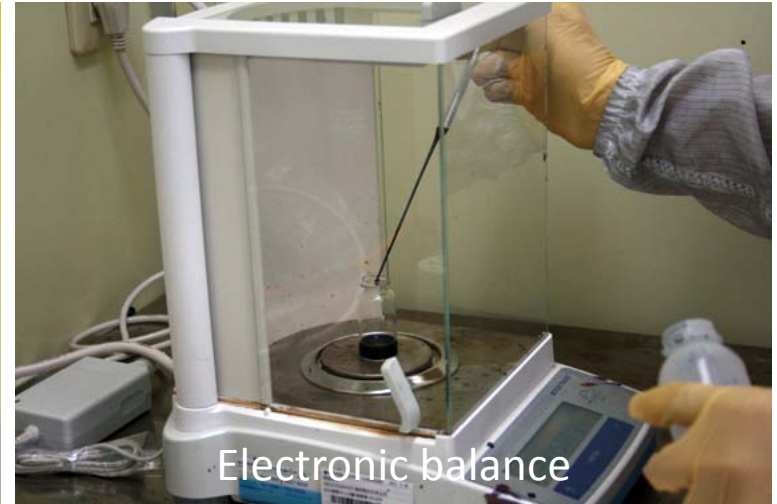
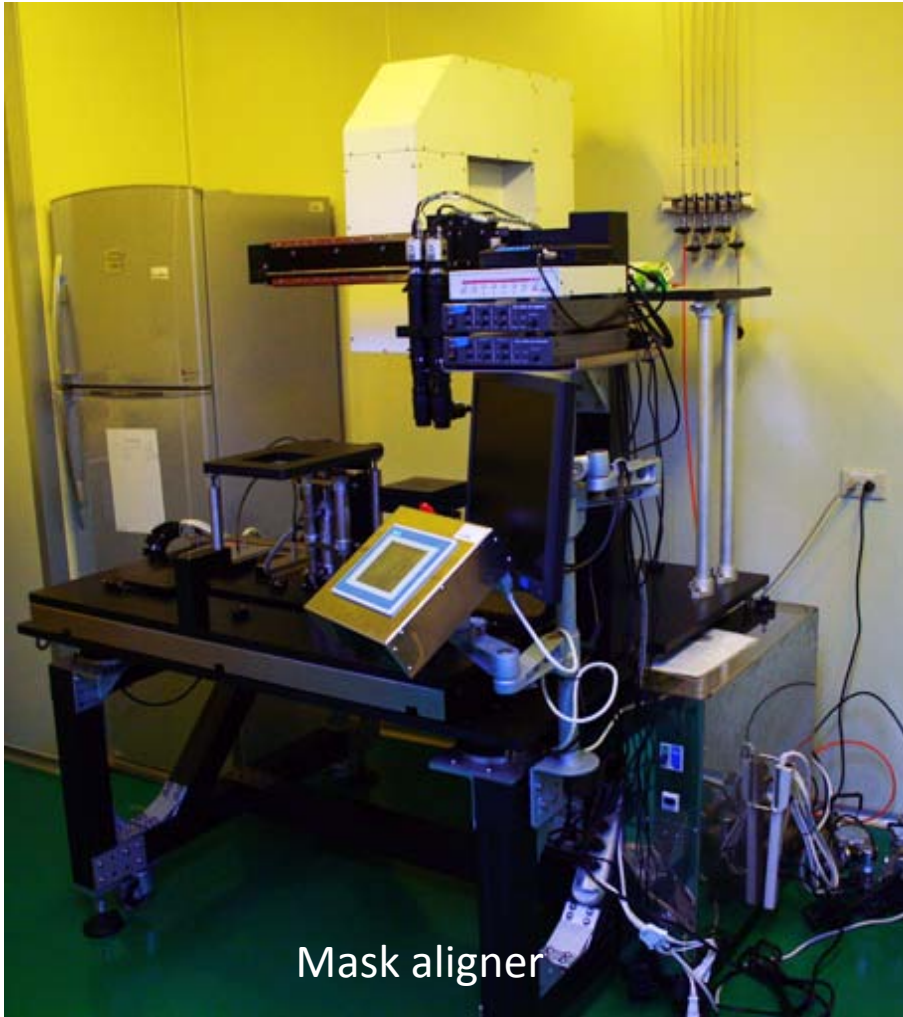


<http://nobelprize.org/educational/physics/microscopes/tem/index.html>



Bright-field TEM images of P3BT-nw/PC71BM (1:1) blend thin films (a,b) and pure P3BT-nw films (c, d) under condition A (a, c) and condition D (b, d). The films were spin-casted on top of ITO/PEDOT substrates and peeled off by putting the samples in water. The insets are the electron diffraction of the corresponding film

Facilities for Device Fabrication



Facilities for Device Fabrication



Si Solar Cells

Wafer-based Si solar cells

- Single crystalline Si solar cell (c-Si)
 - ➡ Highest efficiency, most expensive
- Poly-crystalline Si solar cell
- Ribbon Si solar cell

Thin film Si solar cells

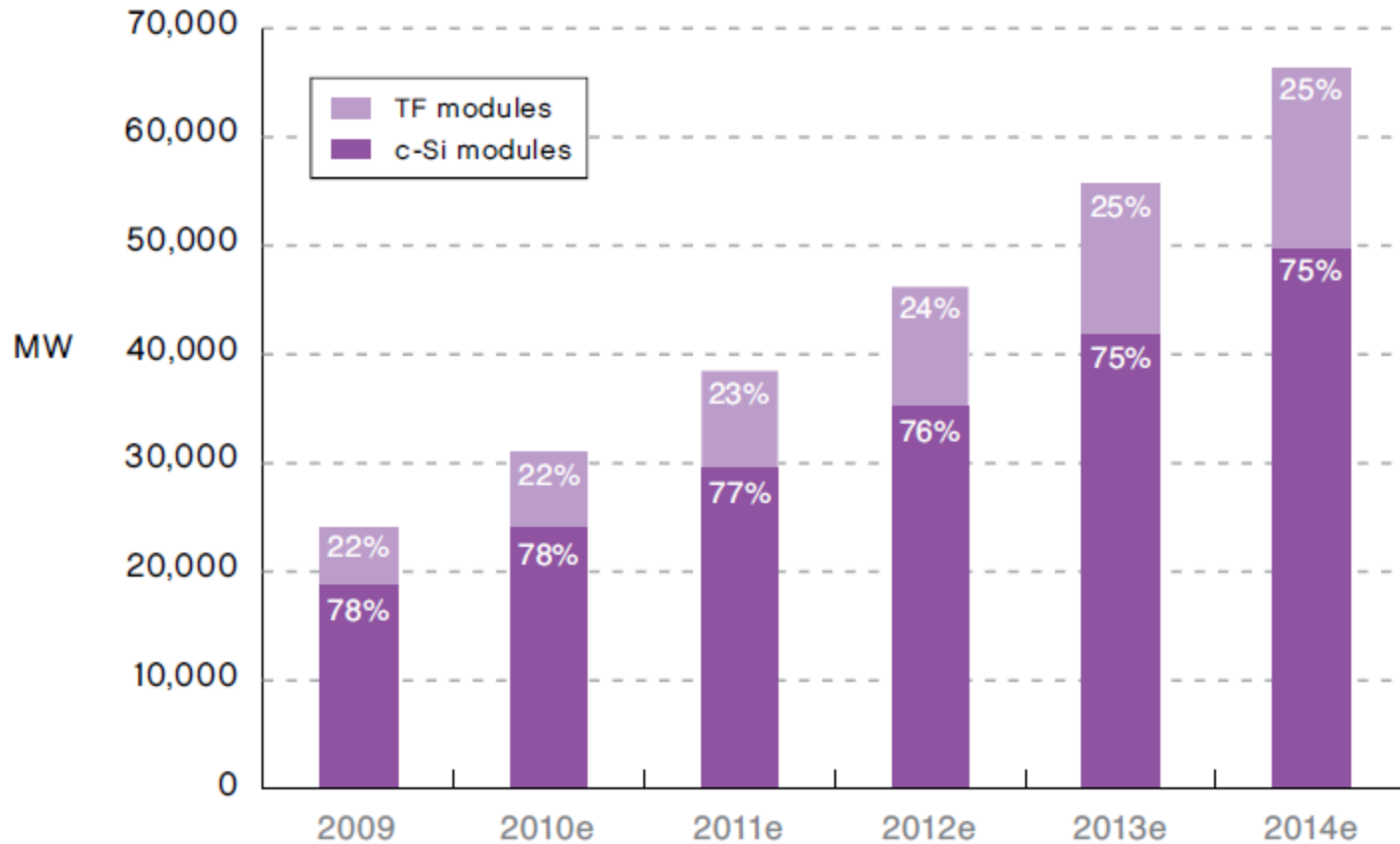
- Amorphous Si solar cell (a-Si)
- macro-crystalline Si solar cell (mc-Si)

◆ Thin-film technologies

Advantage ➡ the amount of material required ↓ ➡ material cost ↓
➡ flexibility, lighter weight, ease of integration.

Disadvantage ➡ energy conversion efficiency ↓

Technology Development

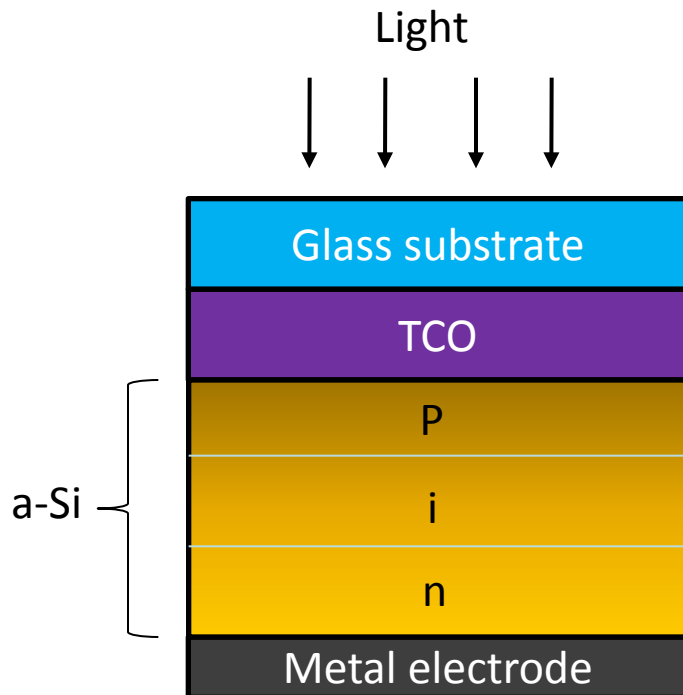


Production Capacity Outlook – Crystalline and Thin Film technologies

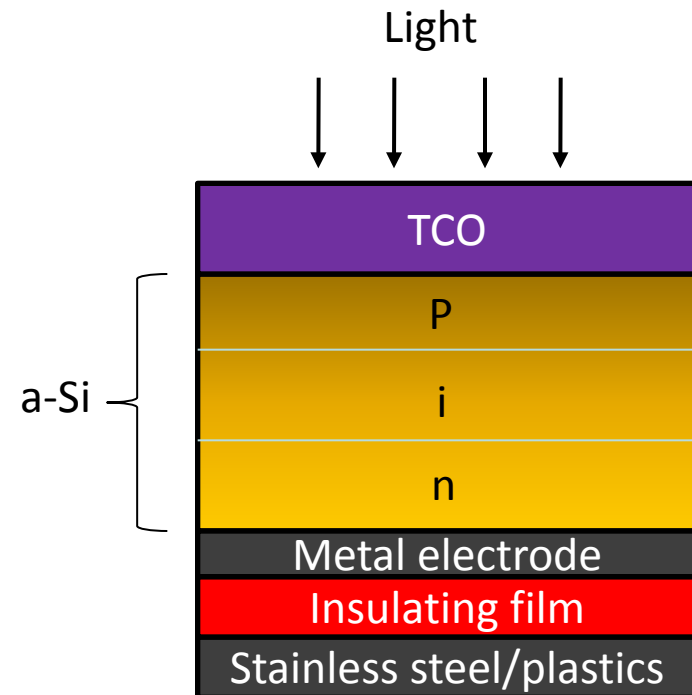
Source: EPIA 2009

Structures of Si-based Thin Film Solar Cells

Superstrate

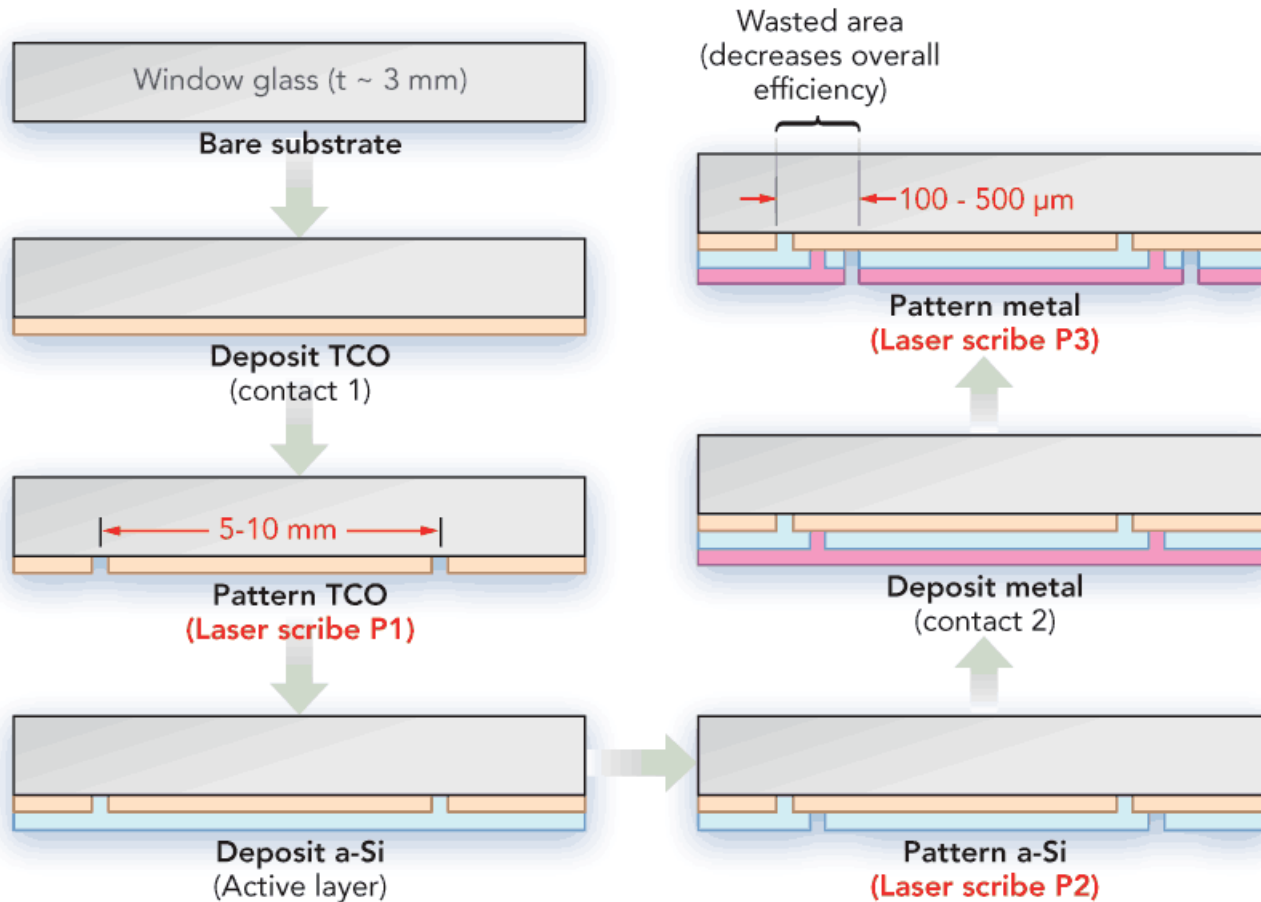


Substrate



Roll-to-Roll process for flexible photovoltaic device

Fabrication process of a-Si solar cell



CIGS/CZTS Solar Cell

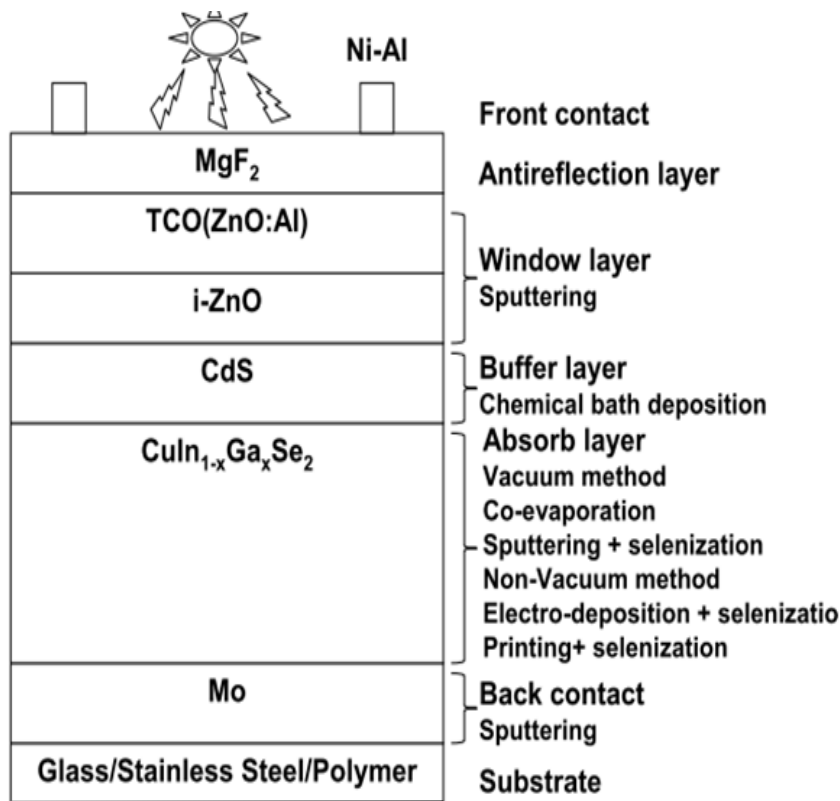
CIGS solar cell



What is CZTS solar cell?



● Copper Indium Gallium Diselenide (CIGS) Solar Cells



Device structure

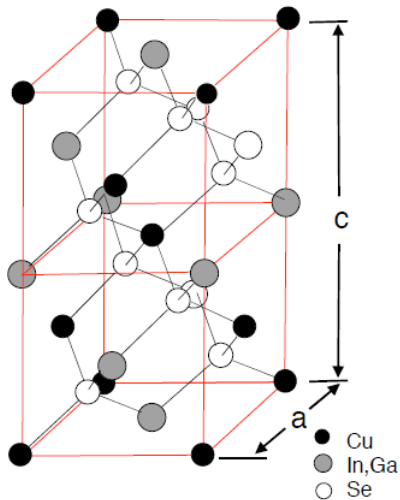
Advantages

- High cell efficiency (19.2%) and module efficiency (13.4%).
- The band-gap can be determined by the In/Ga ratio
- Can be deposited on flexible substrates
- Comparatively long lifetime

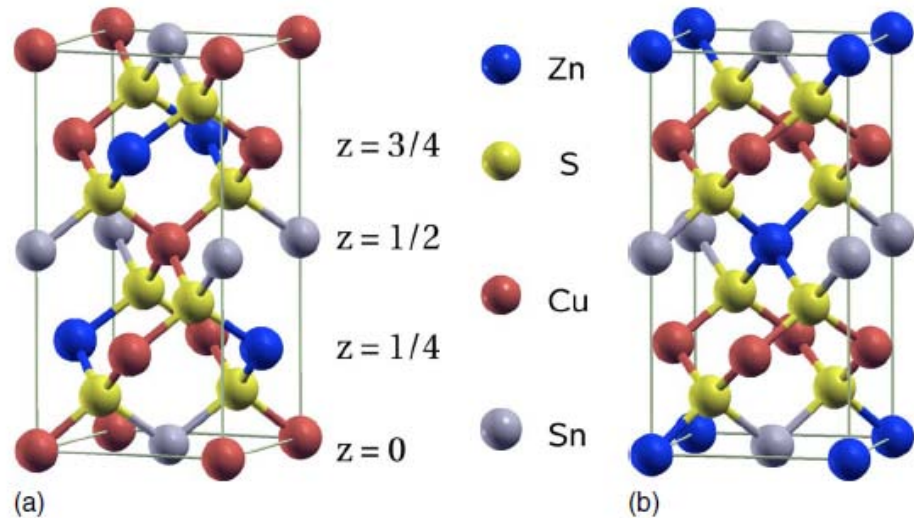
Disadvantages

- Limited availability of indium
- Toxicity of CdS n-type buffer layer

Crystallographic Properties of CIGS/CZTS











CIGS
(Chalcopyrite)



Schematic representations of the (a) kesterite and
(b) stannite structures

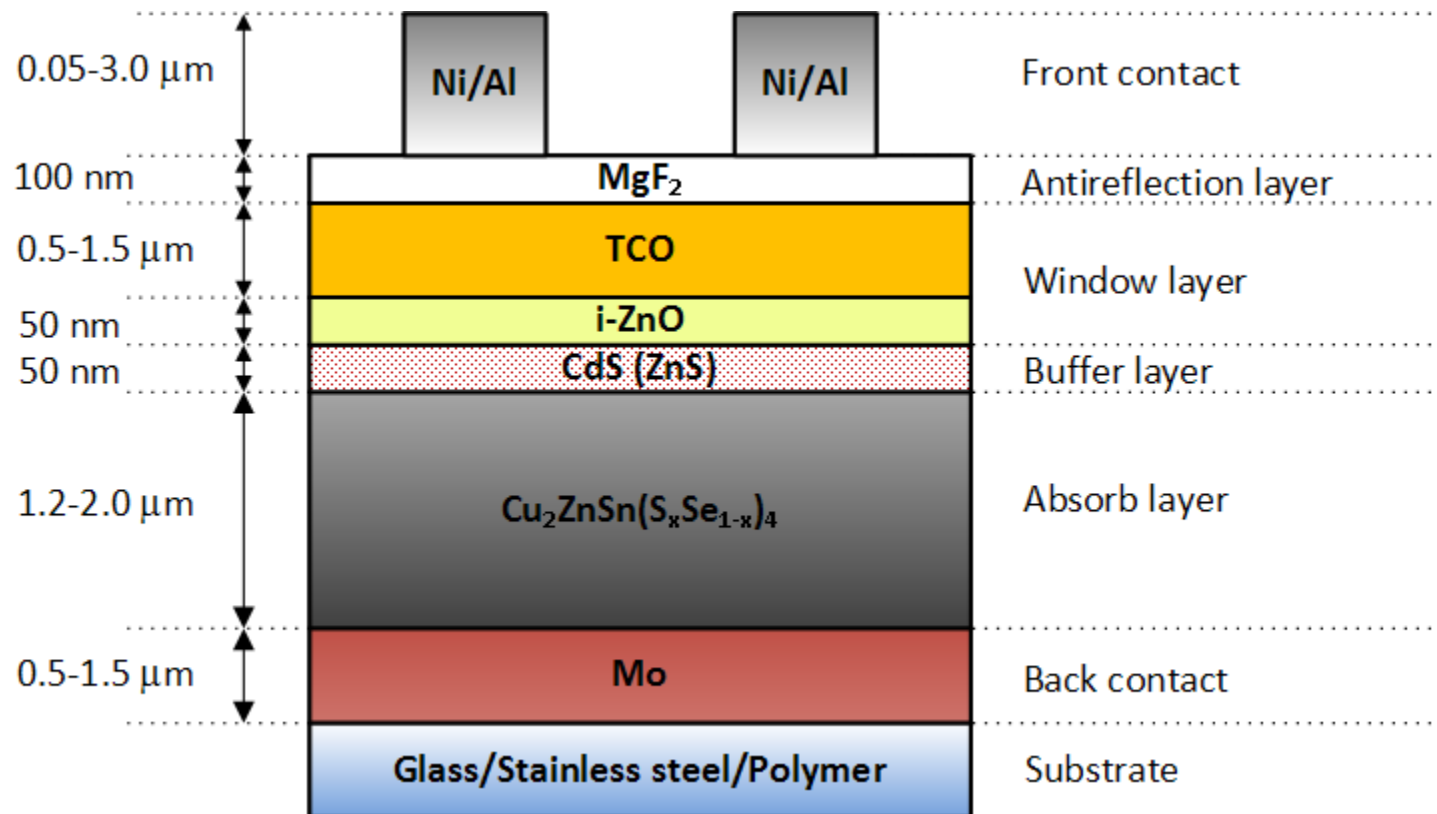
CIGS solar cell manufacture

Vacuum method			
Co-evaporation		Sputtering + selenization	
			
<p>Best cell: 19.9%</p> <p>Best module: 14%</p>	<ul style="list-style-type: none"> ● Process control ● Modest material utilization 	<ul style="list-style-type: none"> ● Process control ● Sputtering is mature technology ● Moderate conversion efficiency ● Two steps can be combined 	<ul style="list-style-type: none"> ● Reaction kinetics can be slow ● Targets costly ● Adhesion ● H₂Se hazardous, attacks metal foils
Non-vacuum method			
Electro-deposition + selenization		Printing + selenization	
			
<ul style="list-style-type: none"> ● Process control ● High production rates ● High materials utilization 	<ul style="list-style-type: none"> ● Low conversion efficiency ● Uniformity ● Adhesion ● H₂Se hazardous 	<p>Best cell: 16.4%</p> <p>Best module: 11%</p>	<ul style="list-style-type: none"> ● Low conversion efficiency ● Reaction kinetics can be slow ● H₂Se hazardous

Global CIGS Manufacturer

Manufacturer		Substrate	Process	Module Efficiency (%)
Japan	Showa Shell	glass	Sputter/Selenization	14
	Honda	glass	Selenization	13.9
U.S.A.	Global Solar	steel	Co-evaporation/R2R	10
	Ascent Solar	polymer	Co-evaporation	-
	Nanosolar	flexible	Print/RTP	11
	Daystar	glass	Sputter	10
	ISET	glass/flex	Ink/Selenization	13.6/glass
	Miasole	glass	Sputter	-
	SoloPower	steel	ED/RTP	-
Europe	Avancis	glass	Sputter/RTP	-
	Würth Solar	glass	Co-evaporation	13

CZTS Solar Cell Device



Approaches for the Preparation of CZTS Thin Film

Best efficiency

Physical vapor method

Sputtering	6.77%	K. Jimbo <i>et al.</i> , <i>Thin Solid Films</i> 515 , 5997 (2007). H. Katagira <i>et al.</i> , <i>Appl. Phys. Express</i> 1 , 041201 (2008). T. Tanaka <i>et al.</i> , <i>J. Phys. Chem. Solids</i> 66 , 1978 (2005).
Evaporation	1.79%	H. Araki <i>et al.</i> , <i>Thin Solid Films</i> 517 , 1457 (2008). H. Katagiri <i>et al.</i> , <i>Sol. Energy Mater. Sol. Cells</i> 49 , 407 (1997). T. Tanaka <i>et al.</i> , <i>Phys. Status Solidi C</i> 3 , 2844 (2006).

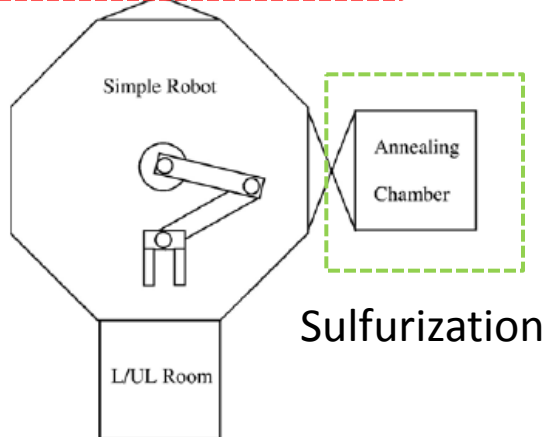
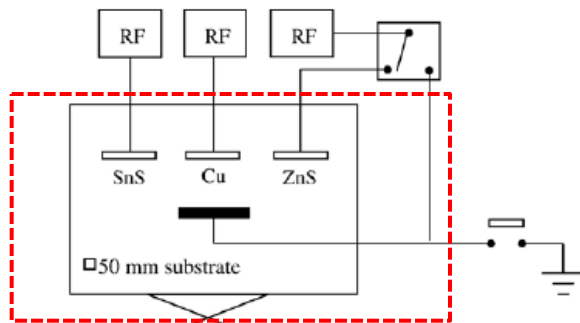
Chemical deposition method

Electro-deposition	3.4%	M. Kurihara <i>et al.</i> , <i>Physica Status Solidi C</i> 6 , 1241 (2009). A. Ennaoui <i>et al.</i> , <i>Thin Solid Films</i> 517 , 2511 (2009). H. Araki <i>et al.</i> , <i>Sol. Energy Mater. Sol. Cells</i> 93 , 996 (2009).
Photochemical deposotion	-	K. Moriya <i>et al.</i> , <i>Phys. Status Solidi C</i> 3 , 2848 (2006).
Sol-gel	1.01%	M. Y. Yeh <i>et al.</i> , <i>J. Sol-Gel Sci. Technol.</i> 52 , 65 (2009). K. Tanaka <i>et al.</i> , <i>Sol. Energy Mater. Sol. Cells</i> 93 , 583 (2009). K. Tanaka <i>et al.</i> , <i>Sol. Energy Mater. Sol. Cells</i> 91 , 1199 (2007).
Spray pyrolysis	-	N. Nakayama <i>et al.</i> , <i>Appl. Surf. Sci.</i> 92 , 171 (1996). J. Madarasz <i>et al.</i> , <i>Solid State Ionics</i> , 439 (2001). N. Kamoun <i>et al.</i> , <i>Thin Solid Films</i> 515 , 5949 (2007).
Solution-based synthesis	9.66%	T. K. Todorov <i>et al.</i> , <i>Adv. Mater.</i> 22 , E156 (2010). S. C. Riha <i>et al.</i> , <i>J. Am. Chem. Soc.</i> 131 , 12054 (2009). Q. Guo <i>et al.</i> , <i>J. Am. Chem. Soc.</i> 131 , 11672 (2009). C. Steinhagen <i>et al.</i> , <i>J. Am. Chem. Soc.</i> 131 , 12554 (2009).

Vacuum Method for CZTS Solar Cell

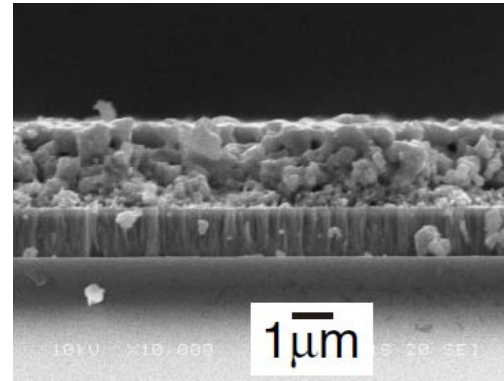
Nagaoka National College of Technology

Cu,Zn,Sn, S
deposition

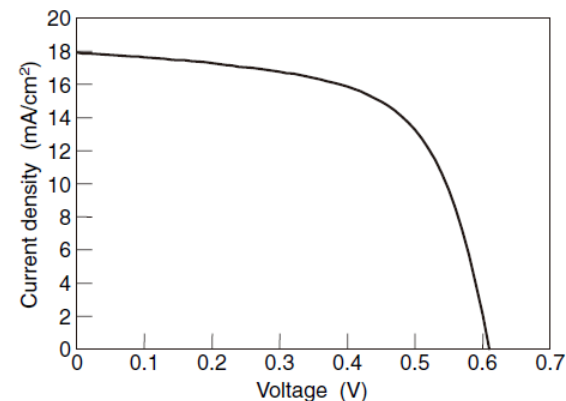


Inline-type vacuum apparatus

Co-sputtering



SEM image of the cross-sectional view of the CZTS absorber layer on the Mo electrode layer.
Many voids in the CZTS absorber layer were confirmed

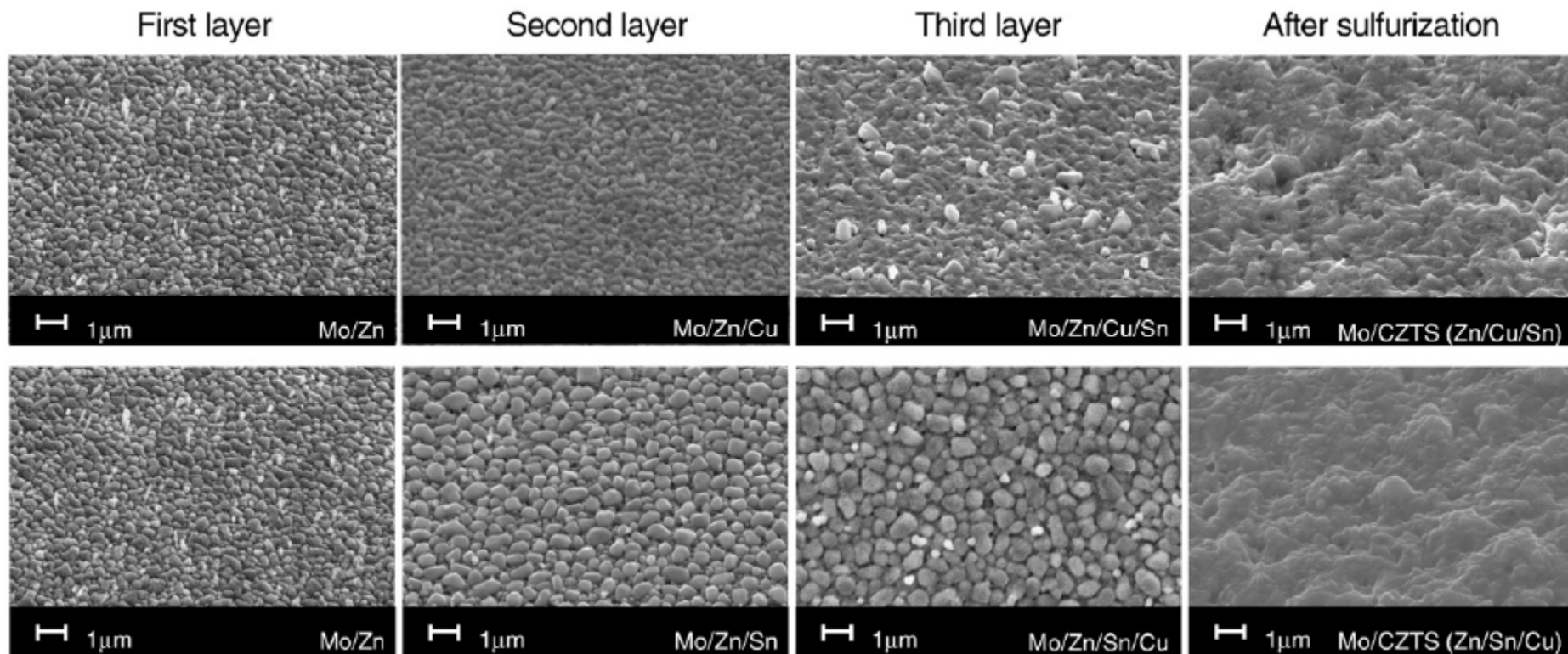


K. Jimbo *et al.*, *Thin Solid Films* **515**, 5997 (2007).

H. Katagira *et al.*, *Appl. Phys. Express* **1**,041201 (2008).

Vacuum method

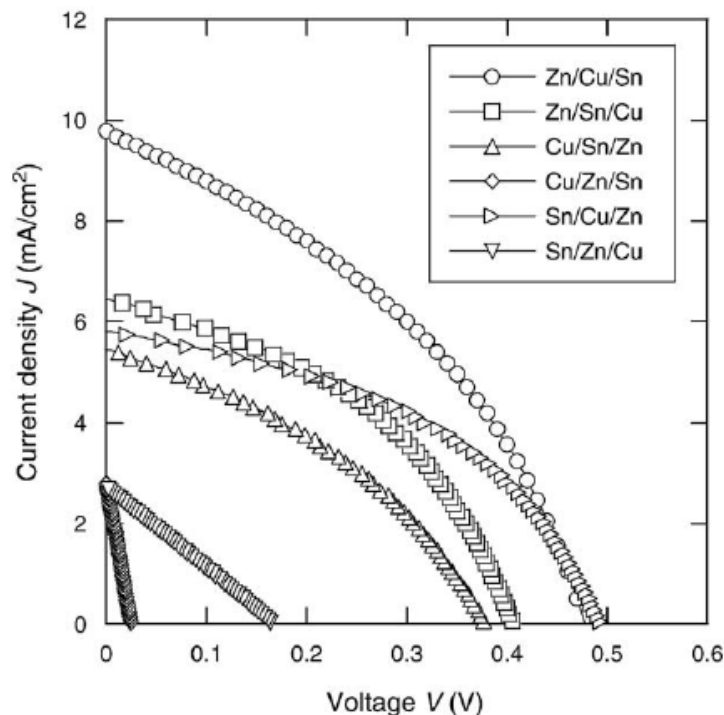
Stacking Sequence of Precursors (1)



SEM micrographs of the precursors and sulfurized films

e-beam evaporation

Stacking Sequence of Precursors (2)



Photovoltaic properties of the solar cells

Stacking order	Group	Photovoltaic properties of cells				
		Area (cm ²)	V _{oc} (mV)	J _{sc} (mA/cm ²)	Fill factor	Efficiency (%)
Mo/Zn/Cu/Sn	A	0.132	478	9.78	0.38	1.79
Mo/Zn/Sn/Cu	A	0.135	406	6.44	0.43	1.12
Mo/Cu/Sn/Zn	A	0.120	377	5.43	0.38	0.77
Mo/Cu/Zn/Sn	B	0.166	24	2.60	0.27	0.01
Mo/Sn/Cu/Zn	B	0.126	495	5.81	0.45	1.29
Mo/Sn/Zn/Cu	C	0.150	166	2.54	0.25	0.11

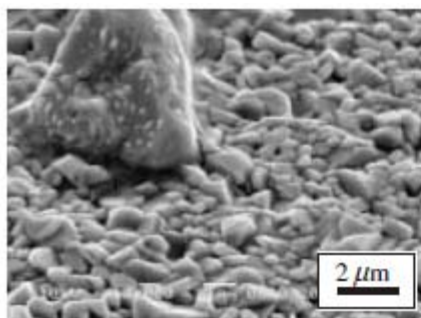
A large conversion efficiency was observed in the cells with stacking order where Cu and Sn were adjacent.

Comparison of the I–V characteristics of cells used six stacking orders of the precursors.

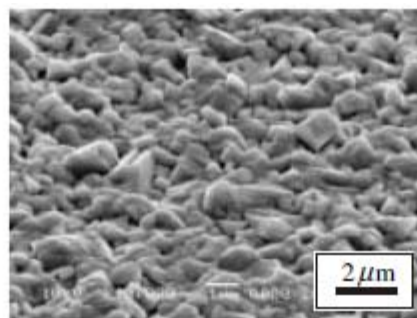
Compositions of CZTS Thin Film

Chemical composition and compositional ratio of CZTS thin films with several composition

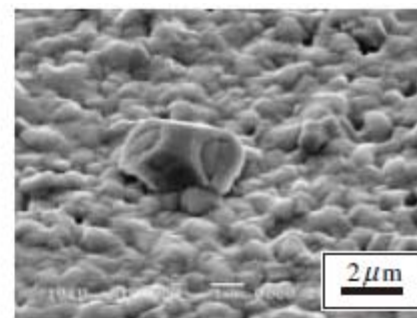
Sample No.	Chemical composition				Compositional ratio		
	Cu (at%)	Zn (at%)	Sn (at%)	S (at%)	Cu/(Zn+Sn)	Zn/Sn	S/Metal
CZTS-0.49	16.0	16.2	16.7	51.1	0.49	0.97	1.05
CZTS-0.69	20.0	14.1	15.1	50.8	0.69	0.93	1.03
CZTS-0.80	22.1	13.7	14.0	50.3	0.80	0.98	1.01
CZTS-0.91	23.5	12.7	13.1	50.7	0.91	0.98	1.02
CZTS-0.99	25.0	12.6	12.8	49.6	0.99	0.98	0.98
CZTS-1.01	26.1	11.8	12.2	49.9	1.09	0.97	1.00
CZTS-1.18	27.4	11.4	11.9	49.4	1.18	0.96	0.98



(a)



(b)



(c)

SEM micrographs of the surface of CZTS films with various compositions. These numbers correspond to their Cu/(Zn+Sn) ratio. (a) CZTS-0.49 (b) CZTS-0.83 (c) CZTS-1.18.

Zn-rich, Cu-poor compositions are desirable for the CZTS
Cu/(Zn+Sn) = 0.8-0.9 suitable for absorber

Organic Solar Cells

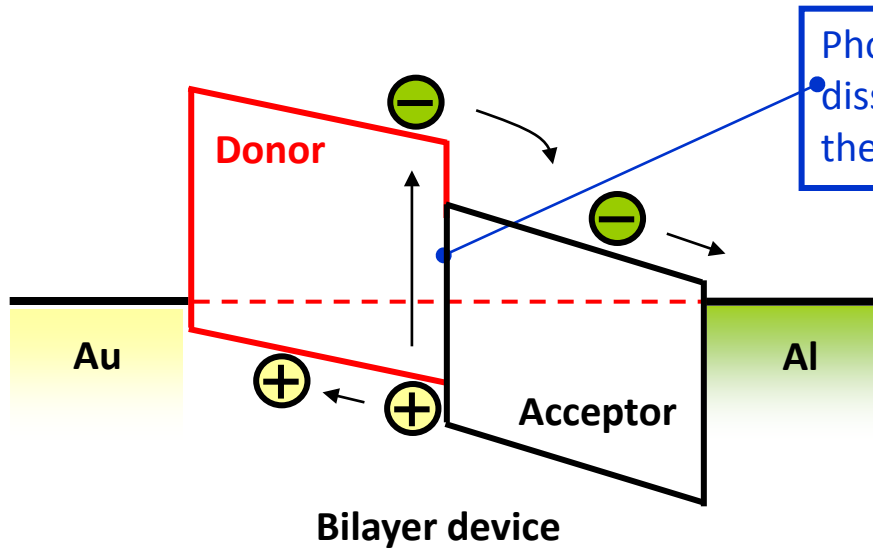
- **Why Organic Solar Cells**
 - low cost, roll-to-roll process
 - light weight, flexibility
 - selectivity of materials
- **Drawback of Organic Solar Cells**
 - poor efficiency
 - stability, life time issue



Device Structure

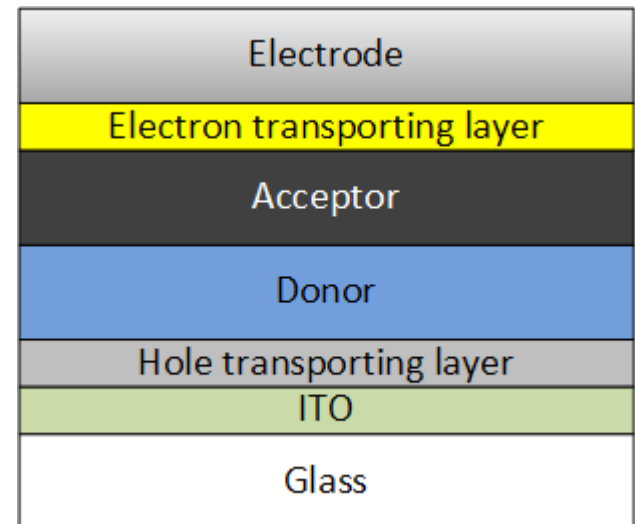
- **Planer Heterojunction OSC**

- Formed between a homogeneous donor layer and a homogenous acceptor layer
- Charge collection efficiency(η_{CC}) will be relatively large
- The exciton diffusion efficiency(η_{ED}) might be a bottleneck



Photogenerated excitons can only be dissociated at the D-A interface and thus the device is exciton diffusion limited.

The bilayer structure usually use in the small molecular OSC system with the thermal evaporation fabrications.

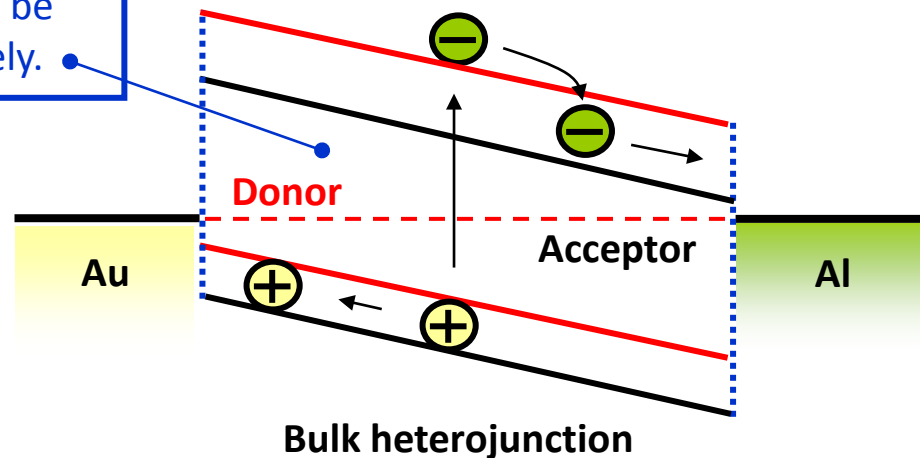
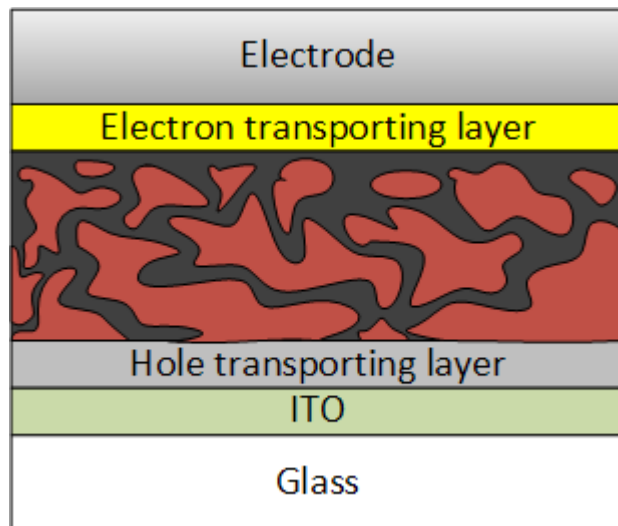


Device Structure

- **Mixed HJ(Blending, BHJ) OSC**

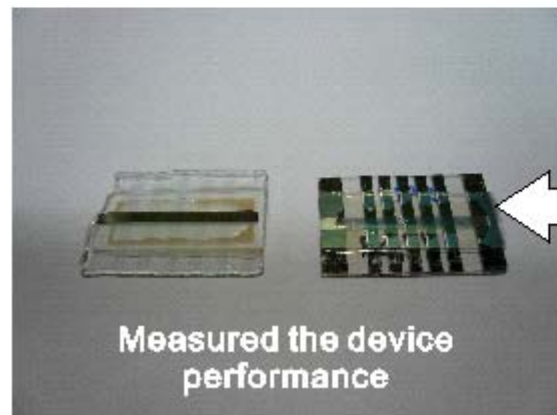
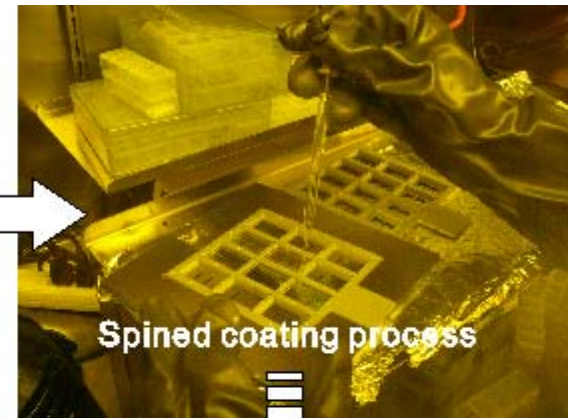
- Usually used in polymer based organic solar cell employs the solution process
- The η_{ED} approaches to unity in the mixed HJ generally
- Charge collection efficiency(η_{CC}) in mixed HJ OSC often plays the role of the bottleneck

The donor is blended with the acceptor.
Thus, photogenerated excitons can be
dissociated into charges immediately.

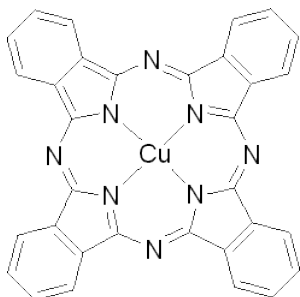


The polymer OSC systems usually
use the BHJ structure with the
spin coating process.

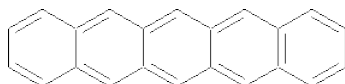
Fabrication Process of Organic Photovoltaic Device



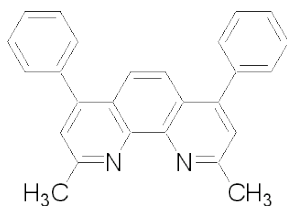
Active Materials



**copper phthalocyanine
(CuPc)**

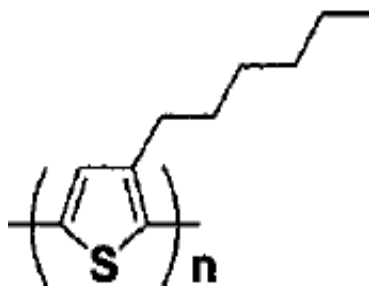


pentacene

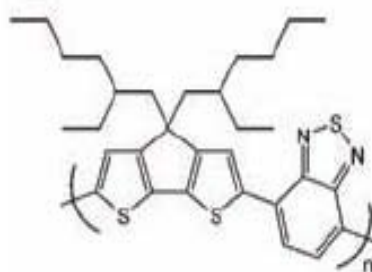


**bathocuproine
(BCP)**

small molecular materials



P3HT

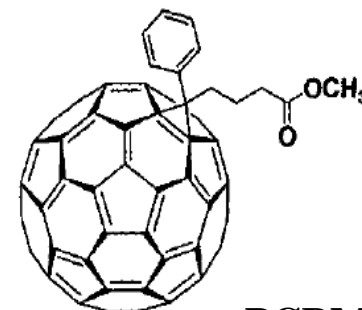


PCPDTBT

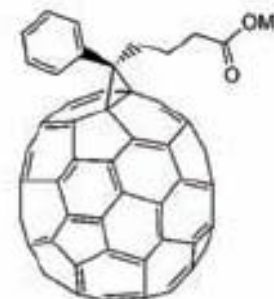
polymer materials



C₆₀



PCBM

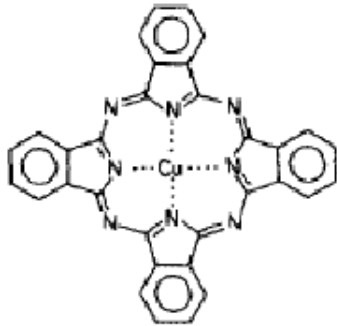


PC₇₀BM

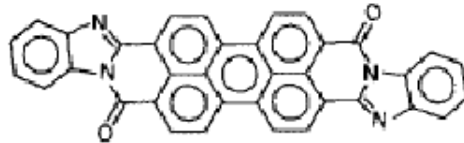
fullerene system

Evolution of OSC

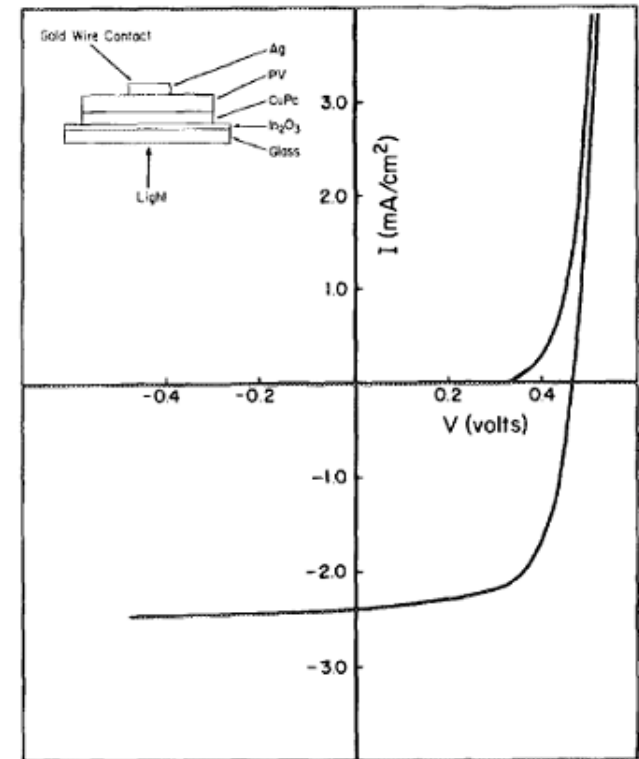
The first breakthrough of organic based solar cell



CuPc



PV

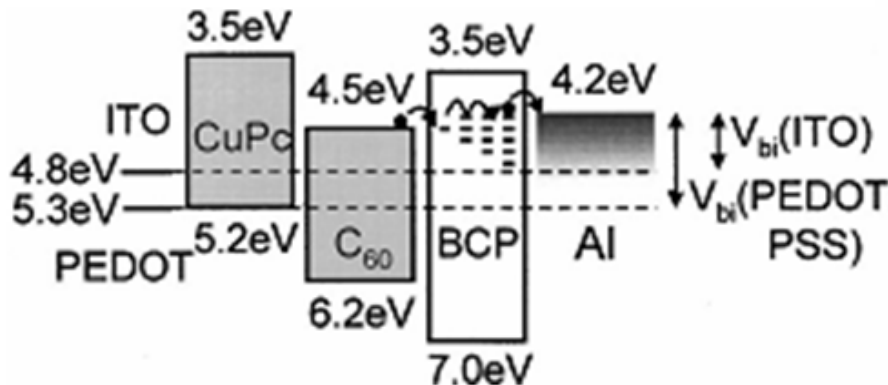


**Under 75 mW/cm² illumination
Active area: 0.1 cm²**

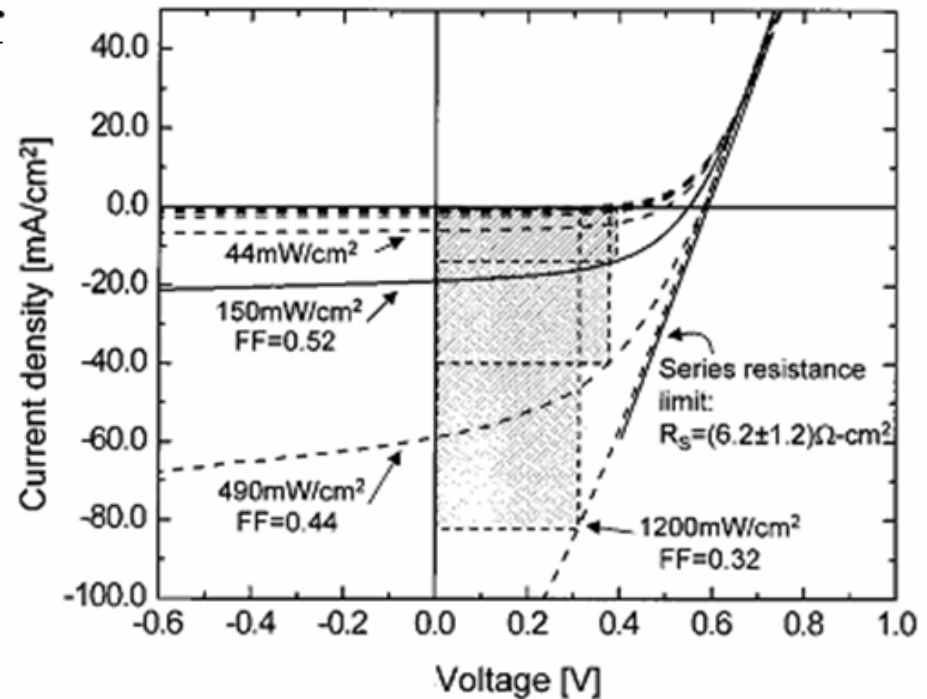
**Tang's group in 1986.
Deposit CuPc and PV thin film in sequence by
thermal evaporation under high vacuum. The
power conversion efficiency reaches 1%**

Evolution of OSC

Using BCP as the exciton blocking layer

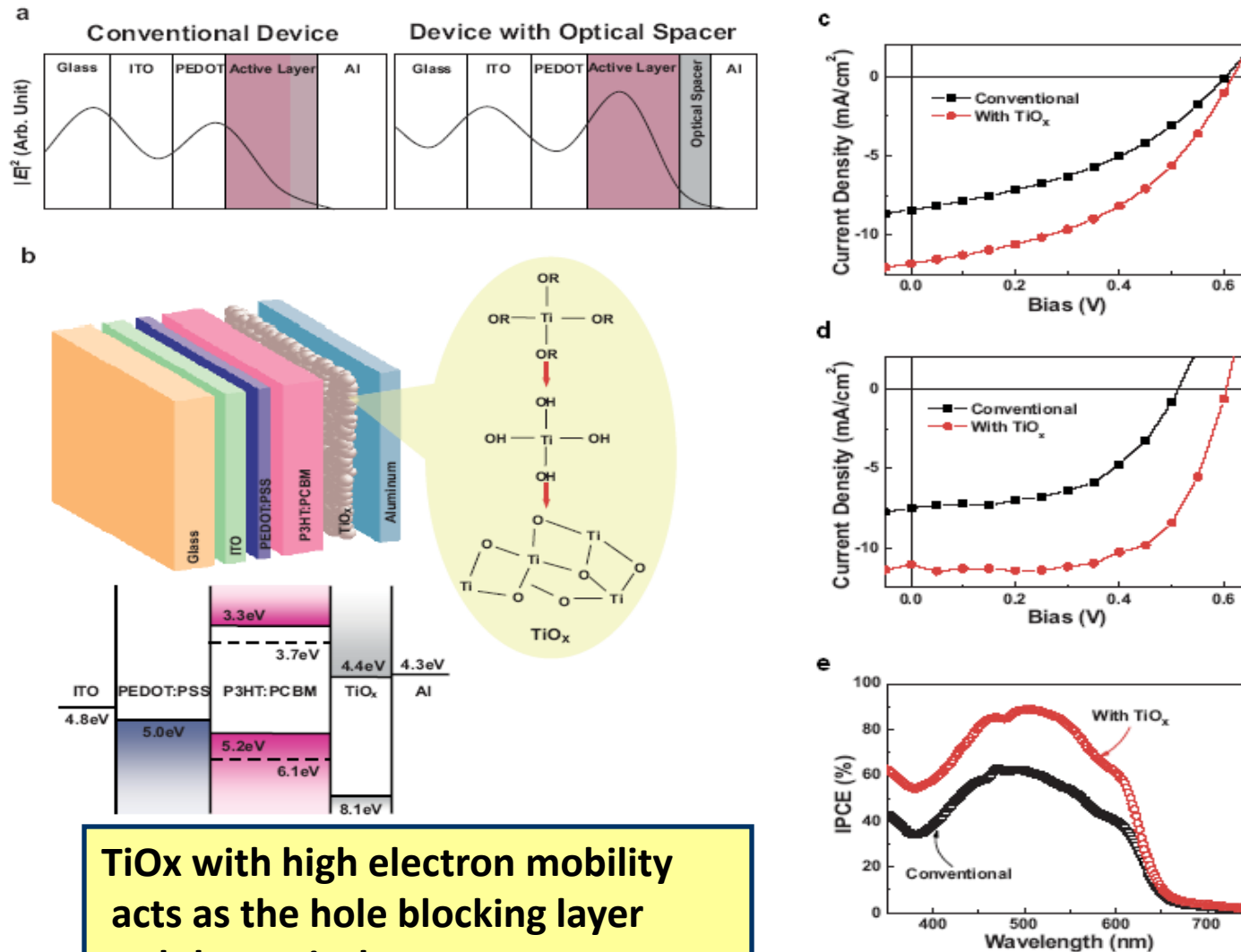


Introducing of C₆₀ and BCP as the acceptor and exciton blocking layer respectively. The power conversion efficiency reaches 3%

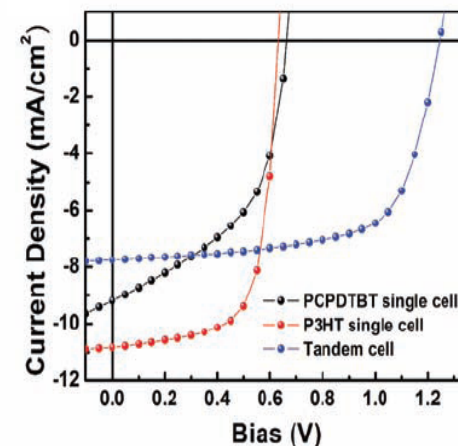
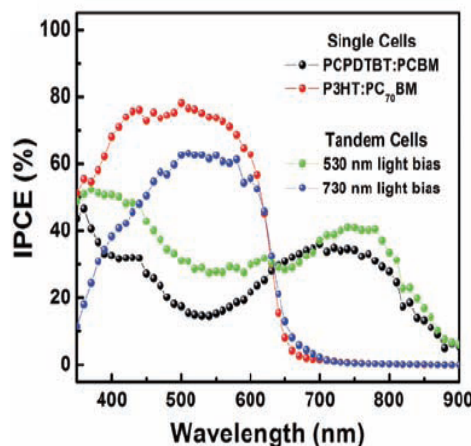
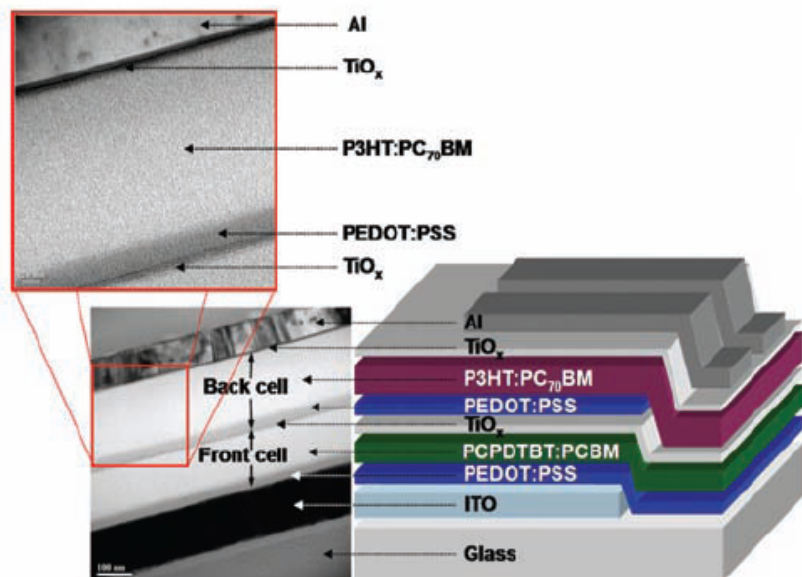
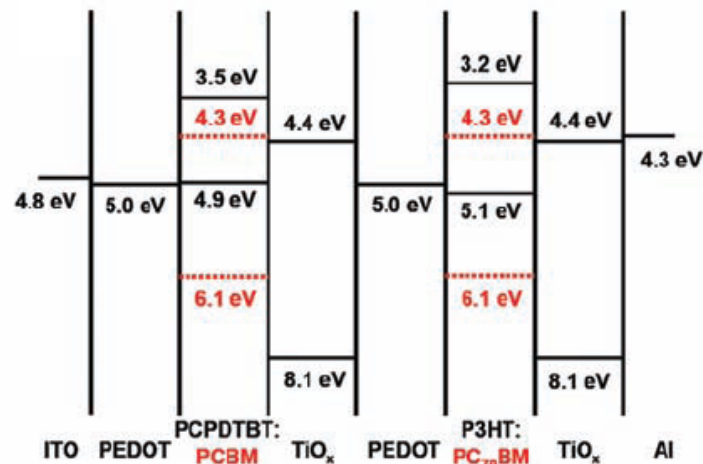
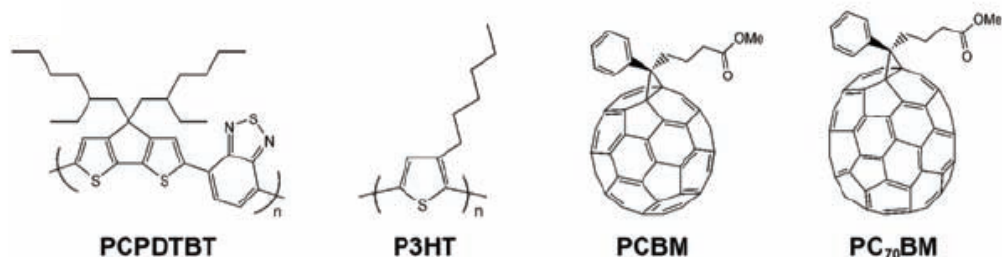


Under 150 mW/cm^2 illumination
Active area: 0.0079 cm^2

Evolution of OSC



Evolution of OSC

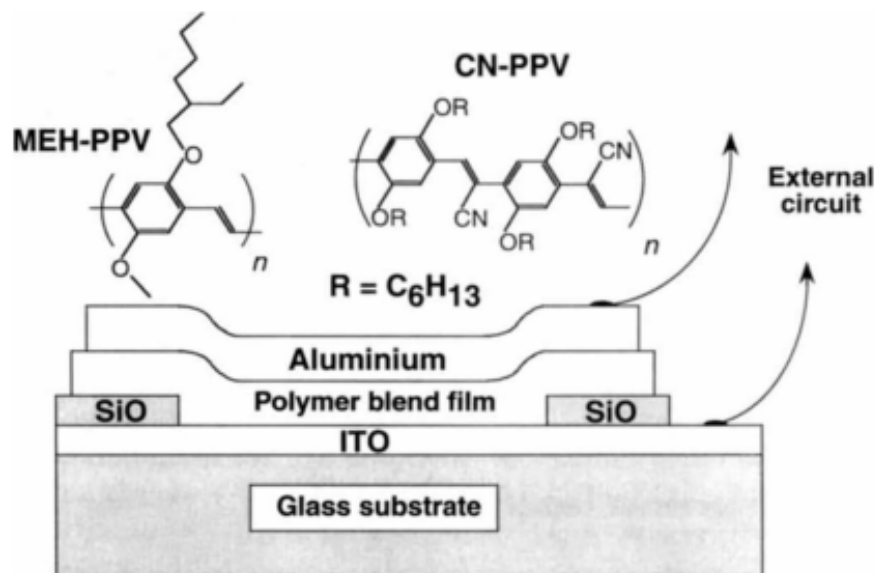


The tandem device introduces the optical spacer and the low band gap material. The power conversion efficiency reaches 7%, which is one of the highest value of the record of efficiency in OSC.

BHJ Solar Cell

First Bulk heterojunction photovoltaics

➡ Composite films of MEH-PPV and fullerenes exhibit η_c of about 29 percent of electrons and η_e of about 2.9 percent.



Schematics of MEH-PPV/C60 solar cells

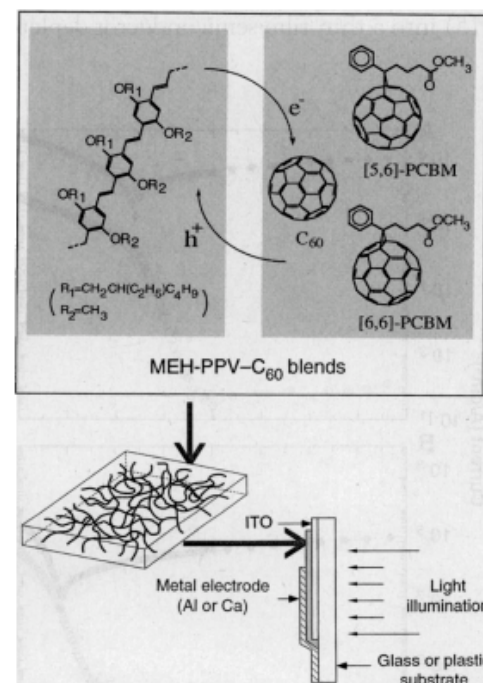
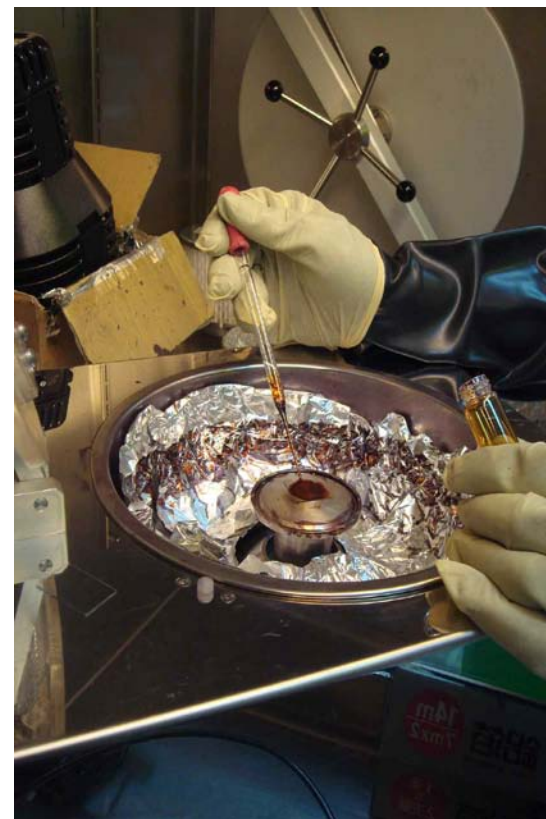
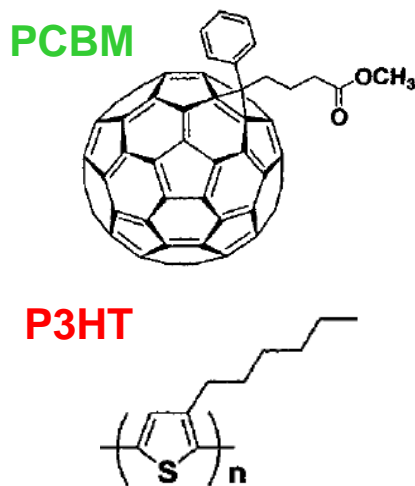
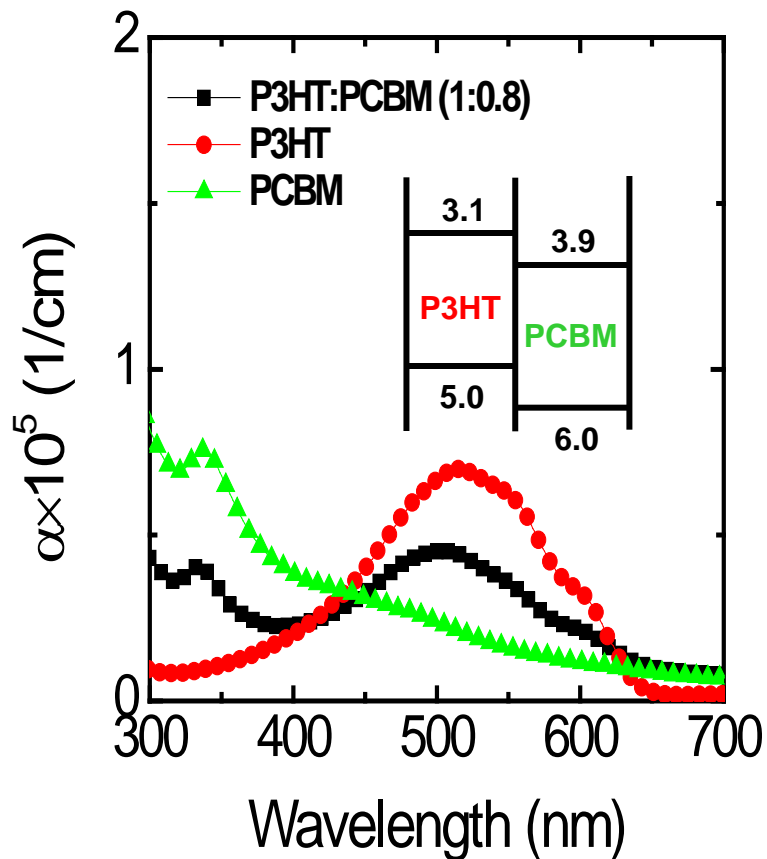


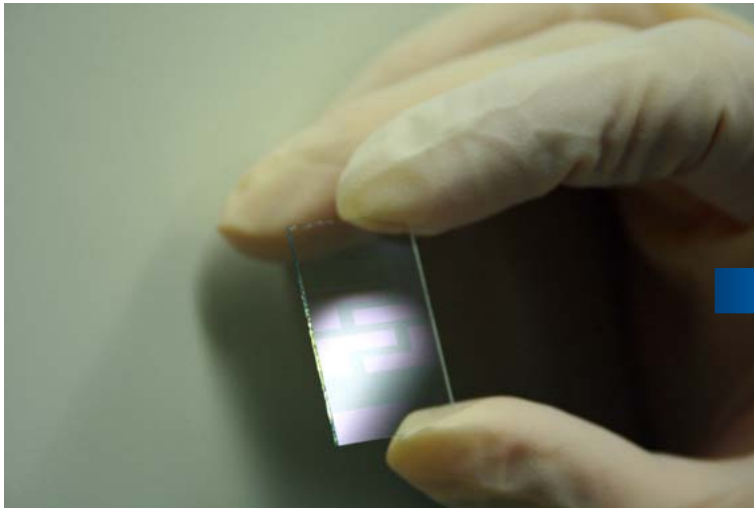
Photo-induced electron transfer from the excited state of a conducting polymer onto buckminsterfullerene, C₆₀, is reported

P3HT:PCBM Solar Cell

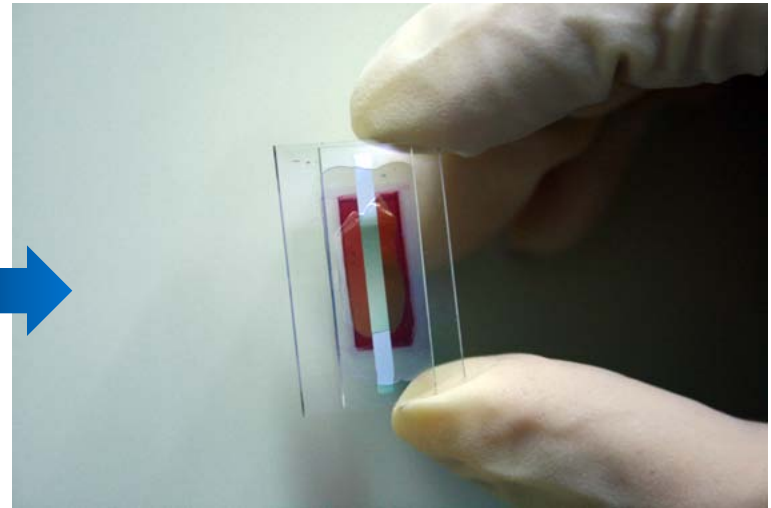
Bulk heterojunction solar cells using P3HT as the electron donor and PCBM as the acceptor were fabricated in the following simple structure: **ITO/PEDOT/P3HT:PCBM/Metal**



P3HT:PCBM Solar Cell



Patterned ITO substrate



Completed P3HT:PCBM solar cell

The Determining Factors of Fabricating Organic Photovoltaic Devices

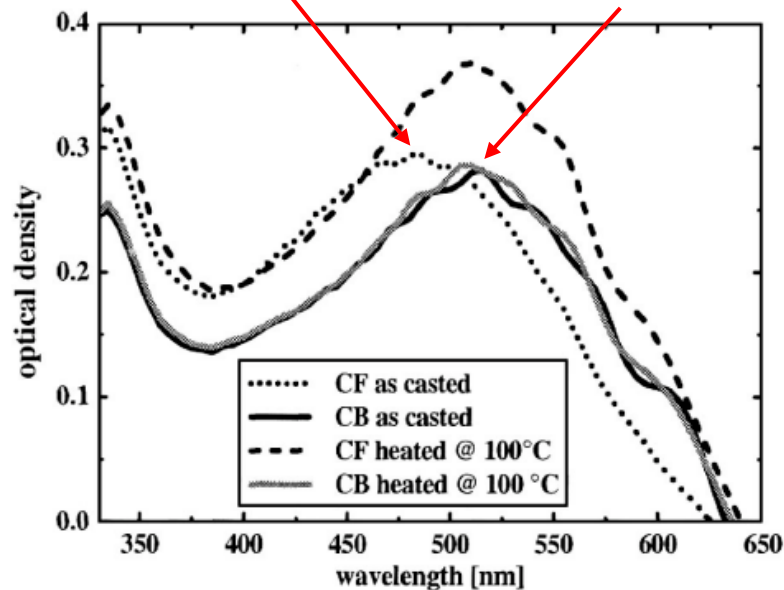
	Resulting influence		
	Absorption	Morphology	Mobility
Solvent	✓	✓	-
Composition	✓	✓	-
Molecular weight	-	-	✓
Thermal annealing	✓	✓	✓
Solvent annealing	✓	✓	-
Additives	✓	✓	-
Buffer layer	-	-	-
Metal contact	-	-	-

Absorption

P3HT:PCBM films casted from chlorobenzene (CB) solution absorb more red light than the films casted from chloroform (CF) solution.

Absorption Maximum - 460 nm (CF)

Absorption Maximum - 510 nm (CB)

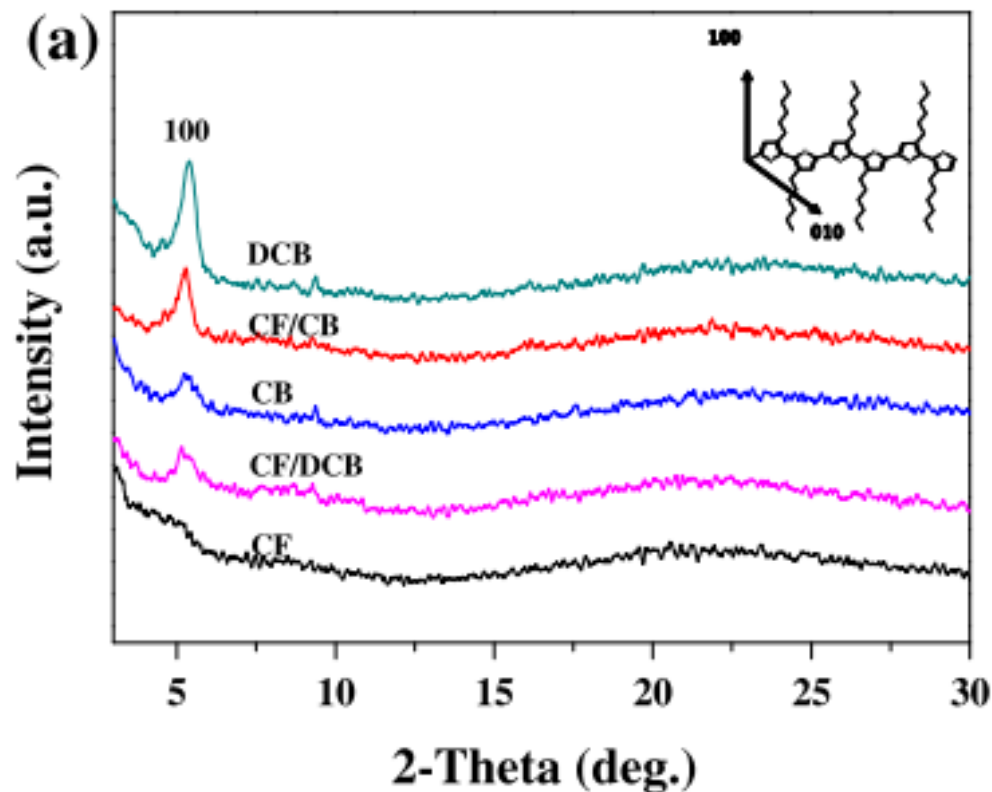


M. Al-Ibrahim *et al.*, *Appl.Phys.Lett.* **376**,201120 (2005)

Crystallinity

The slow evaporation rate of high boiling point solvent and the slow film growth rate may assist P3HT film in forming high degree of crystalline structure.

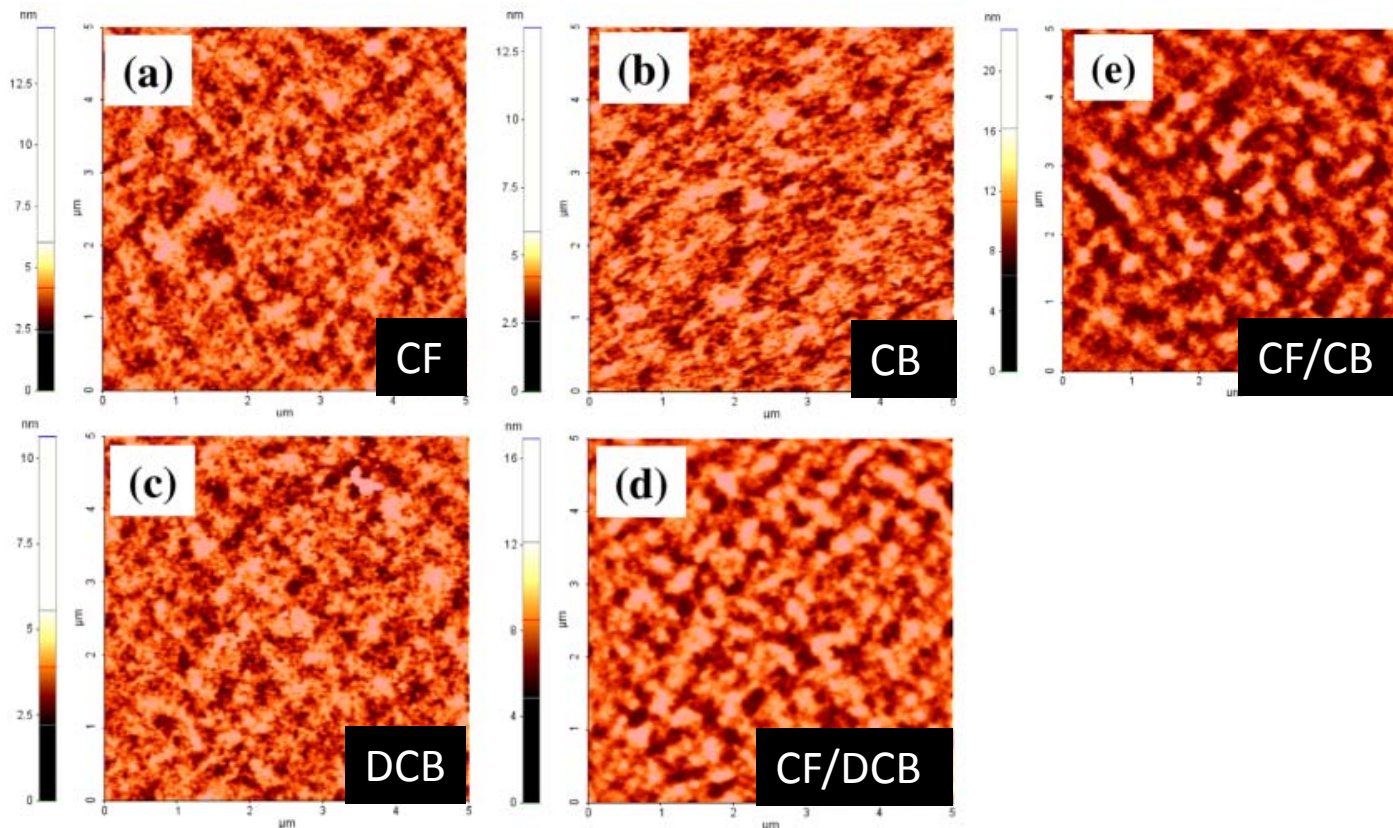
Boiling point	
Chloroform (CF)	61.2 °C
Chlorobenzene (CB)	131.0 °C
Dichlorobenzene (DCB)	180.5 °C



Y. S. Kim *et al.*, *Current Applied Physics*. **10**,985 (2010).

Morphology

Low boiling point solvents (CF and CB) → smoother surface
High boiling point solvents (DCB) → Rougher surface



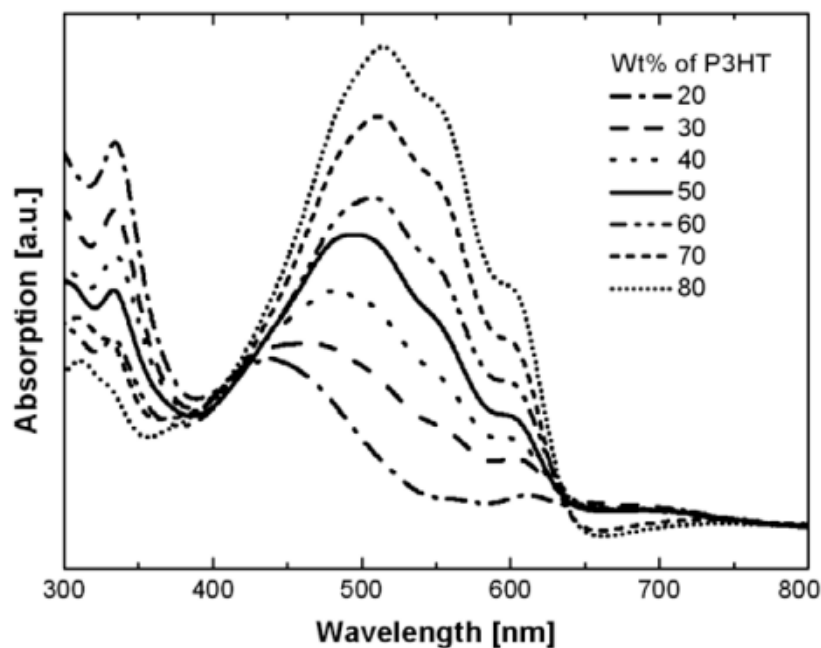
Absorption

The content of P3HT ↑, the absorption spectra of P3HT

➡ Absorption ↑ (450 ~ 650 nm)

➡ become broader

➡ red-shifted



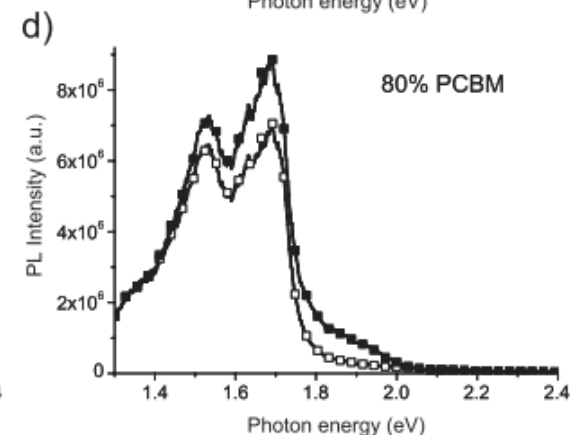
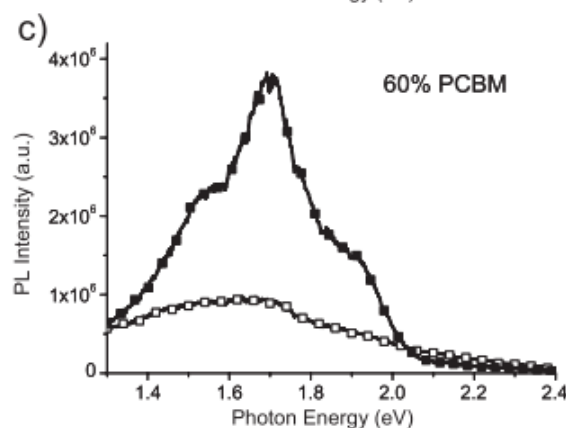
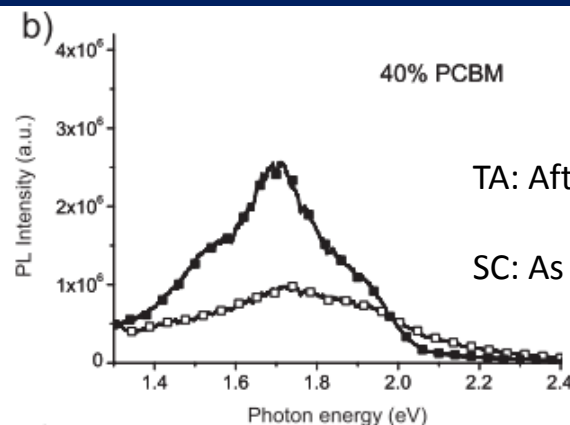
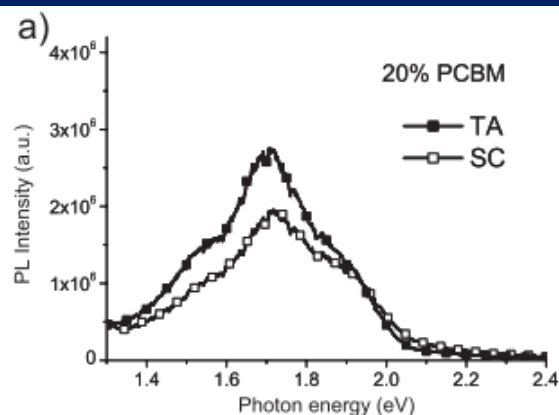
Wt% of P3HT [%]	20	30	40	50	60	70	80
P3HT λ_{max} (nm)	437	461	482	495	507	512	515

Phase Segregation

Photoluminescence (PL) quenching decreasing after thermal annealing

➡ Phase segregation of both P3HT and PCBM increases upon annealing

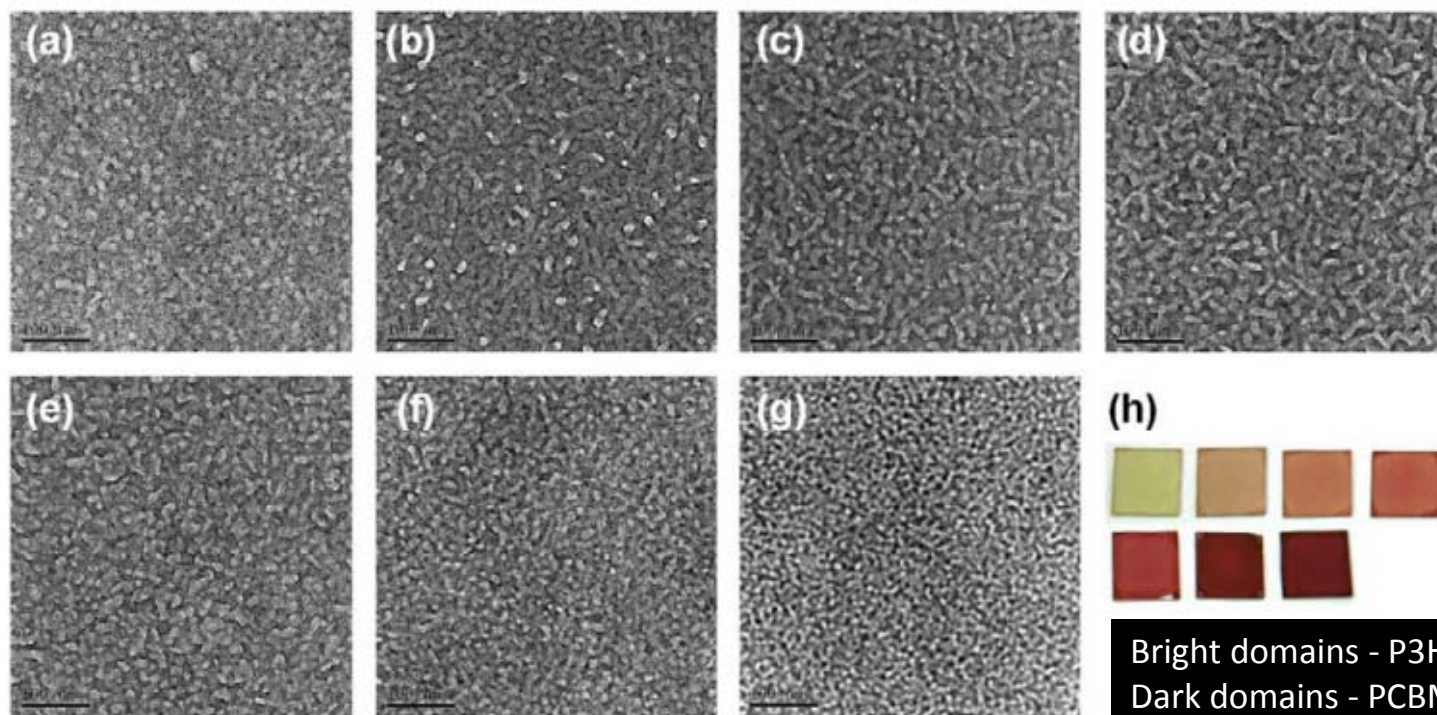
➡ less efficient photoinduced electron transfer between P3HT and PCBM



➡ PL quenching will change obviously before and after annealing as P3HT/PCBM ratio ~ 1

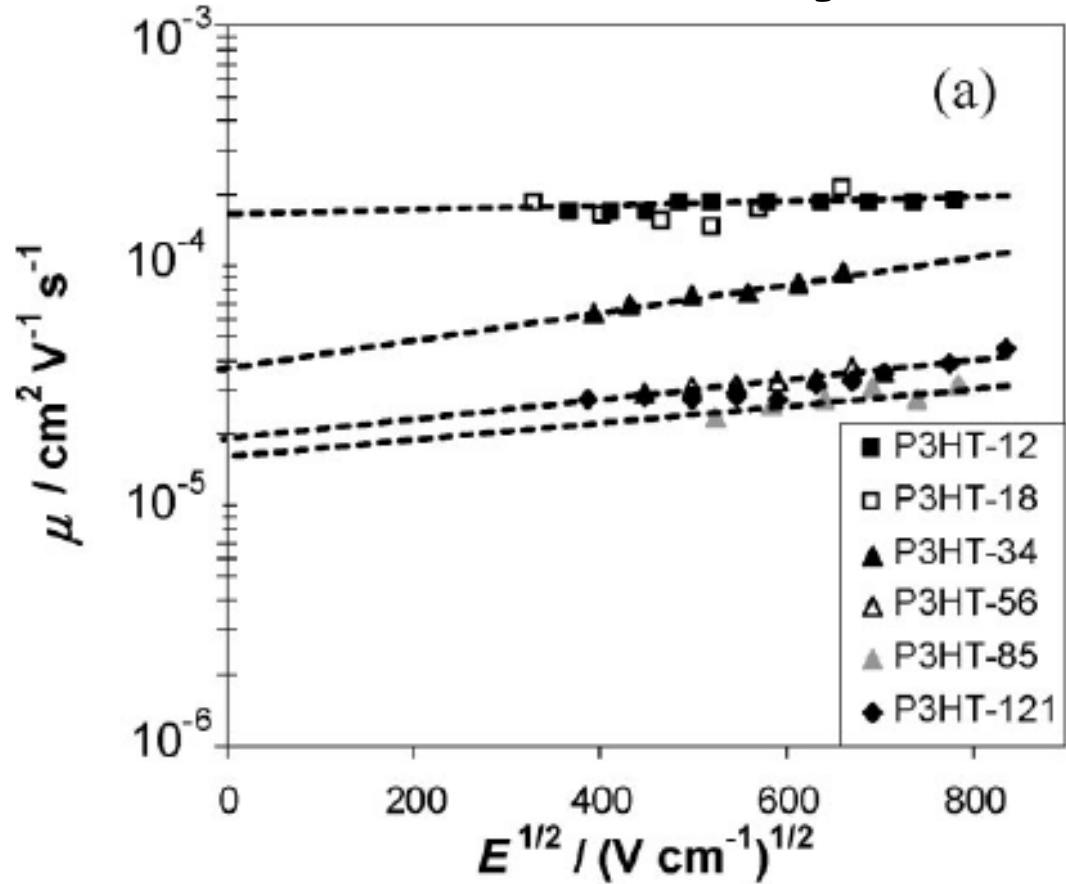
Morphology

The fraction of the highly ordered fiber structure of P3HT increased as the P3HT composition increased up to 50 wt.% and decreased as the composition increased further.



(a) 20% (b) 30% (c) 40% (d) 50% (e) 60% (f) 70% (g) 80% of P3HT

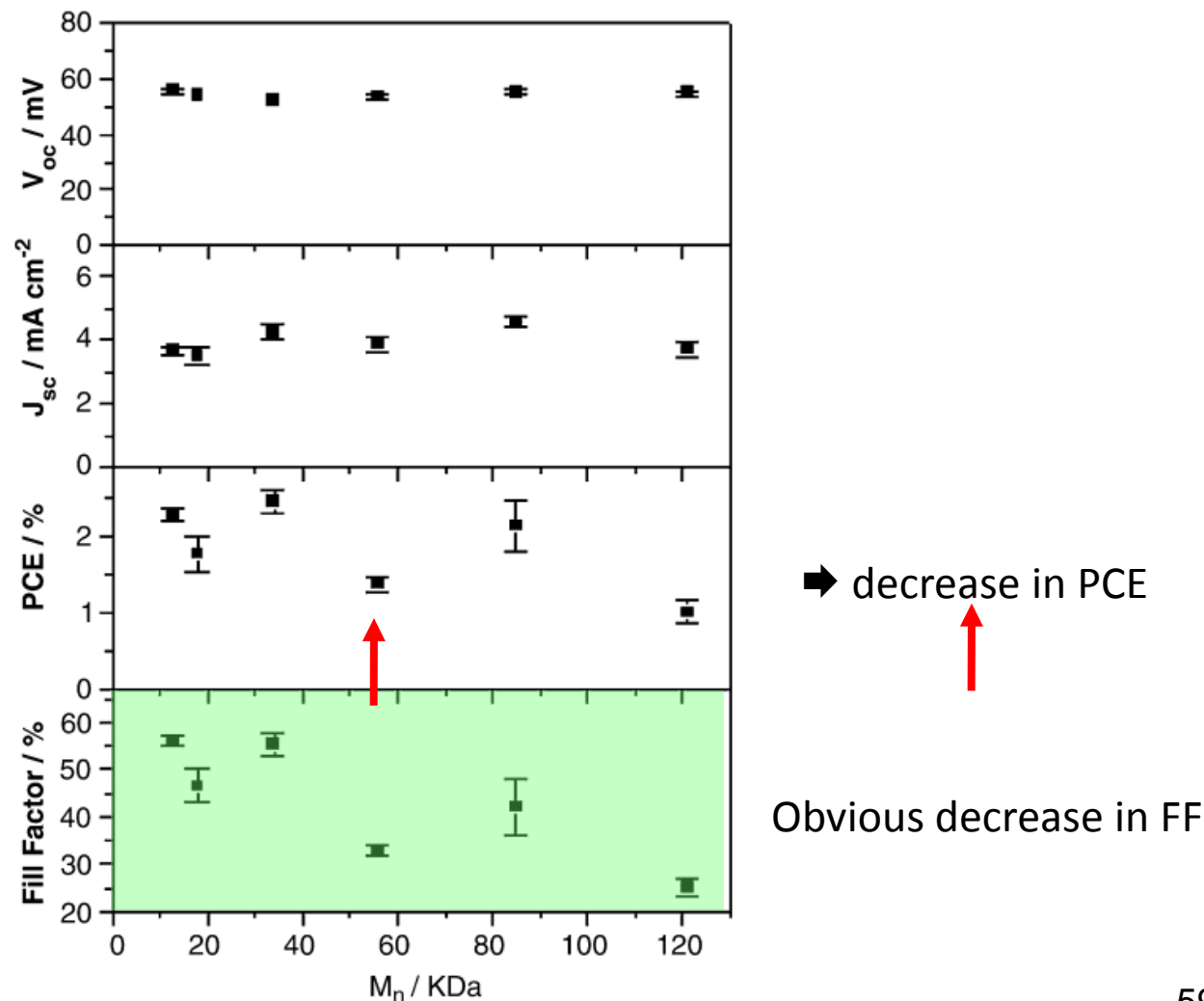
Mobility



Molecular weight ↑
⇒ mobility ↓

	P3HT-13	P3HT-18	P3HT-34	P3HT-56	P3HT-85	P3HT-121
M_n	13.0 kDa	17.6 kDa	34.4 kDa	55.6 kDa	85 kDa	121 kDa
M_w/M_n	2.0	1.8	2.1	2.8	2.6	3.7

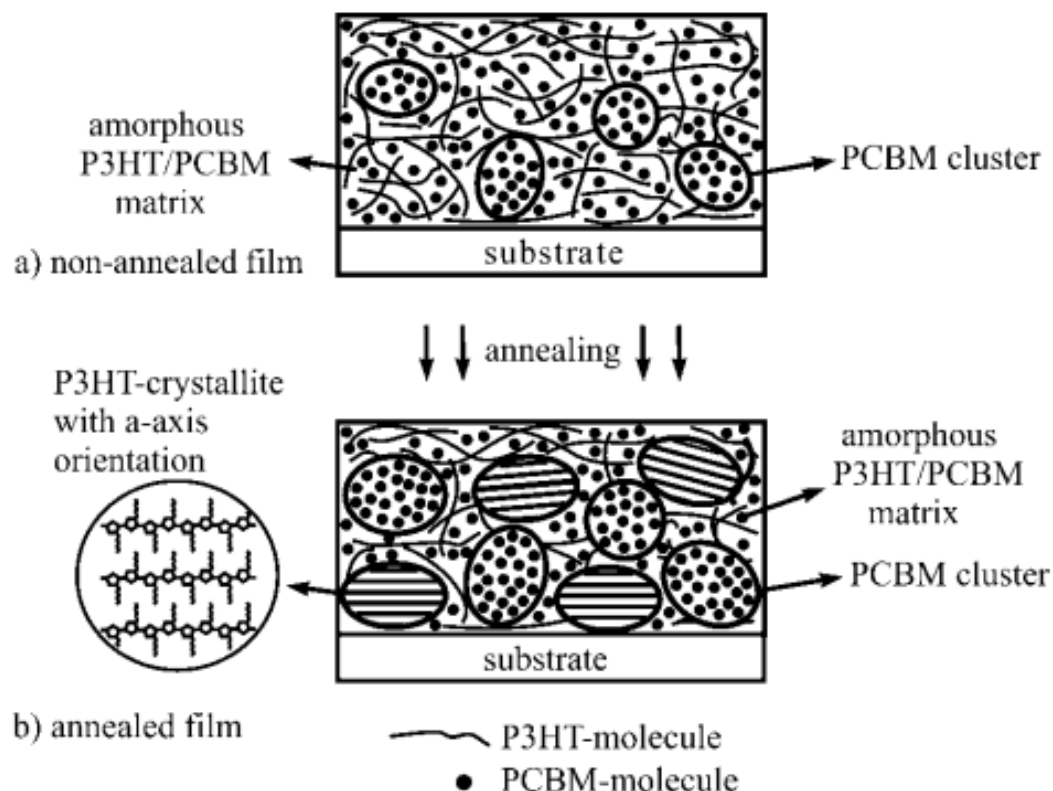
Device Performance



The Mechanism of Thermal Annealing - Redistribution of active materials

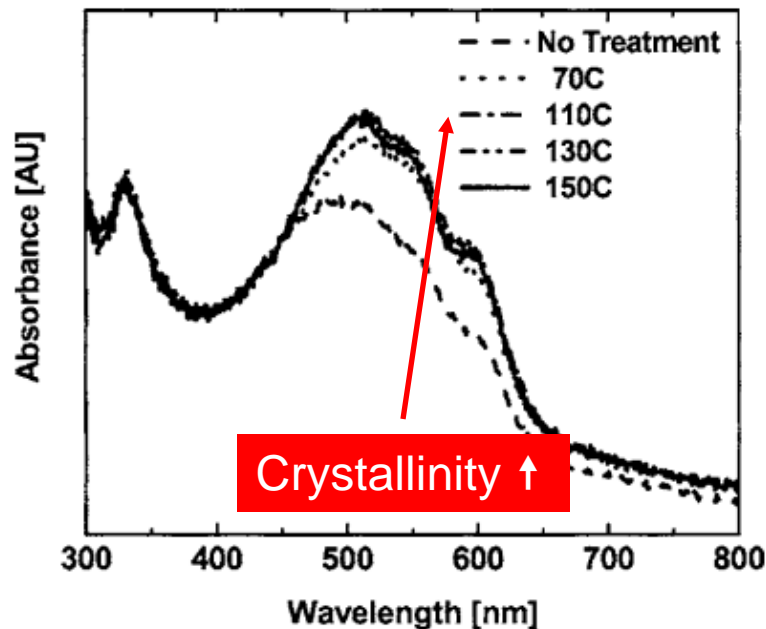
At elevated temperature

- ➔ isolated molecules of PCBM diffuse into larger aggregates
- ➔ in those PCBM-free regions - P3HT aggregates can be converted into P3HT crystallites.

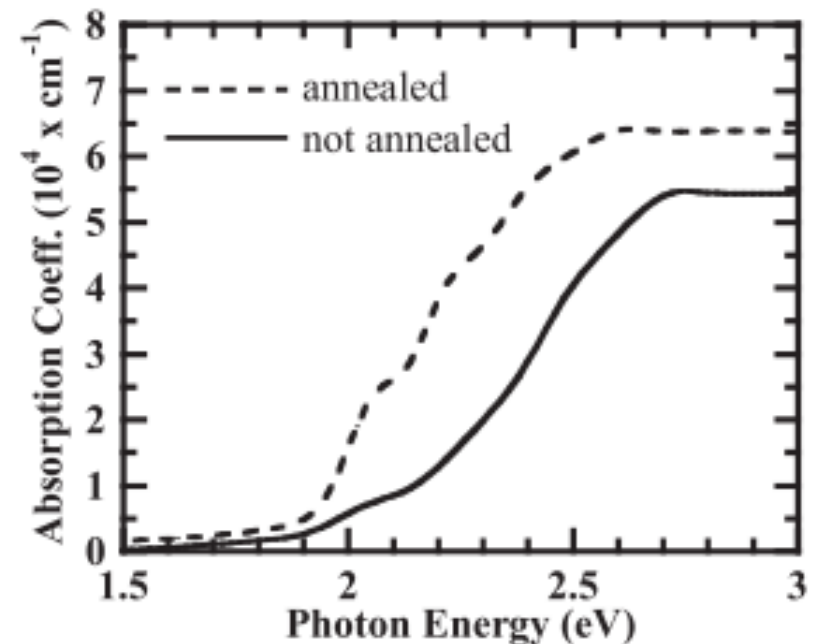


Optical Absorption

The annealed sample showed stronger optical absorption (high crystallinity).



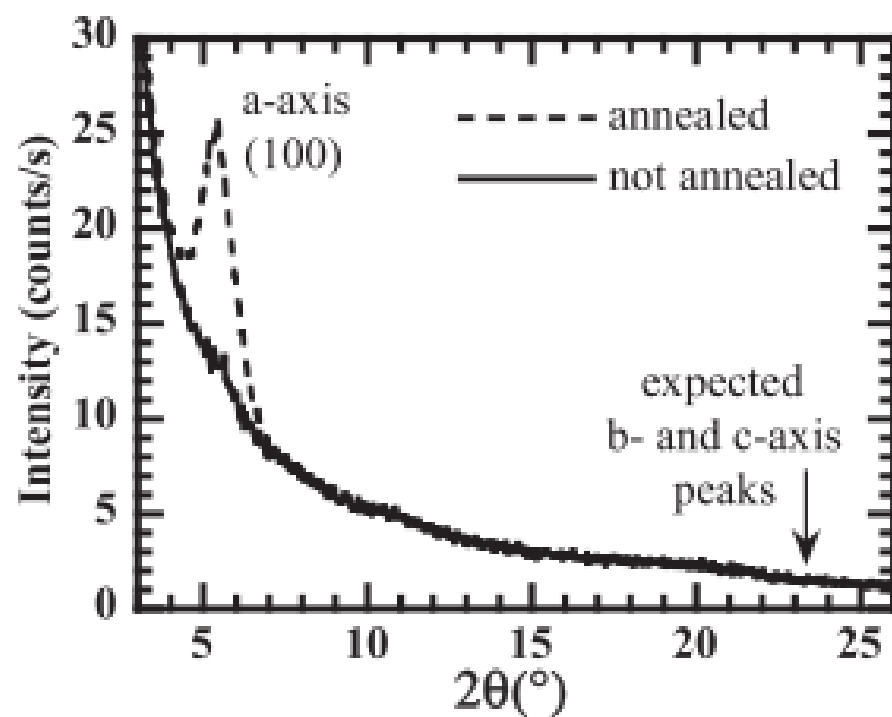
G. Li *et al.*, *J. Appl. Phys.* **98**, 043704 (2005).



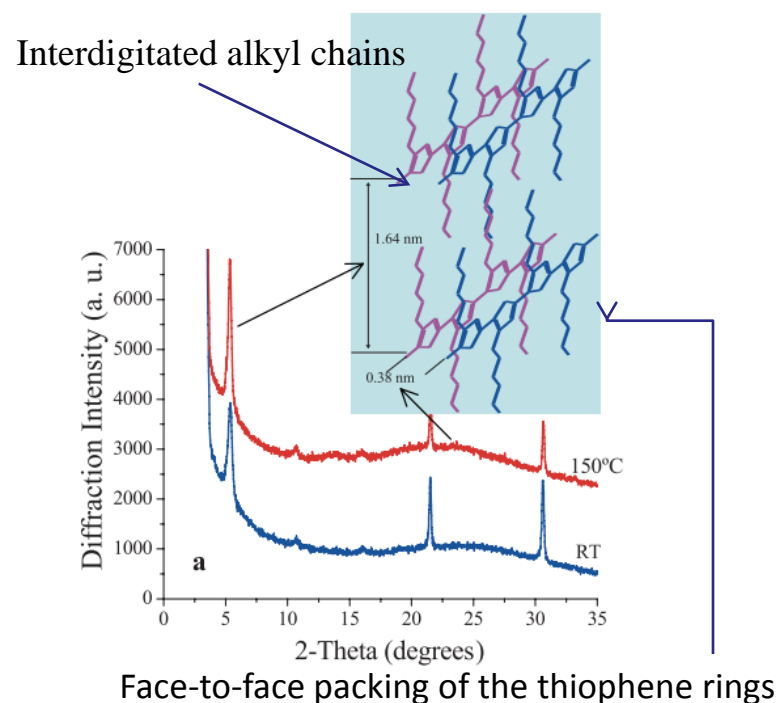
T. Erb *et al.*, *Adv. Funct. Mater.* **15**, 1193 (2005).

Crystallinity

(investigated by XRD)



T. Erb *et al.*, *Adv. Funct. Mater.* **15**, 1193 (2005).

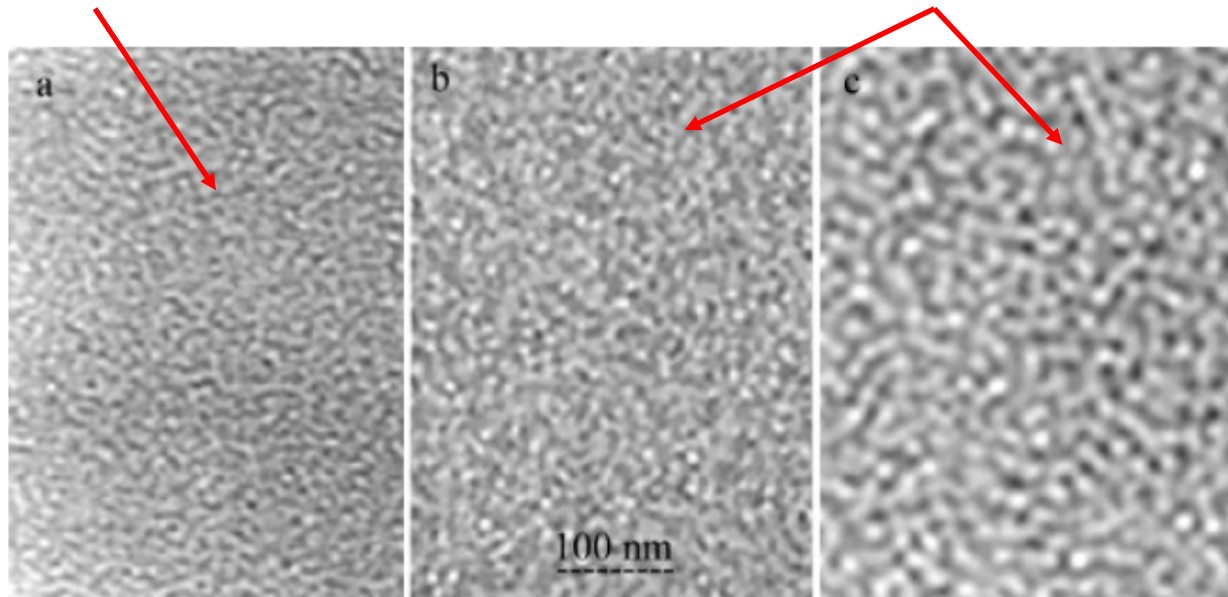


W. Ma *et al.*, *Adv. Funct. Mater.* **15**, 1617 (2005).

Morphology control

The interpenetrating networks are not well developed.

The morphology of interpenetrating networks becomes clearer and easily visible.



TEM images of P3HT:PCBM film bulk morphology before thermal annealing(a), after thermal annealing at 150 °C for 30 min(b), and after thermal annealing at 150 °C for 2 h(c).

Mobility

With increasing annealing time

➡ Mobility ↑ (improved charge separation and transport due to the phase separation between P3HT and PCBM).

However, a large extent of phase separation

➡ reduces the bicontinuous phases ⇒ mobility↓ again

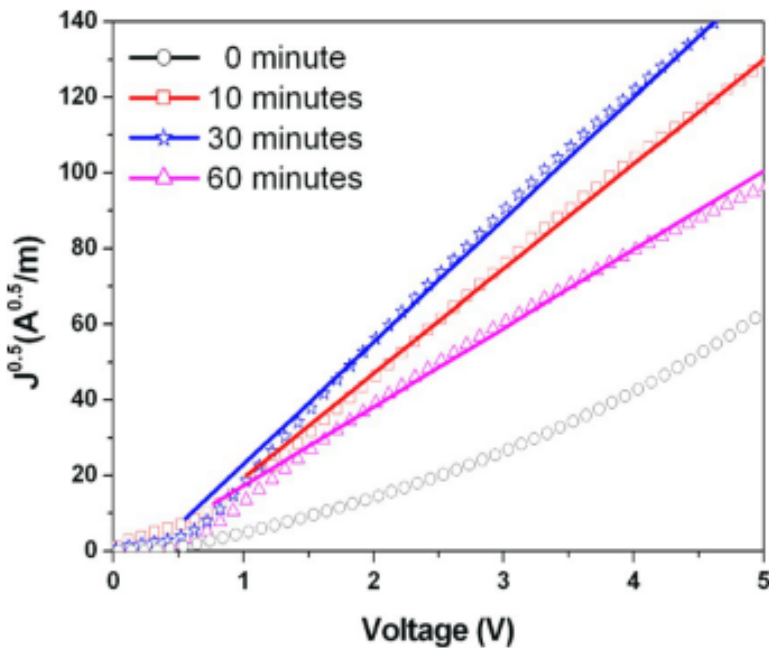


TABLE I. Mobility and performance of the P3HT/PCBM solar cells under A.M. 1.5 illumination (100 mW/cm²) annealed at 140 °C for different times.

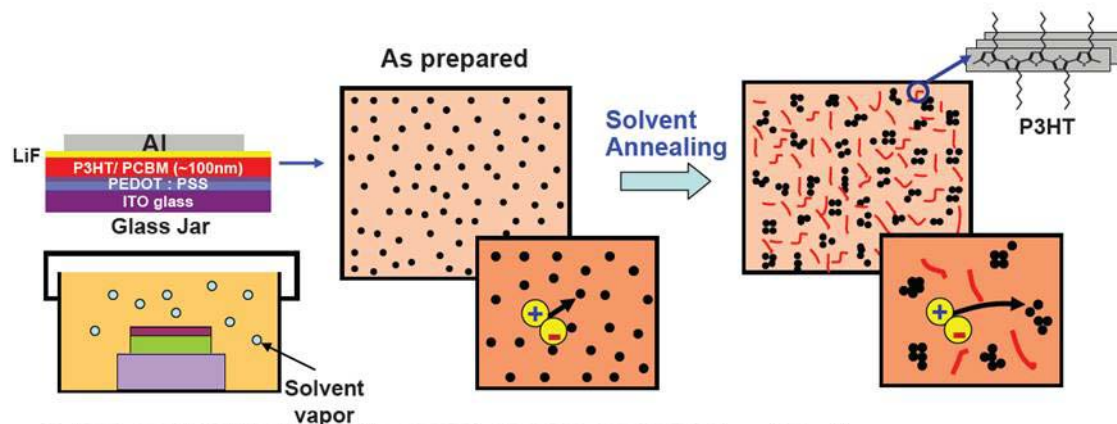
Annealing time (min)	V_{oc} (V)	J_{sc} (mA/cm ²)	FF (%)	η (%)	Mobility (cm ² /V s)
0	0.58	6.72	27.14	1.06	2.51×10^{-5}
10	0.62	10.02	42.32	2.61	2.01×10^{-3}
30	0.64	11.15	54.27	3.85	2.64×10^{-3}
60	0.59	5.06	44.90	1.35	1.02×10^{-3}

increase



decrease

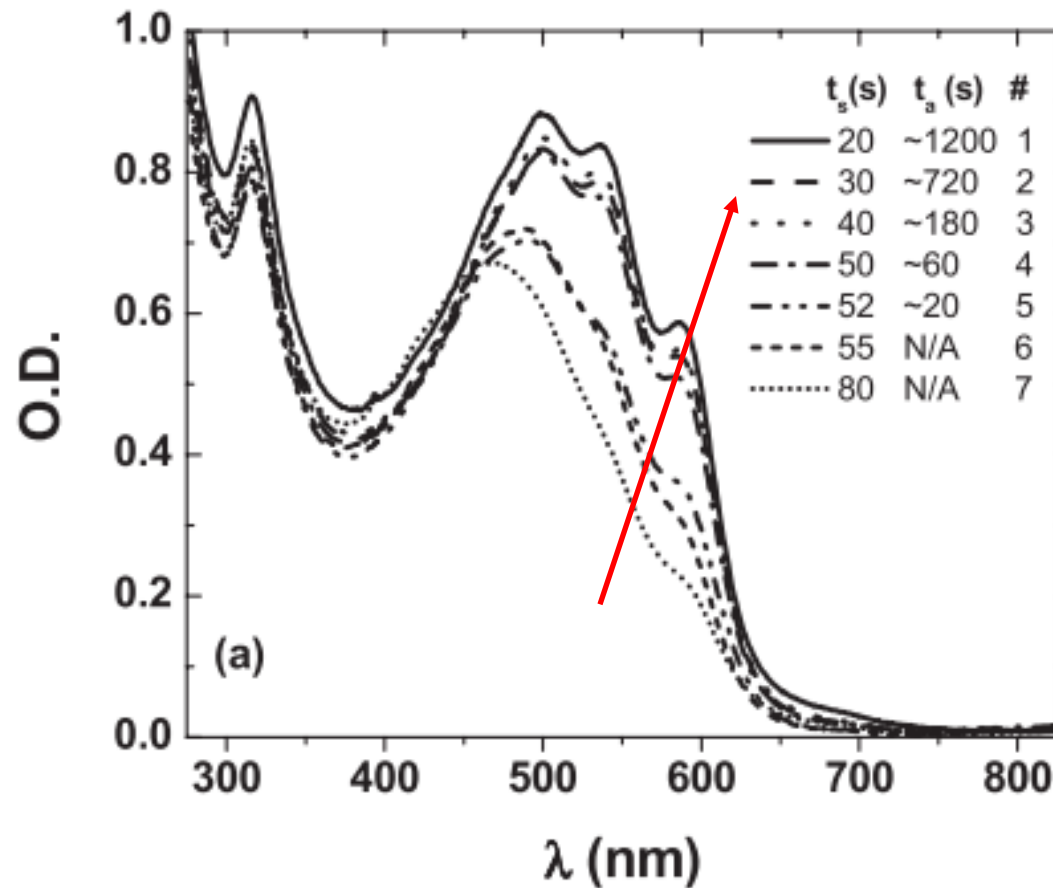
The Concept of Solvent Annealing



- enhanced light absorption and charge transport $\rightarrow \eta_p \uparrow$
 - decrease of interfacial area where excitons dissociate
 - decrease of exciton diffusion efficiency
- } Exciton Loss $\rightarrow \eta_p \downarrow$
- \rightarrow Optimum solvent annealing condition (solvent type, annealing time)

The solubility and volatility of annealing solvent have a substantial effect on the degree of nanoscale phase separation of photoactive organic films. By controlling solubility and vapor pressure of annealing solvent, we can optimize morphology and molecular ordering of solar cells

Absorption



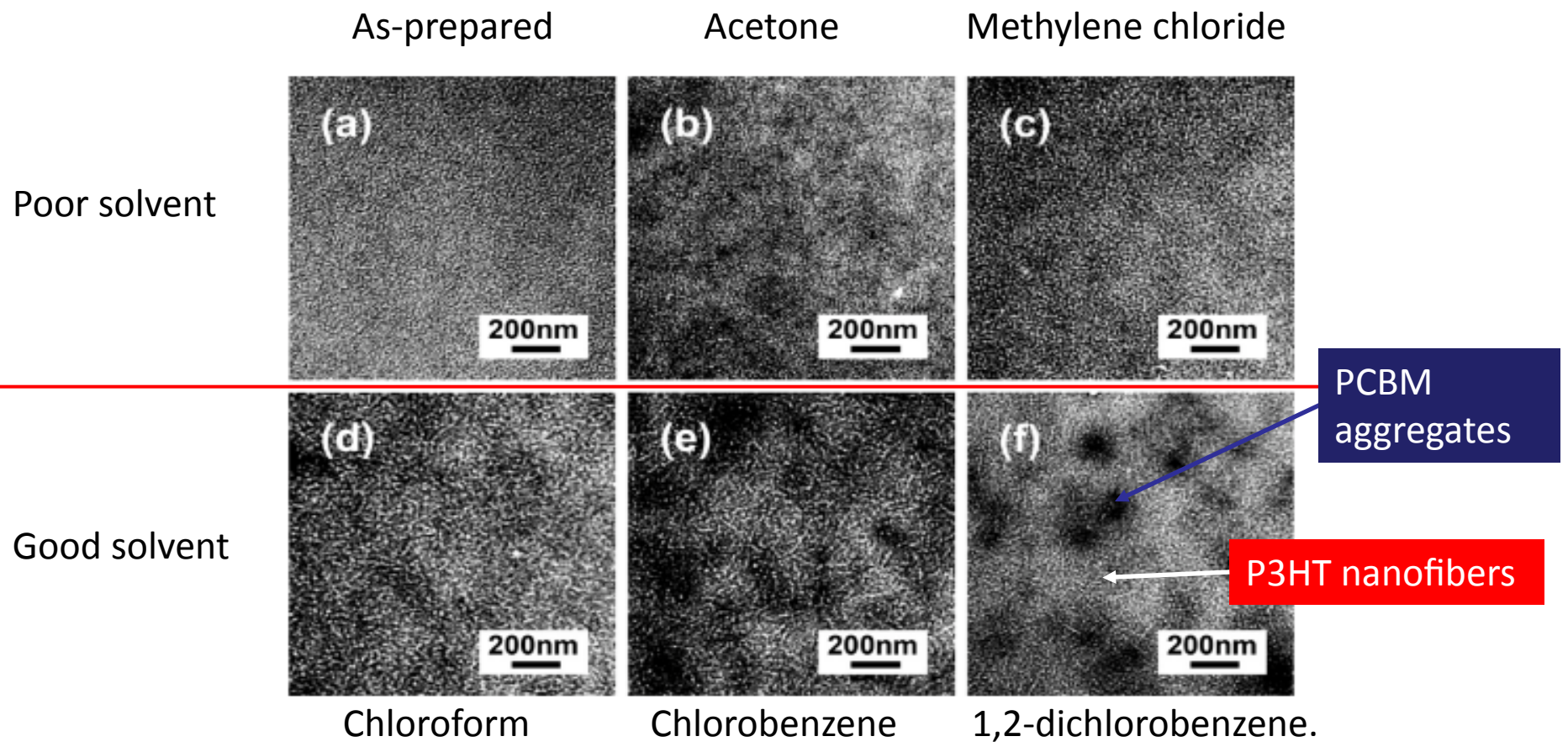
Solvent annealing
time ↑

Vibronic shoulder ↑

t_s : spin-coating time
 t_a : solvent annealing time

Morphology Controlled by Solvent Properties

(investigated by TEM)



Morphology Controlled by Solvent Properties

(investigated by AFM)

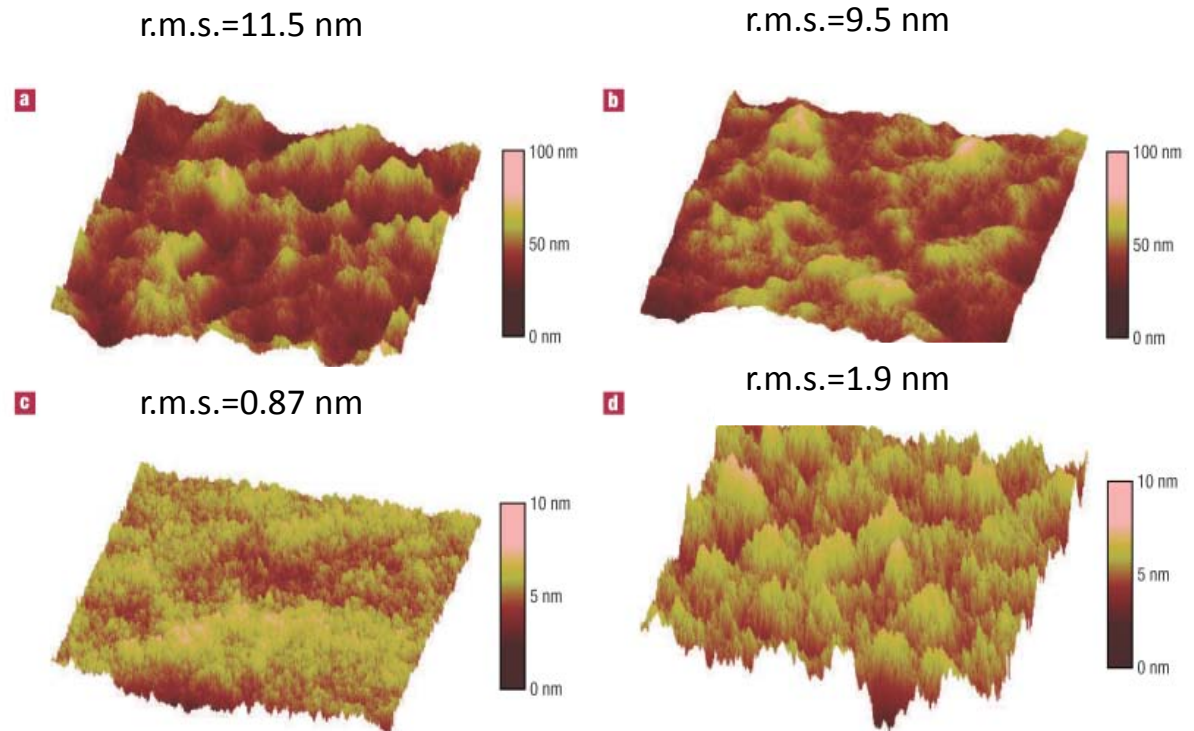
Slow grown



Rough surface
(nanoscaled
texture → internal light
scattering and light
absorption ↑)



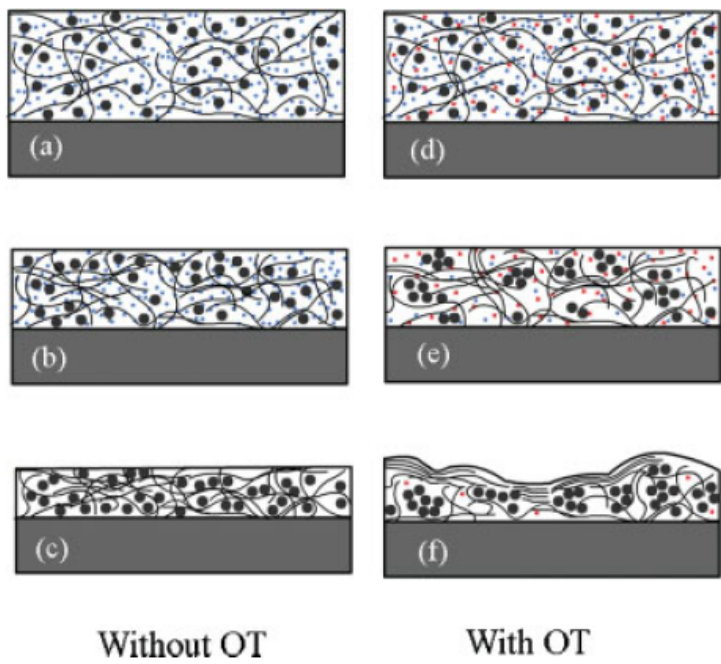
Jsc ↑



(a) Slow-grown film before thermal annealing. (b) Slow-grown film after thermal annealing at 110 °C for 10 min. (c) Fast-grown film before thermal annealing. (d) Fast-grown film after thermal annealing at 110 °C for 20 min.

The Concept of Solvent Additives

The addition of solvent additives provides the similar function of preserving P3HT crystallinity in P3HT:PCBM blend as achieved in the “solvent annealing” approach.



DCB evaporate much faster than OT during spin-coating, and gradually the concentration of OT increases in the mixture.

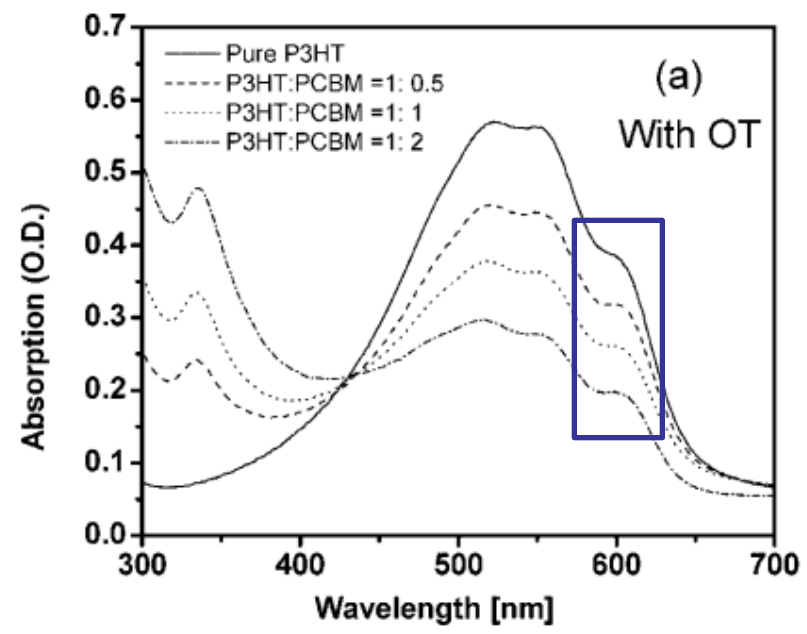
Due to the limited solubility of PCBM in OT, PCBM form clusters and precipitate. With a smaller amount of PCBM contained in the solution, P3HT chains are able to self-organize in an easier fashion.

Pre-formed PCBM clusters not only provide a percolation pathway for better electron transport, but also enable better hole transport in the polymer phase.

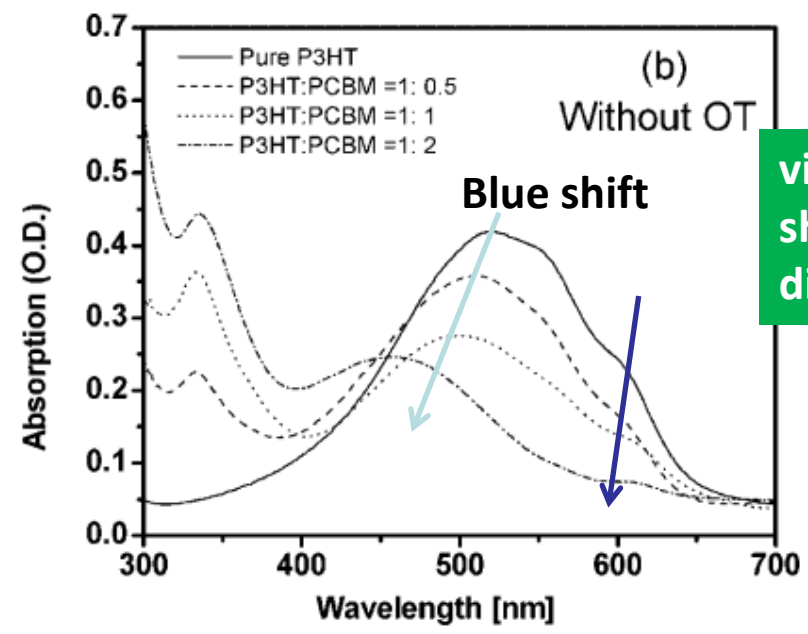
Figure 5. Proposed model during spin-coating process. Black wire: P3HT polymer chain; Big black dots: PCBM; blue dots: DCB molecules; and red dots: 1,8-octanedithiol molecules. (a–c) correspond to three stages in the spin-coating process when DCB is the sole solvent; (d–f) correspond to three stages in the spin-coating process when octanedithiol is added in DCB. Note the difference of PCBM distribution in the final stage of each case, (c) and (f). The total numbers of big black dots are same in all the images.

Solvent	Boiling points [°C]	Vapor pressure at 30 °C [Pa]	PCBM solubility [mg ml ⁻¹]
1,2-dichlorobenzene (DCB)	198	200	100
1,8-octanedithiol (OT)	270	1	19
di(ethylene glycol)diethyl ether	189	100	0.3
N-methyl-2-pyrrolidone	229	10	18

Absorption



With additives
➡ obvious vibronic shoulder



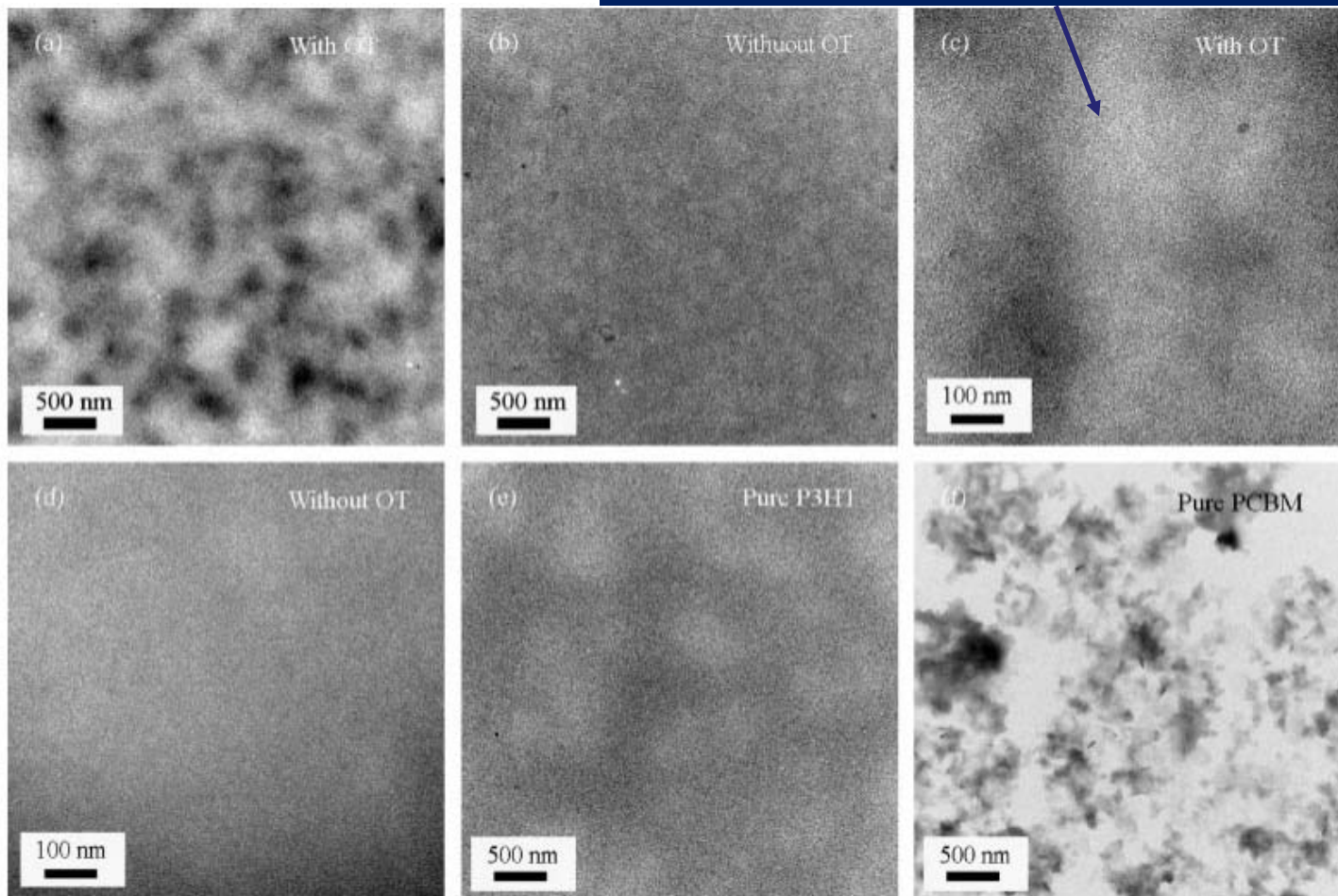
w/o additives
➡ vibronic shoulder diminish

vibronic
shoulders
diminish

Morphology

(investigated by TEM)

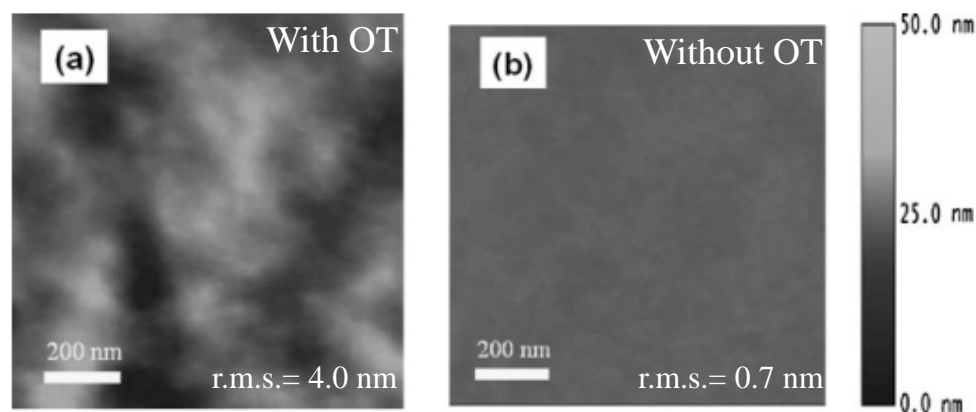
Pronounced fibrillar P3HT crystals (c) suggest the crystallinity has been improved compared to pristine film (d).



Morphology

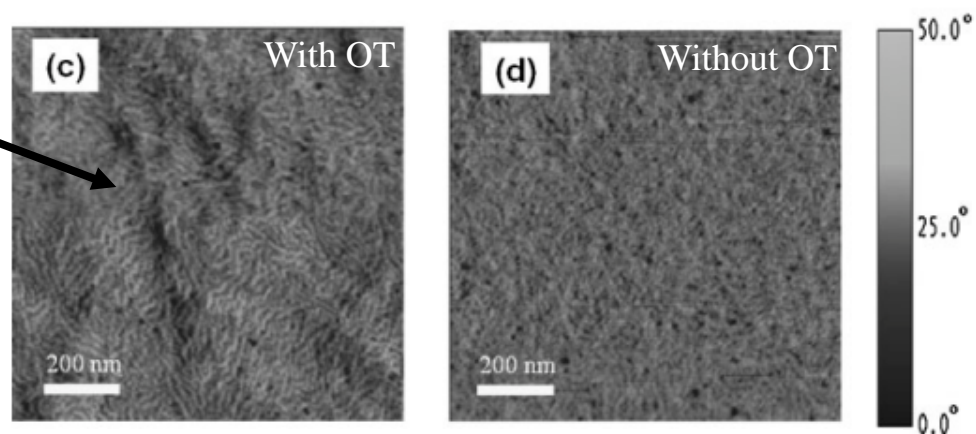
(investigated by AFM)

Height image



P3HT
fibrillar
crystalline
domains

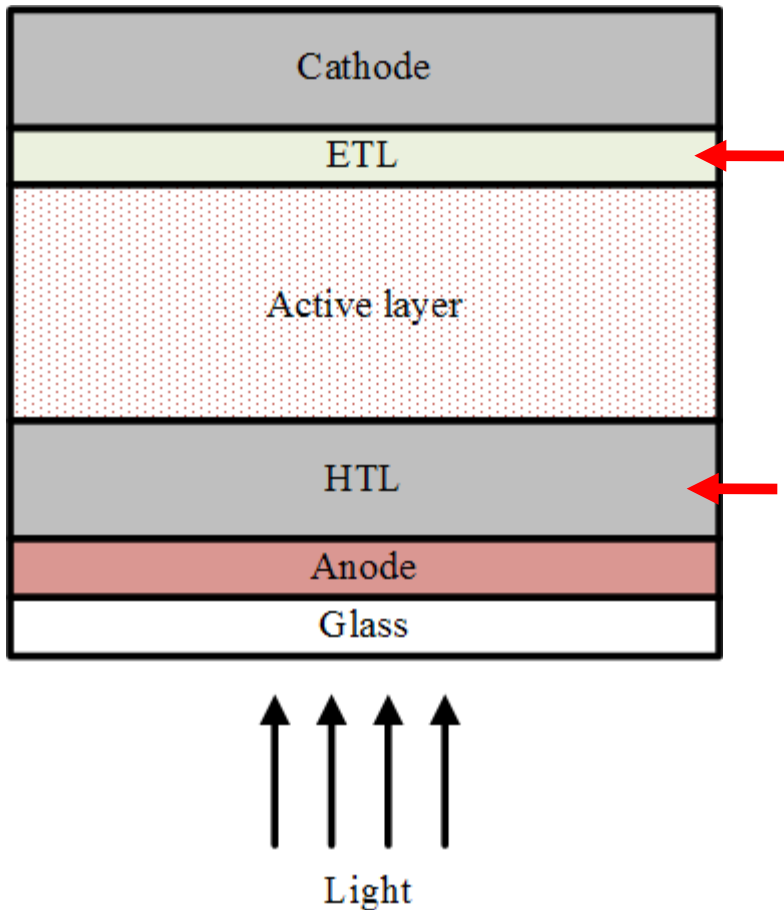
Phase images



A rough surface is a “signature” of high efficiency solar cells both in “thermal annealing” and “solvent annealing”.

Highly ordered P3HT chain alignment is achieved when OT is added in the mixture.

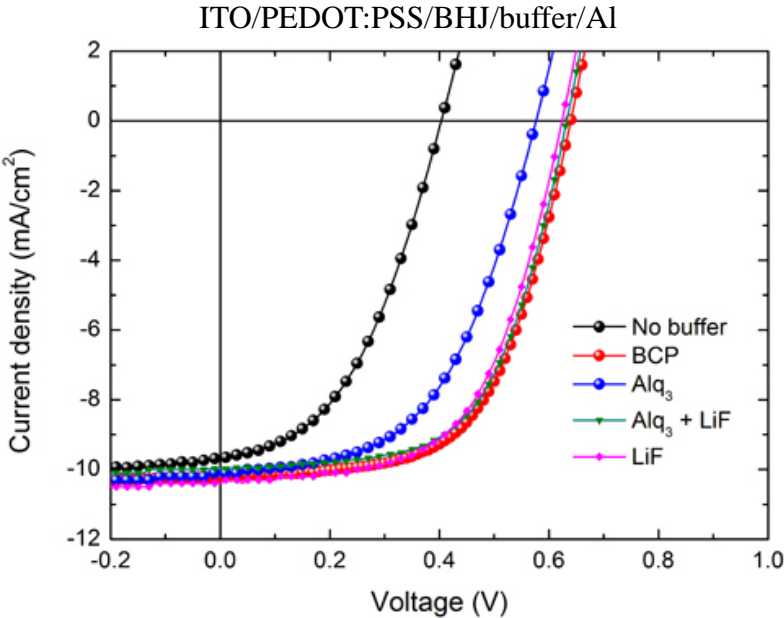
For organic solar cell-



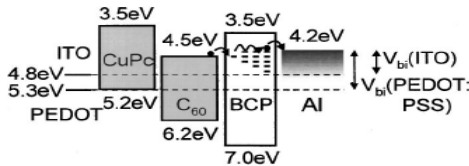
Functions-

1. To prohibit the electron transfer from metal to active layer
 - a desired built-in electric field
 - promote the free carrier collection
 2. To prevent excitons/hole from recombining at cathode
-
1. To improve the hole transporting from active layer to anode
 2. To prevent excitons/electron from recombining at anode

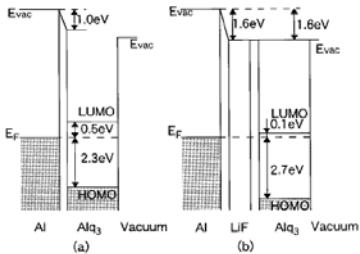
Cathode Buffer Layer - BCP



P. Peumans and S. R. Forrest, *Appl. Phys. Lett.* **79**, 126 (2001).

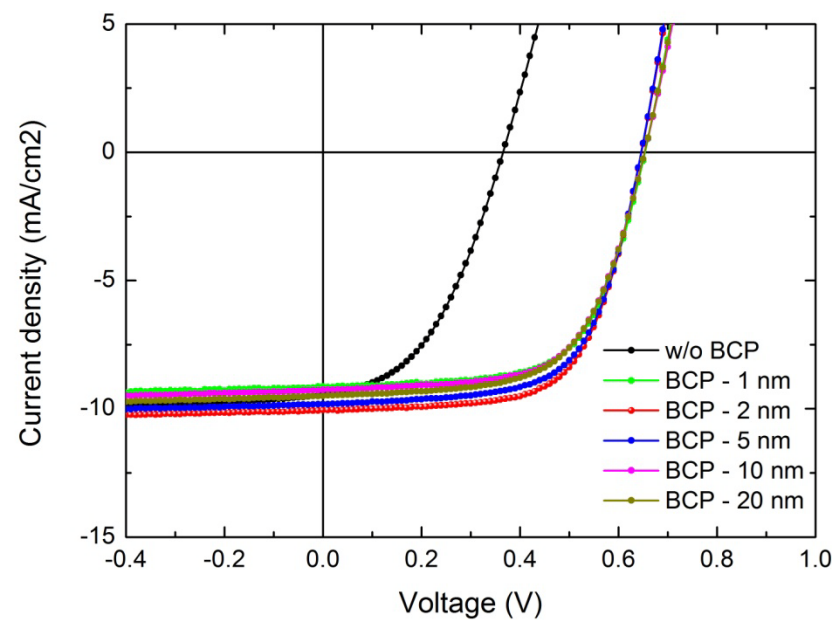


T. Mori, *Appl. Phys. Lett.* **73**, 2763 (1998).



	V _{oc} (V)	J _{sc} (mA)	FF (%)	eff (%)	R _{sh} (kΩ)	R _s (Ω)
w/o buffer	0.41	9.7	44	1.77	9.27	643
BCP (2 nm)	0.64	10.1	60	3.89	35.95	207
Alq ₃ (2 nm)	0.59	10.1	53	3.18	23.68	316
Alq ₃ (2 nm) + LiF (1.2 nm)	0.65	10.0	59	3.83	37.43	224
LiF (1.2 nm)	0.64	10.5	58	3.89	31.50	199

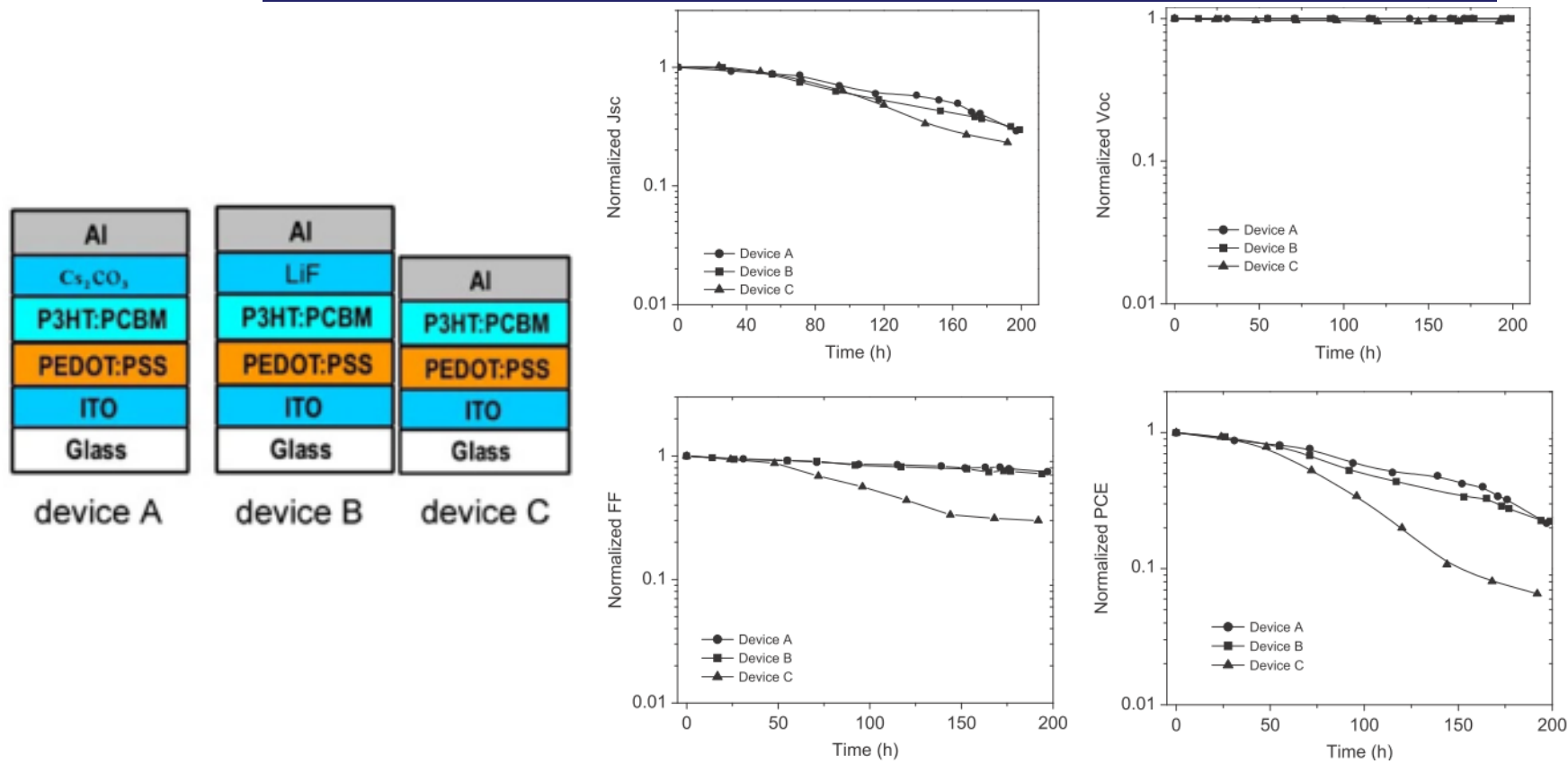
Optimizing Polymer Solar Cells with BCP Buffer Layers



	Voc (V)	Jsc (mA/cm ²)	FF (%)	eff (%)	Rsh (kΩ)	Rs (Ω)
w/o BCP	0.38	9.54	44	1.63	8.59	449
BCP – 1 nm	0.65	9.85	62	3.91	37.34	174
BCP – 2 nm	0.65	9.96	63	4.11	41.68	173
BCP - 5 nm	0.65	9.89	63	4.03	33.26	154
BCP – 10 nm	0.65	9.29	62	3.74	30.36	191
B CP – 20 nm	0.65	9.38	59	3.59	31.19	219

Cathode Buffer Layer – Cs_2CO_3

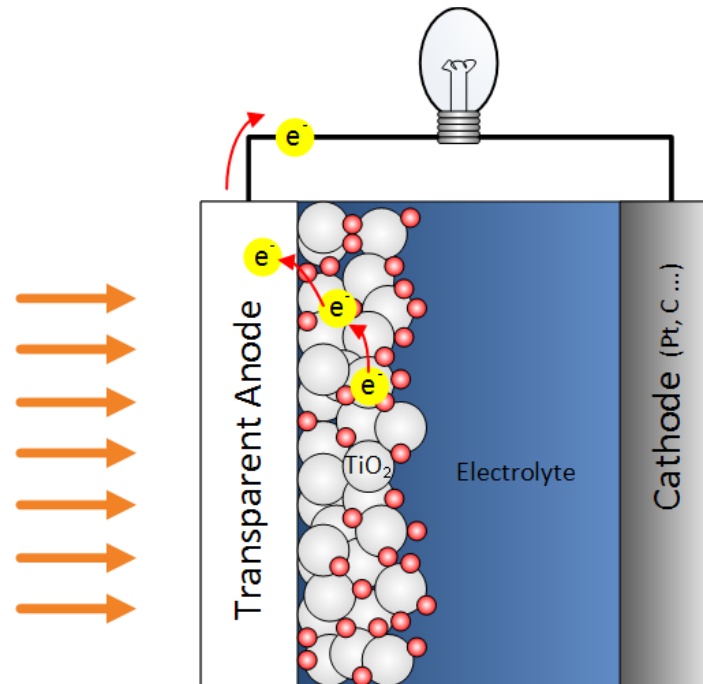
Cs_2CO_3 decomposed into metallic Cs during thermal evaporation. This interfacial material tends to react with oxygen and moisture. Cs_2CO_3 buffer layer works as an excellent shielding and scavenging protector.



Device A with half-life of 130 h gets a 33% improvement compared with the control device B with half-life of 100 h. 76

Other Kinds of OSC

- Dye-sensitized solar cell



Advantages

- Most efficient 3rd generation solar technology
- Work in low-light conditions
- Flexible

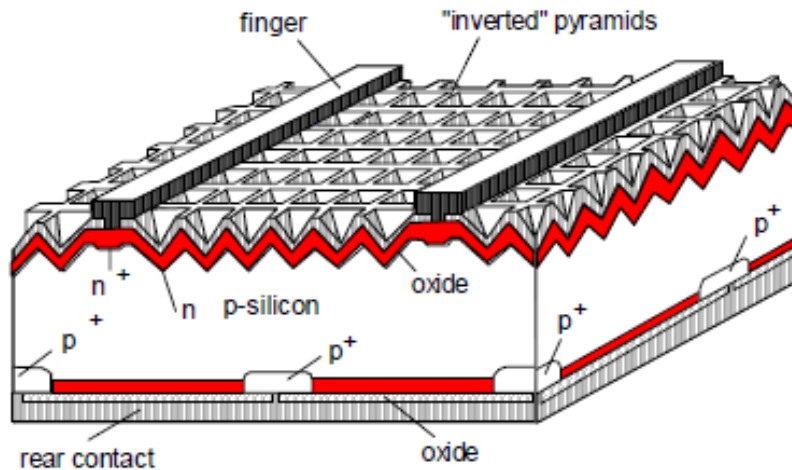
Drawback

- Temperature stability problems
- Encapsulation issue

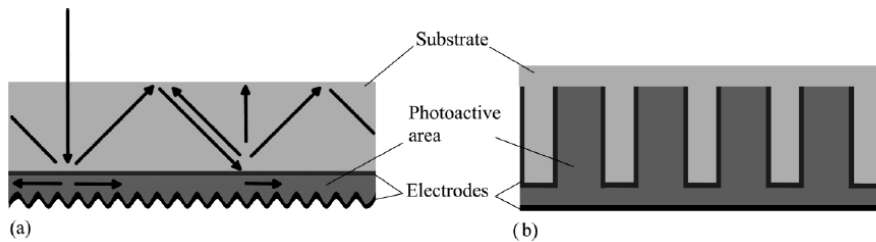
Why Nano?

To Improve Absorption

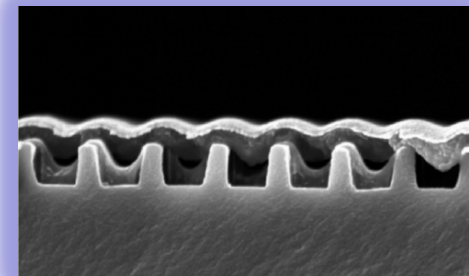
- Anti-reflection coating/layer



Si-based solar cell



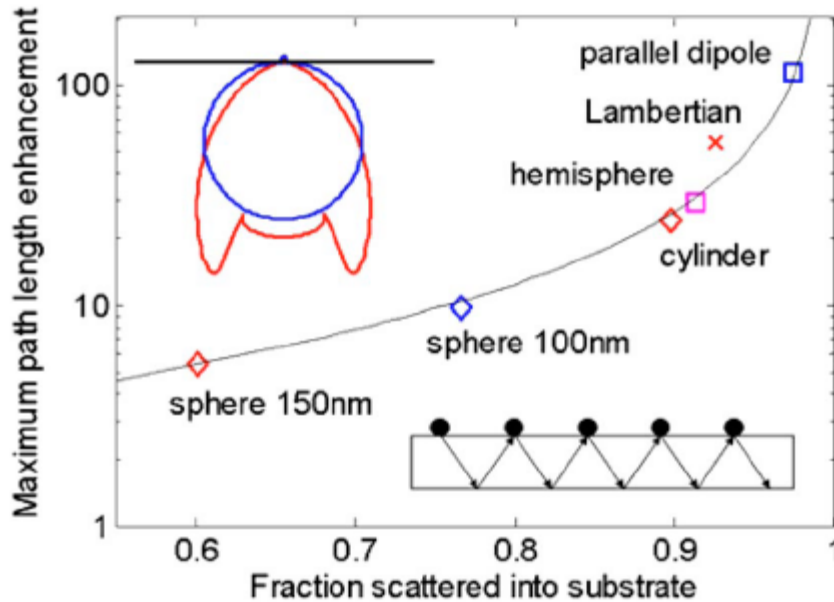
Cell-concepts of organic solar cells. (a) Light trapping with diffraction gratings; (b) buried nano-electrodes



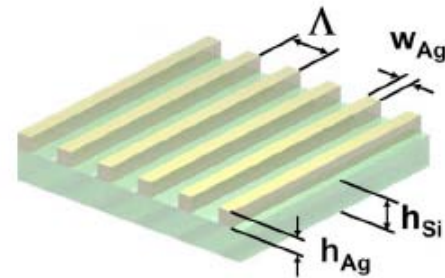
To Improve Absorption

- Surface plasmon resonance (SPR)

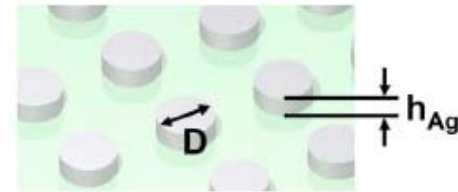
giant near-field enhancement and the enhanced scattering cross section upon exciting localized plasmon polaritons



K. R. Catchpole^a and A. Polman^b, *Appl. Phys. Lett.* **93**, 191113 (2008).



Grating



Nanostructure

C. Rockstuhl *et al.*, *J. Appl. Phys.* **104**, 123102 (2008).

To Improve Absorption

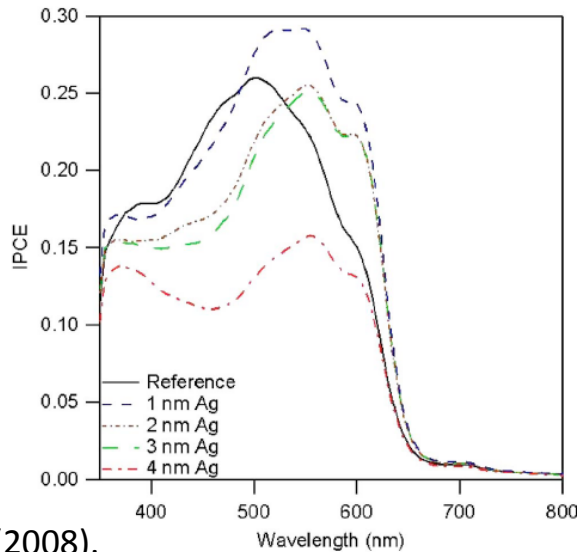
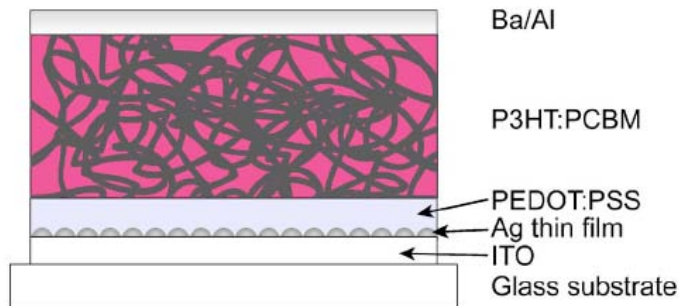
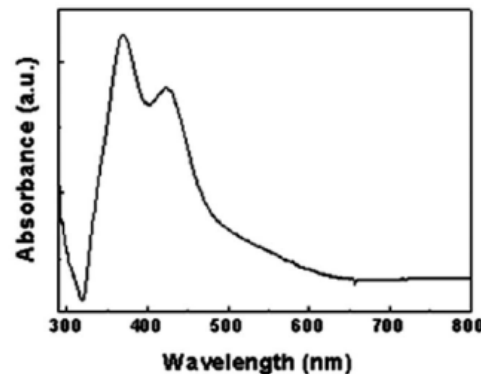
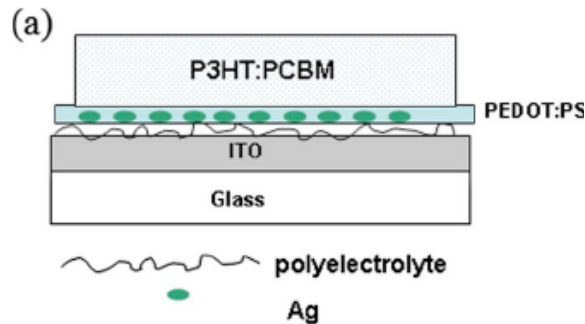


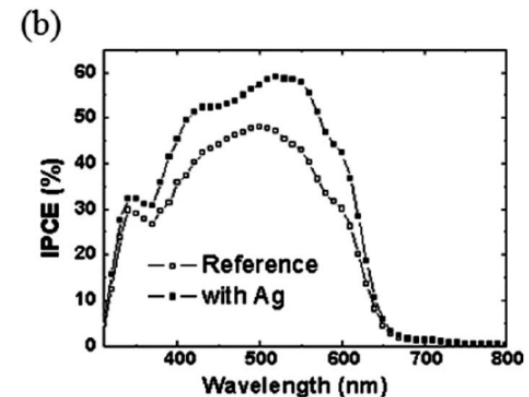
TABLE I. Average device parameters as a function of nominal silver film thickness. Errors reported as one standard deviation.

Ag height (nm)	J_{sc} (mA/cm ²)	η (%)	V_{oc} (mV)
0 (Ref)	4.6 ± 0.4	1.3 ± 0.2	566 ± 5.6
1	6.9 ± 0.2	2.2 ± 0.1	590 ± 5.8
2	7.3 ± 0.3	2.1 ± 0.1	581 ± 8.8
3	6.5 ± 0.1	1.8 ± 0.2	564 ± 30.9
4	2.6 ± 0.4	0.9 ± 0.1	599 ± 6.2

A. J. Morfa *et al.*, *Appl. Phys. Lett.* **92**, 013504 (2008).



3.05% ➔ 3.69%



S. S. Kim *et al.*, *Appl. Phys. Lett.* **93**, 073303 (2008).



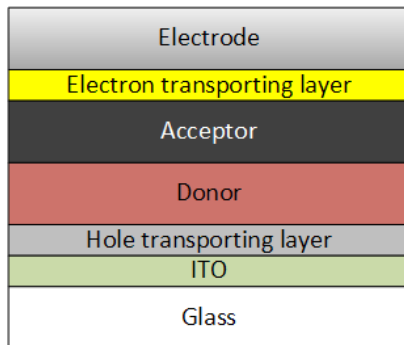
Exciton Diffusion Length

Typically, the diffusion length ~ 10 nm

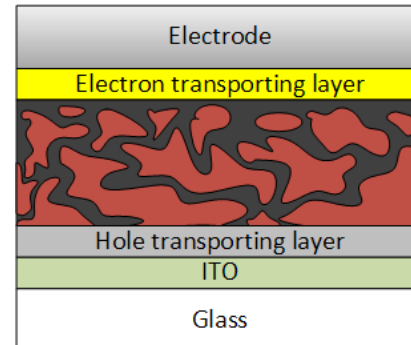
<< absorption length of many of the materials employed in organic photovoltaic device

To solve this issue

➡ Bulk heterojunction

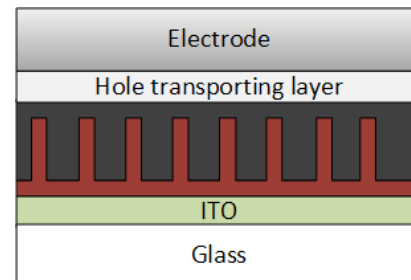


Bi-layer structure



Bulk heterojunction structure

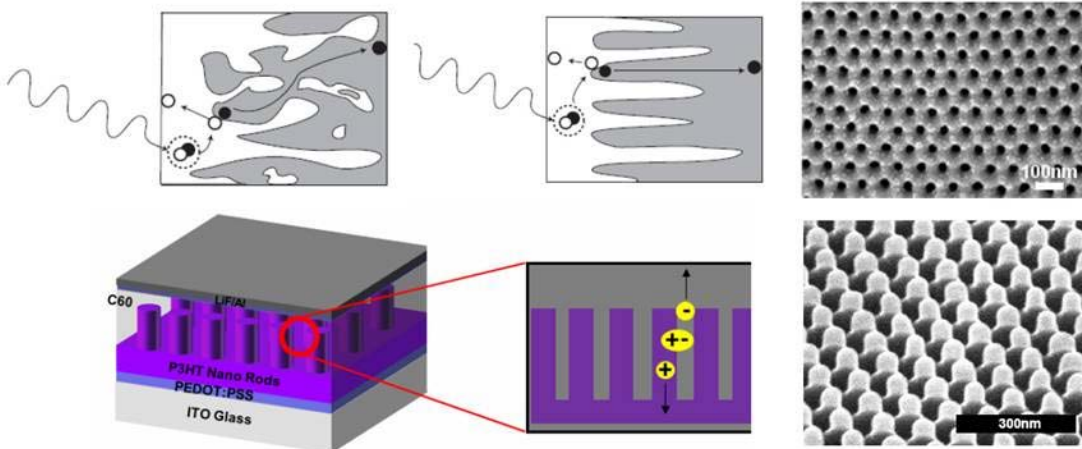
➡ Inter-digitated structure



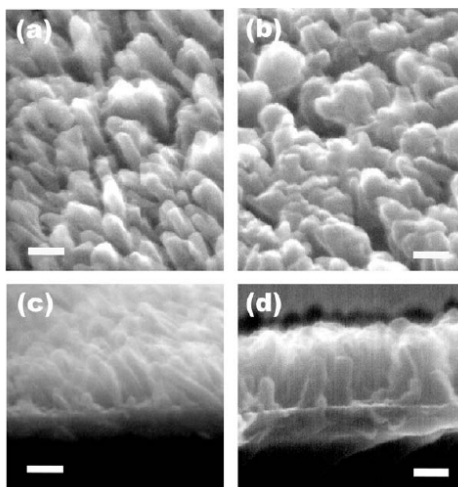
Exciton Diffusion Length

Bulk Heterojunction

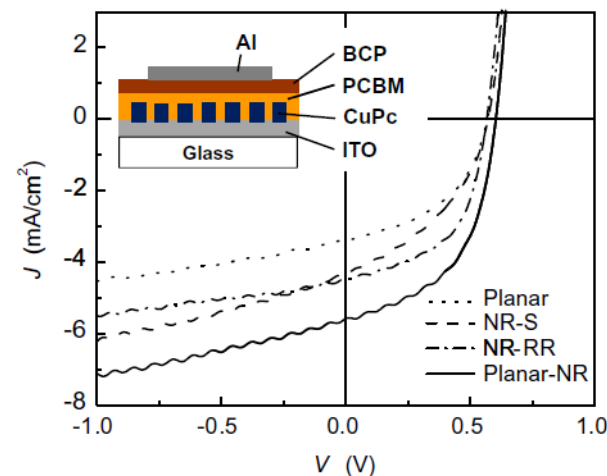
Ordered Bulk Heterojunction



Interdigitated structures also benefit the charge transporting properties



Topographic ((a) and (b)) and cross-sectional ((c) and (d)) scanning electron microscope (SEM) images of CuPc nanorods grown on a stationary ((a) and (c)) or rotational ((b) and (d)) substrate. The scale bar is 100 nm in all four images

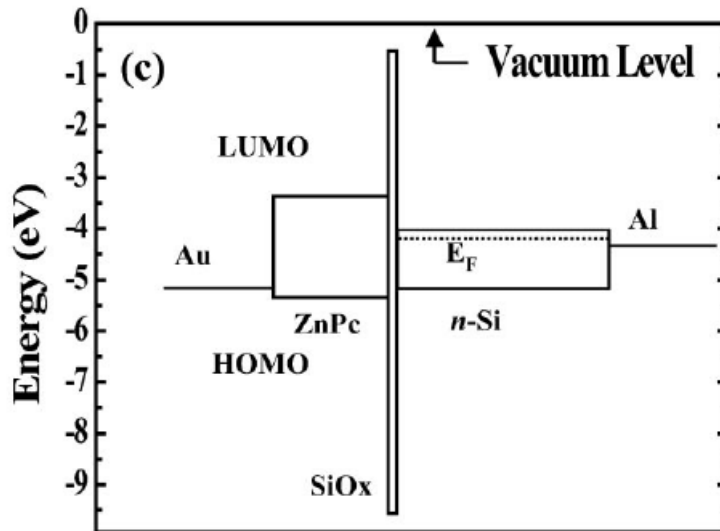


To Improve Charge Separation

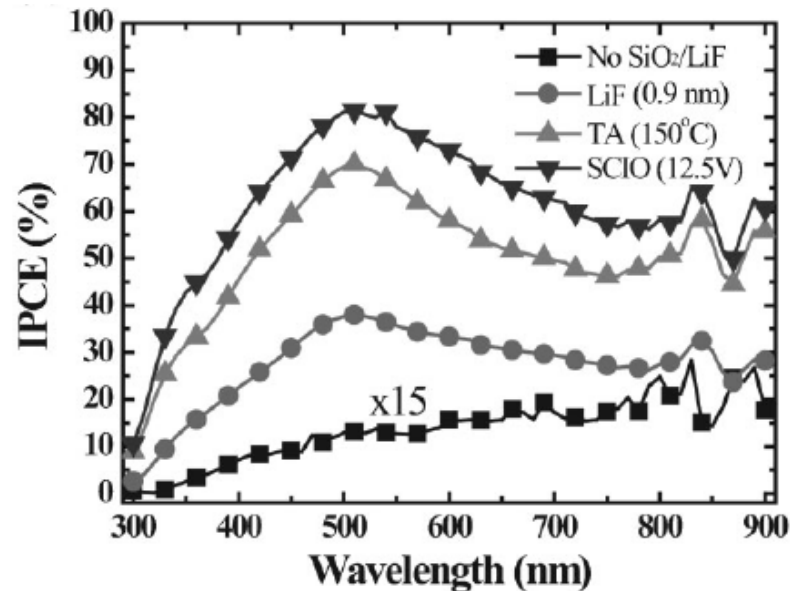
To dissociate electron-hole pairs before recombination

➡ Morphology control (BHJ/interdigitated structure)

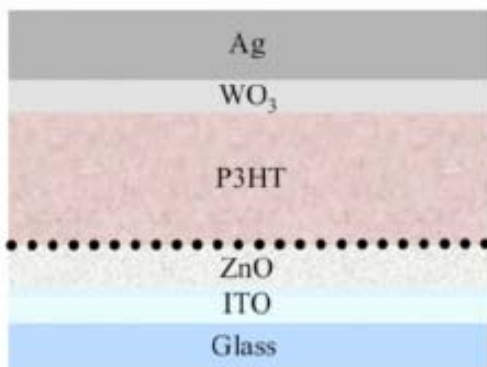
➡ Sieve layer



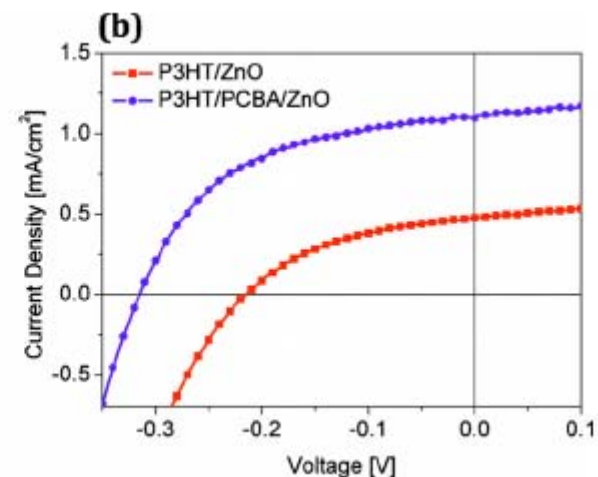
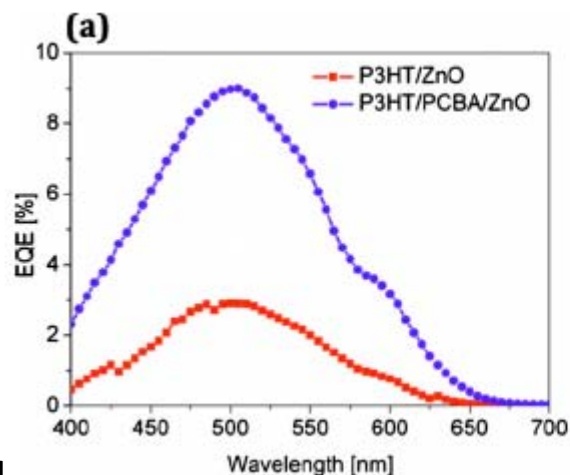
The energy levels of the individual components of the photovoltaic cell



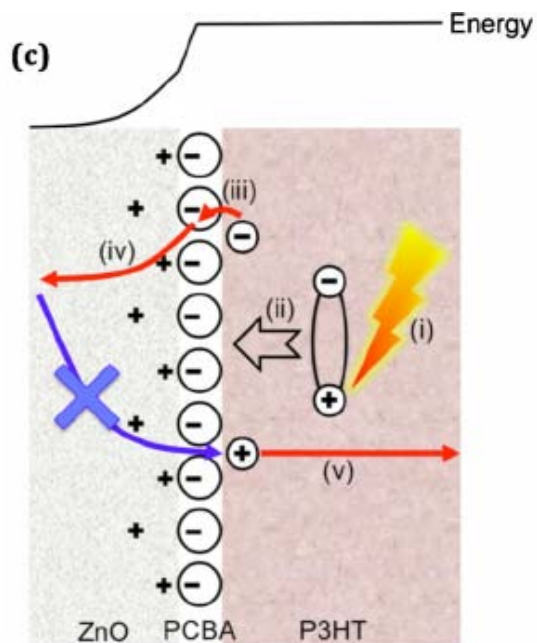
The incident photon-to-current collection efficiency (IPCE) of the device with and without the different electronic sieve layers



Structure of the inverted hybrid PV device and the chemical structure of the PCBA molecule



(a) EQE of inverted hybrid P3HT solar cells on bare ZnO and PCBA/ZnO. (b) I-V curves measured under a solar simulator.



Mechanism of dipole assisted charge separation at the P3HT/PCBA/ZnO interface:

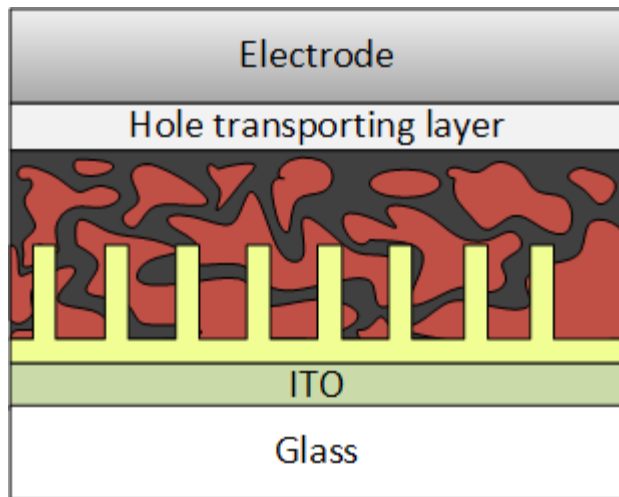
- i excitation
- ii exciton migration to the interface
- iii rapid electron transfer to the PCBA monolayer
- iv interfacial dipole assisted electron collection in the bulk of the ZnO



Hybrid OSC

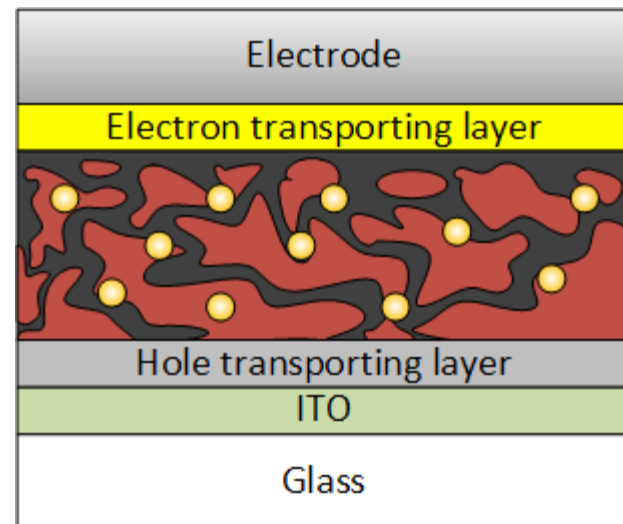
- Organic/Inorganic hybrid solar with nanomaterial/nanostructure

with 1-D nanostructure



- ➡ To increase the interfacial area
- ➡ To enhance exciton dissociation and/or charge collection

with nanomaterial

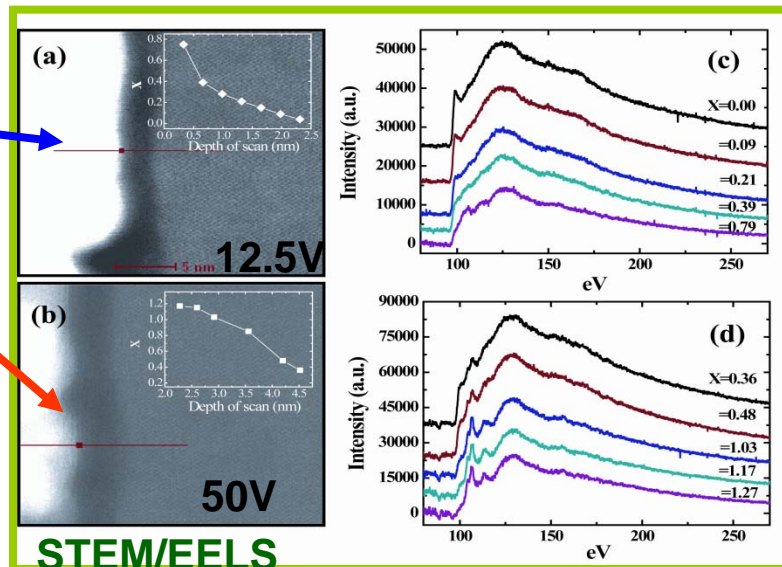
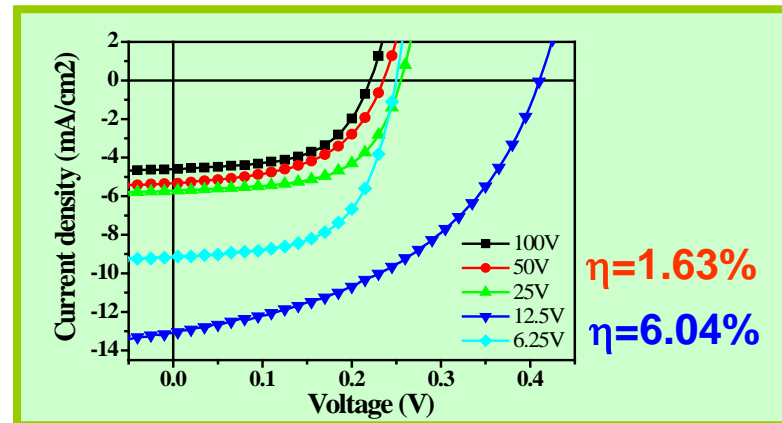
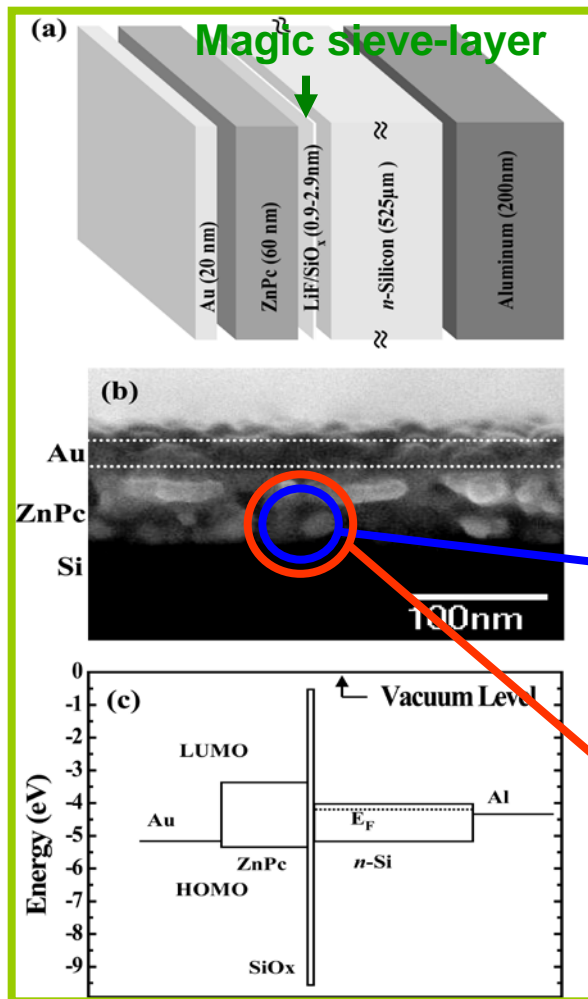


- ➡ To enhance light harvesting

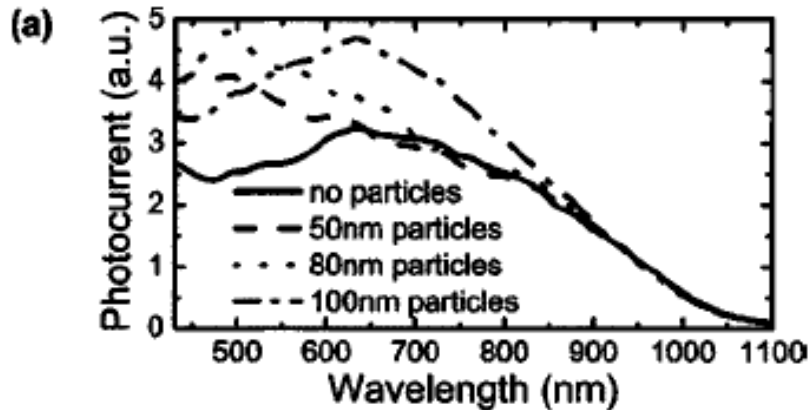
Interface Control is Critical in Hybrid Inorganic-Organic Solar Cells

Enhanced Charge Separation by Sieve-layer Mediation in High Efficiency Inorganic-organic Solar Cell

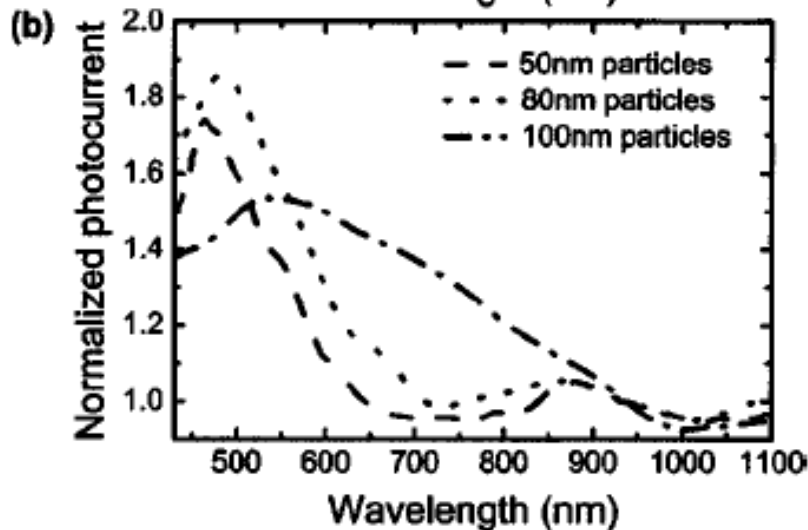
C. H. Lin, et al., *Advanced Materials* 21, 759-763 (2009) & *US Patent* 8,080,824, December 20 (2011)



Nanomaterial - SPR effect



(a) Photocurrent response as a function of illumination wavelength for Si *pn* junction diodes in the absence of nanoparticles, and with Au nanoparticles 50, 80, and 100 nm in diameter.



(b) Photocurrent response spectra for diodes with Au nanoparticles 50, 80, and 100 nm in diameter from part (a), normalized to the photocurrent response measured in the absence of nanoparticles, revealing the increased response arising from the presence of the nanoparticles.

Surface plasmon-induced electromagnetic field

- ➡ increased field amplitude and increased interaction time between the field and the semiconductor
- ➡ to increase absorption of incident electromagnetic energy near the nanoparticle

Other Kinds of OSC

- InGaN and InAlN solar cells

For single III-V semiconductor solar cells

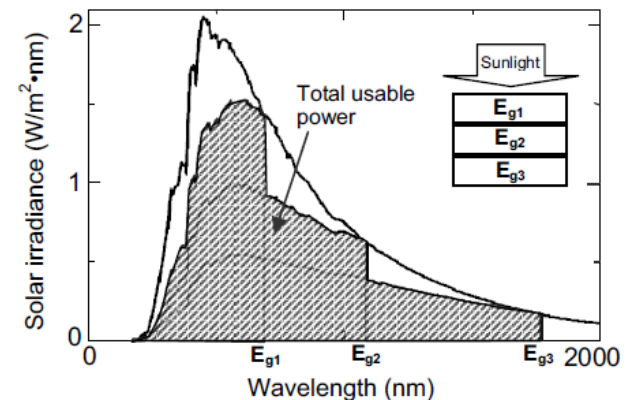
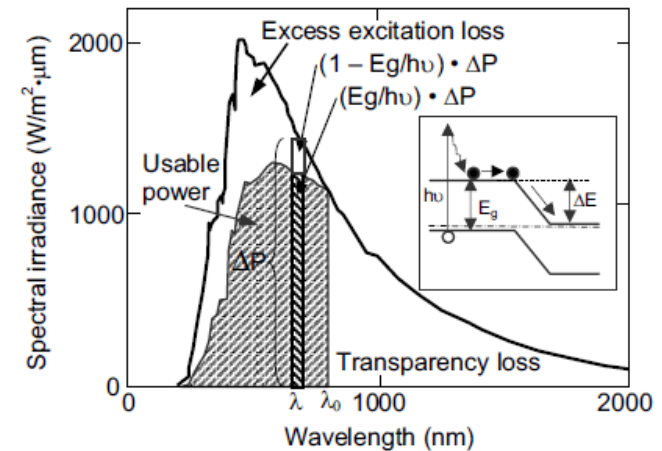
➡ large optical loss



To solve this issue

To fabricate a multi-junction tandem solar cell, where sub-cells composed of a different band-gap material

Current generated in each sub-cell should be matched (current matching) ➡ limit the efficiency

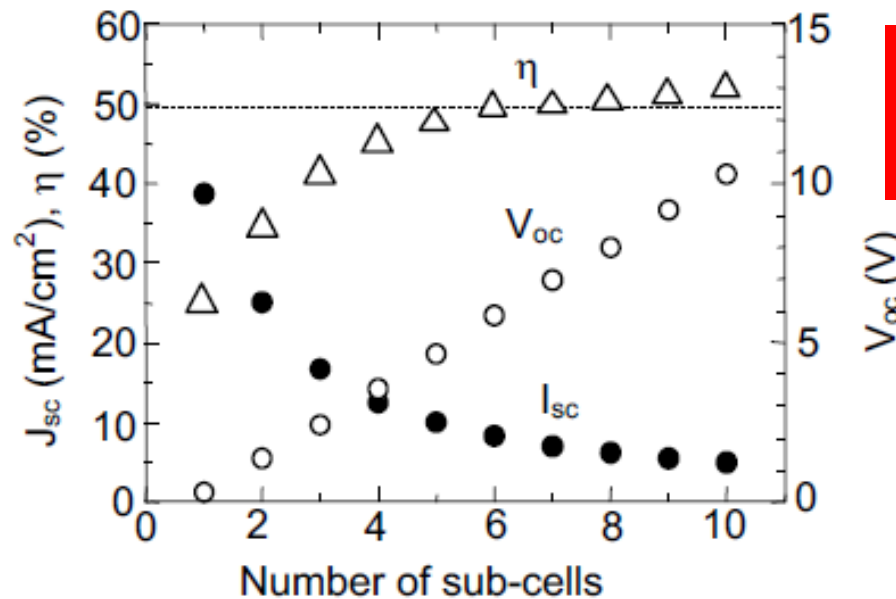


Potential and Status of InGaN and InAlN Solar Cells

- Band-gap of InGa(Al)N can be adjusted from 0.7 to 2.5 eV by changing only the composition .

- ➡ Current matching will be easily achieved using InGa(Al)N system
(A current generated in each sub-cell is assumed to be the same)

- ➡ Multi-junction tandem cell (sub-cells > 4) is possible



Efficiency > 50% !!!
(theoretically)

Expected output performance for multi-junction tandem cells with a different number of sub-cells

Applications of InGaN

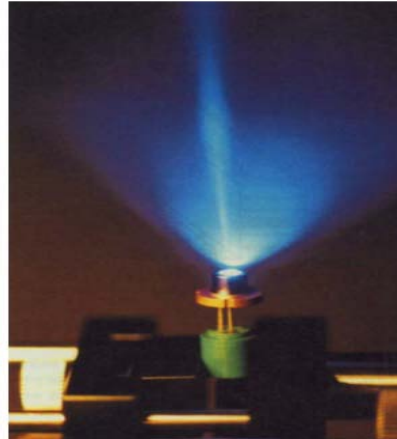
Blue LEDs



Photodetector



Laser Diode



Solar Cell



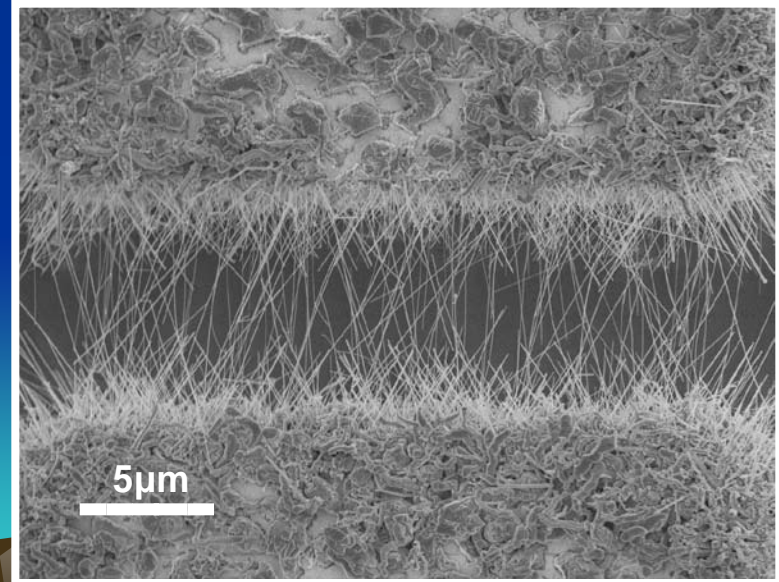
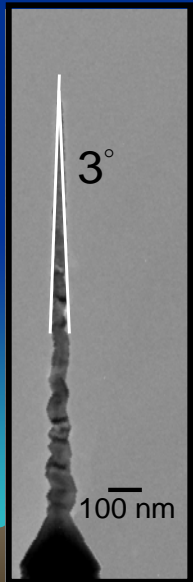
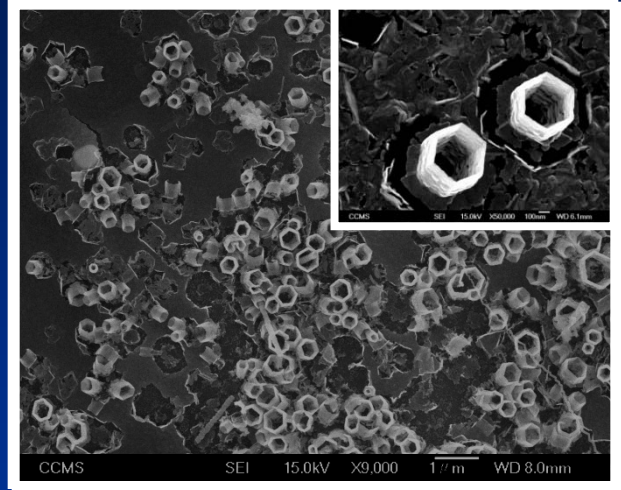
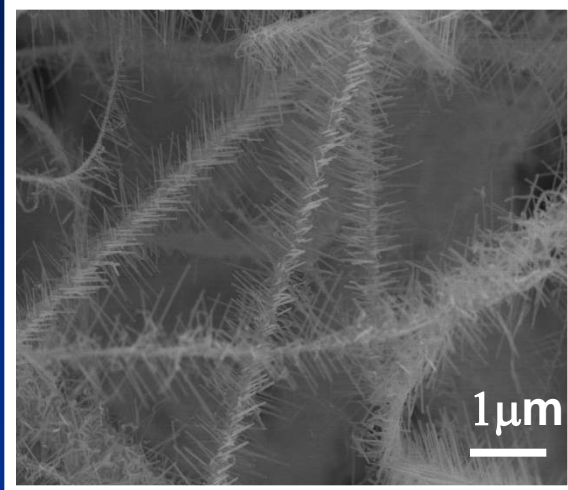
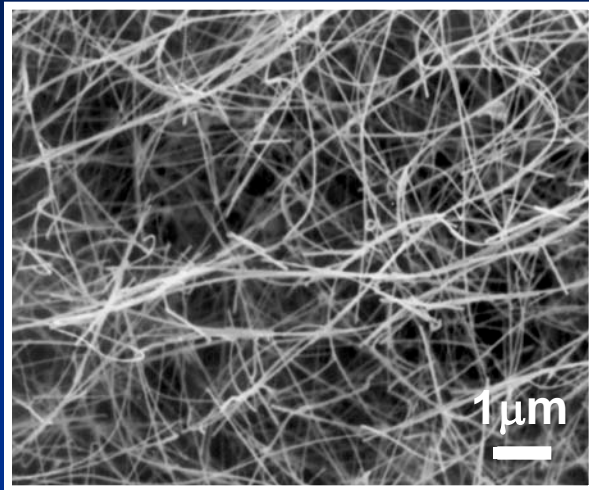
Challenge for InGaN growth and applications

- Phase separation

- ➡ reduces the V_{oc} of the solar cell

- ➡ recombination $\uparrow \rightarrow$ decreasing the photocurrent

Splendid Nitride Nanostructures



Motivation & Rational

III-N, a rapidly growing/maturing industry,
mostly thin film based, but why 1D?

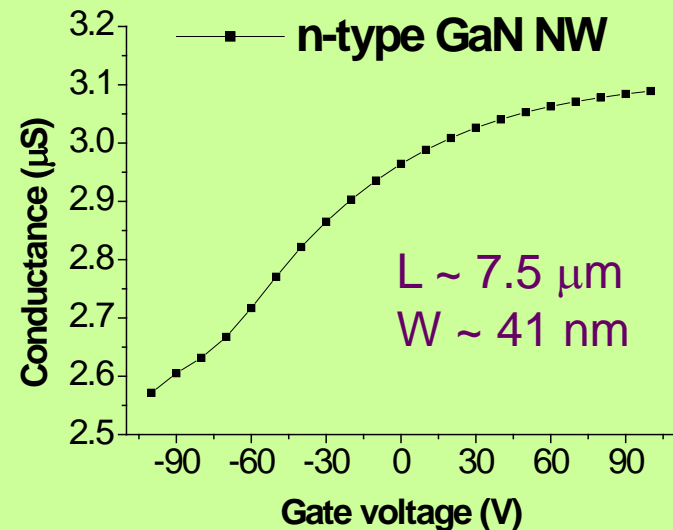
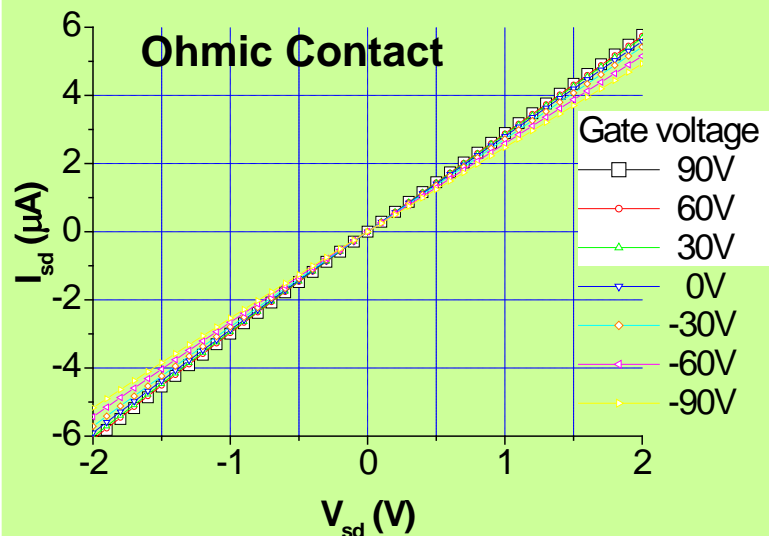
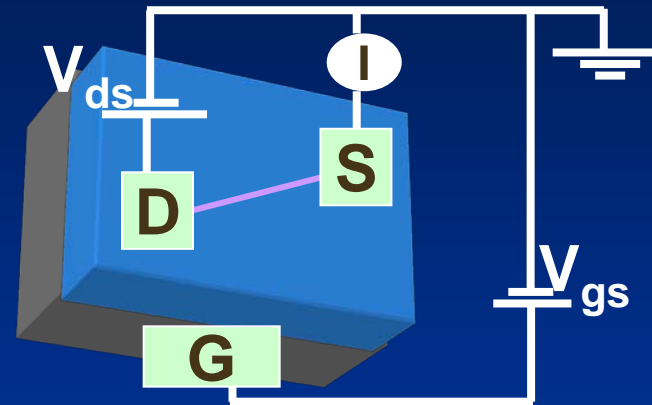
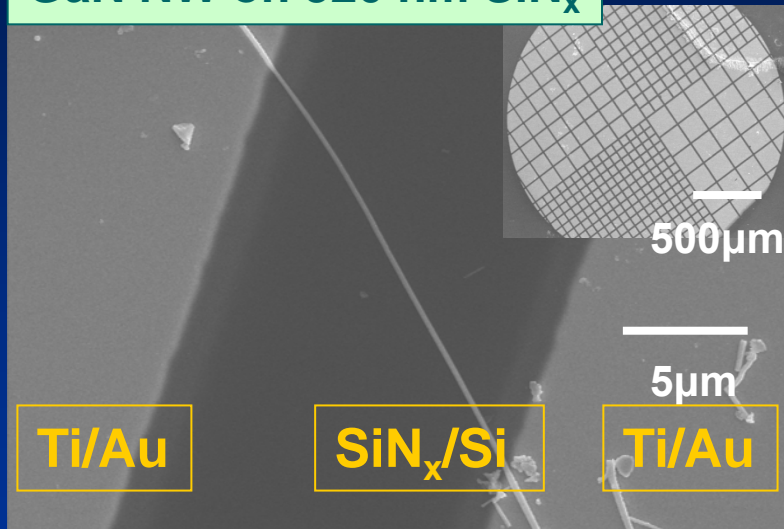
- The extended family of 1D nanostructures
What makes them distinct from thin film or QD?
- Size-dependent optical & transport properties
- Control in size, site, shape & orientation (S^3O)
How about S^3O -distribution tolerant devices?
- On-chip fabrication for integrated devices
- Applications beyond optoelectronics

Bio-compatible & Corrosion-resistant



Single GaN Nanowire FET

GaN NW on 320 nm SiN_x



Toward Chip-process of Nanowire Devices

from

Single Nanowire

Size-, site-, shape- & orientation-controlled device

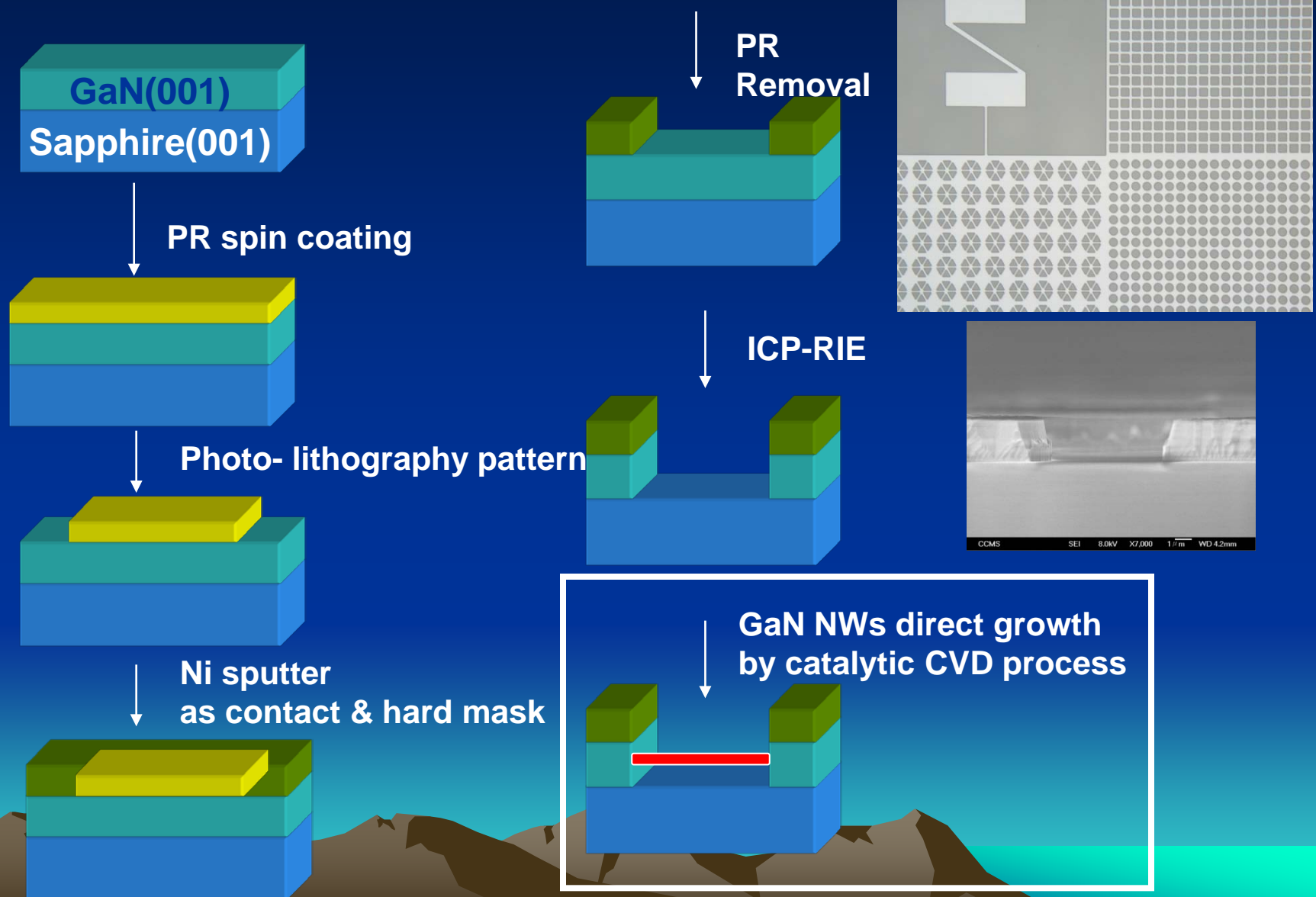
to

an Ensemble of Nanowires

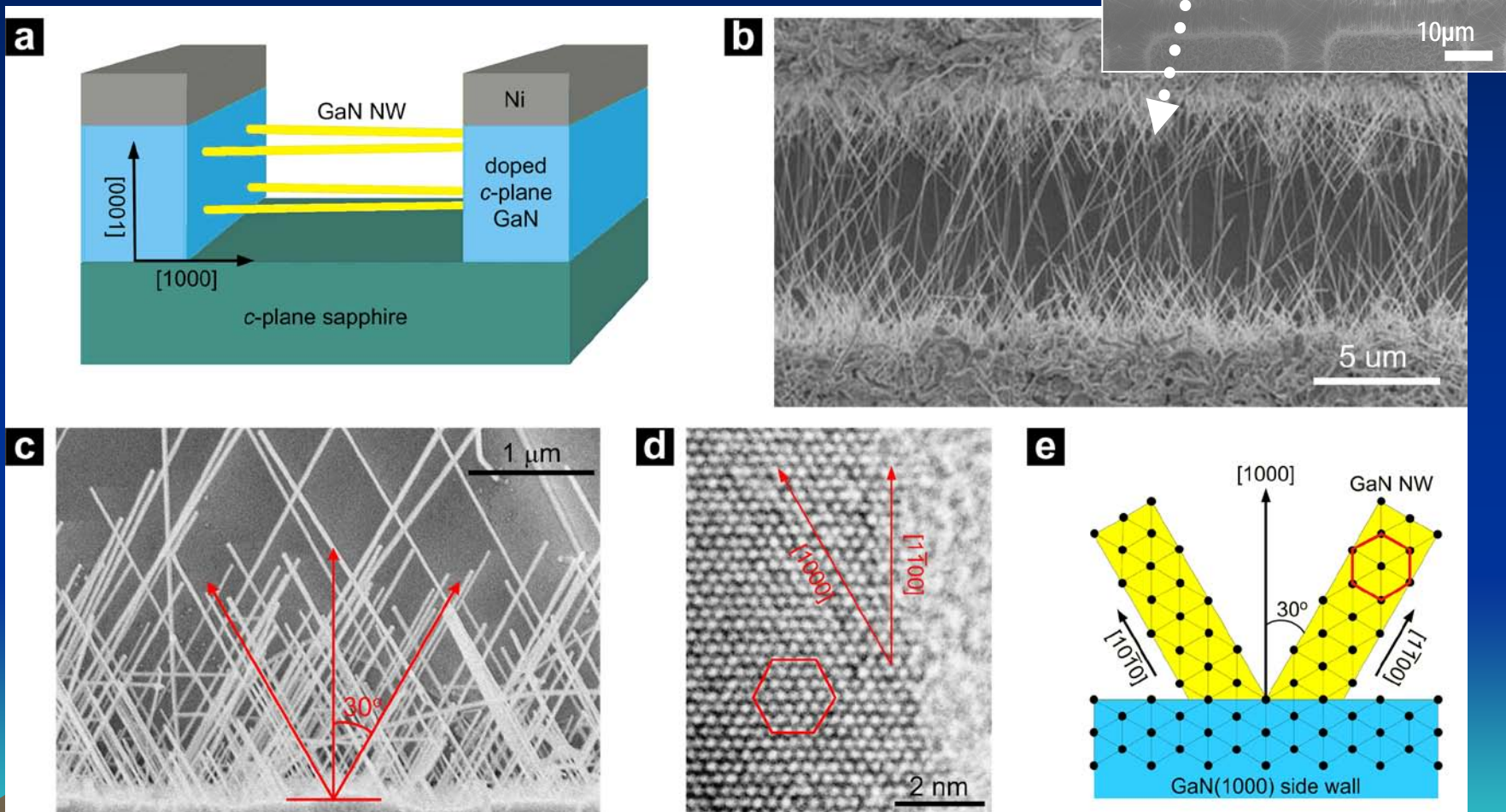
S³O-distribution tolerant devices



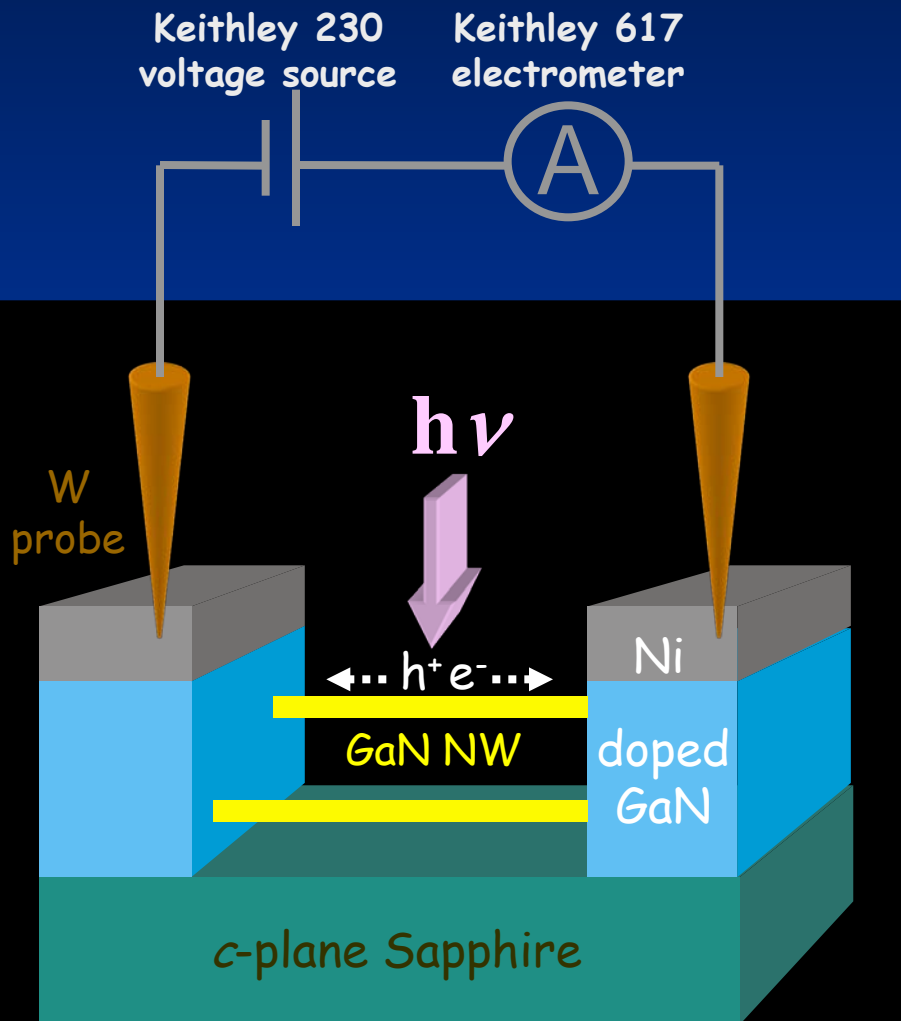
Fabrication of M-S-M Device



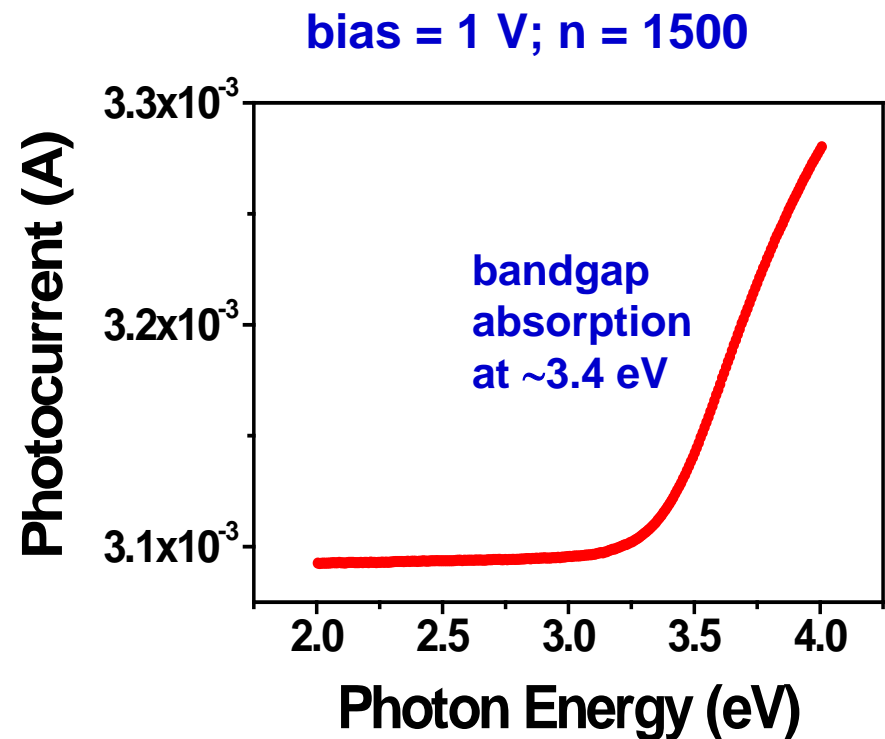
Epi-GaN NWs M-S-M Structure



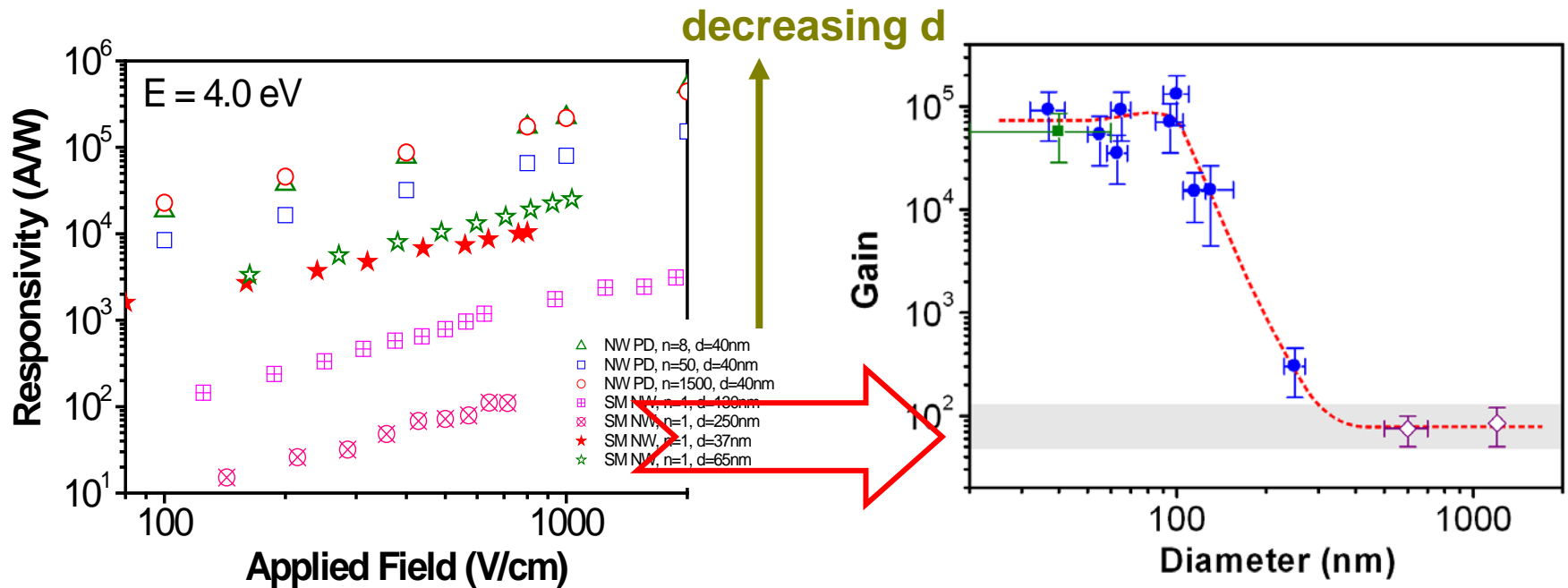
Photoconductivity (PC) Measurement of GaN Nanowires



PC spectrum of GaN NWs



Size-dependent Photoconductivity of GaN NW-bundles and Single-wire



$$R = \frac{\Delta i}{P}$$

photon energy

$$\text{gain } \Gamma = \frac{E}{e \times \eta} \times R$$

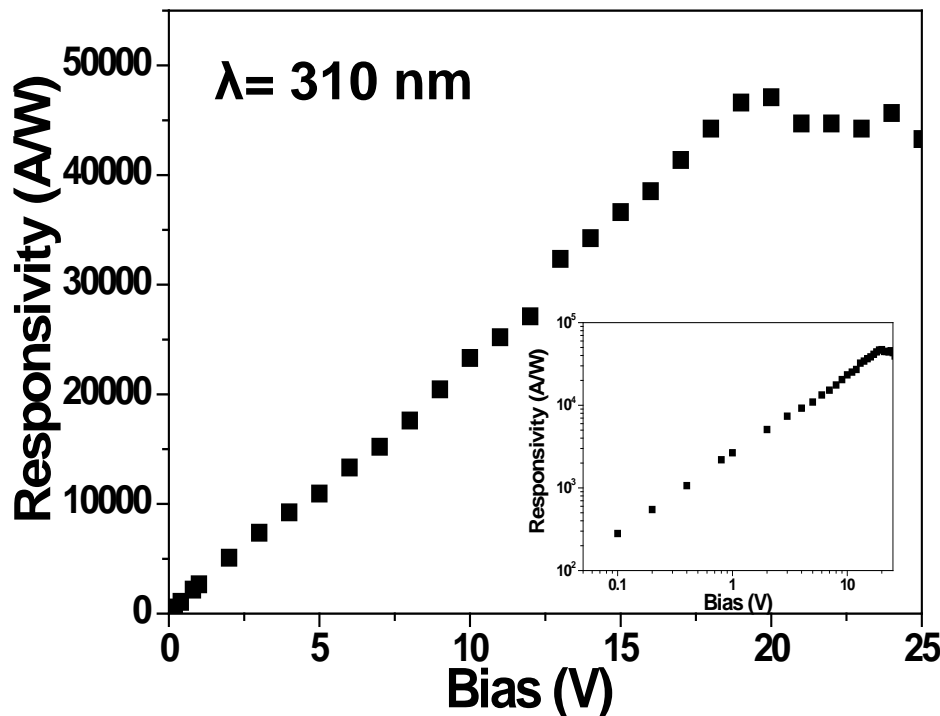
electron charge quantum efficiency

responsivity

Small 4 (2008) 925
APL 95 (2009) 143123

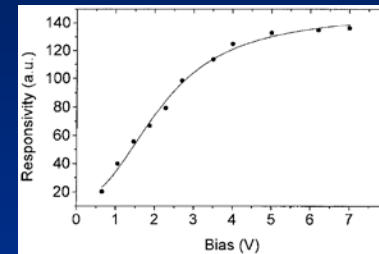
Comparison of Responsivity between the Nanowire and Thin Film Detector

Epi-GaN NWs



Maximum responsivity of 50,000 A/W was obtained at 18V bias

GaN Thin film



Jpn. J. Appl. Phys. Vol. 38 (1999) pp. 767–769

Max $R = 133 \text{ A/W}$ at 5V bias

App. Phys. Lett., Vol. 77, No. 3, 17 July (2000)

Max $R = 6.9 \text{ A/W}$ at 5V bias

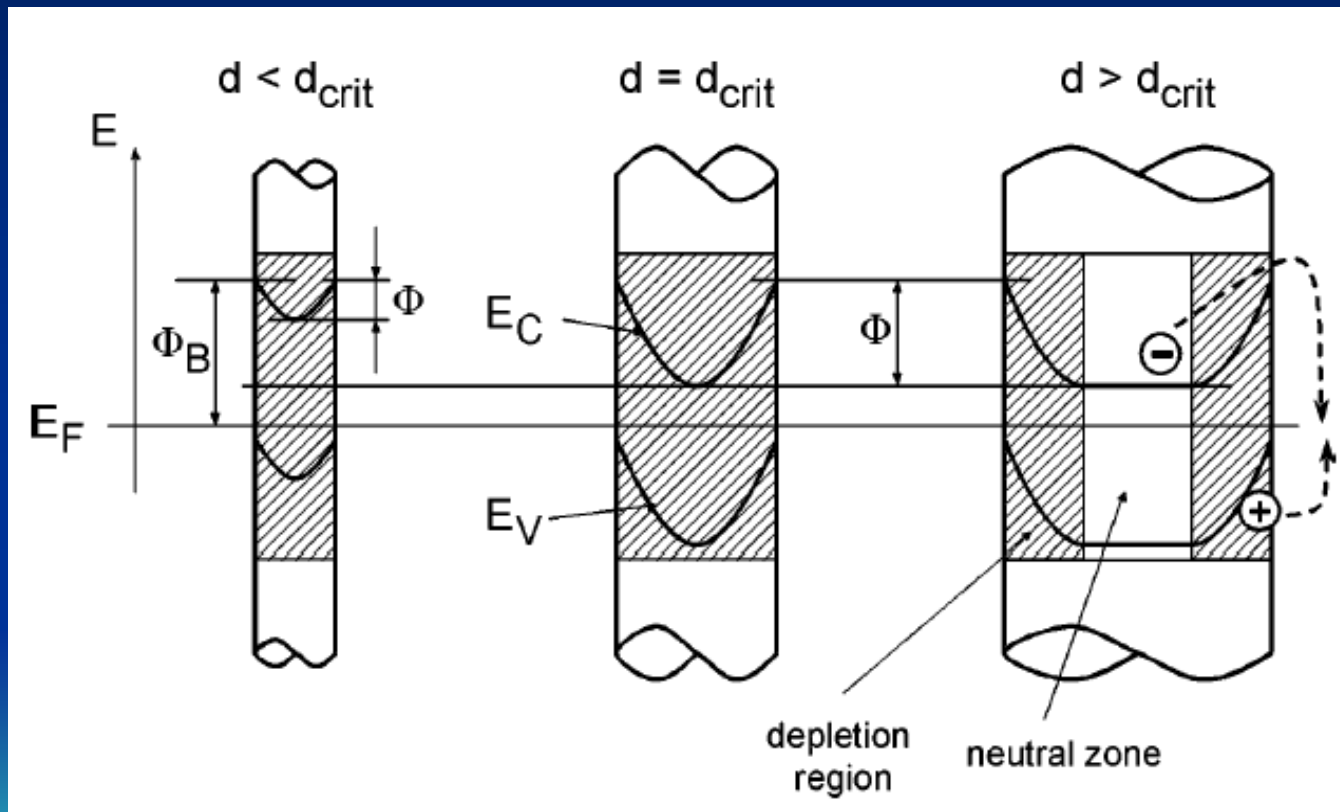
Inter. J. Mod. Phys B, Vol. 16, Nos. 28&29 (2002)

Max $R = 2.53 \text{ A/W}$ at 7V bias

J. Vac. Sci. Technol. B 19(1), Jan/Feb (2001)

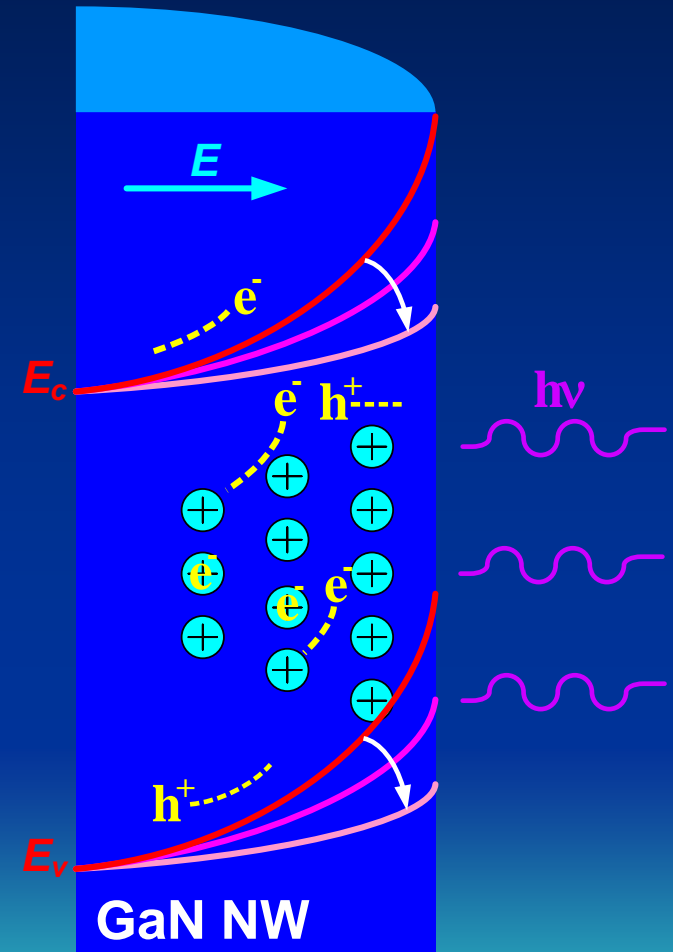
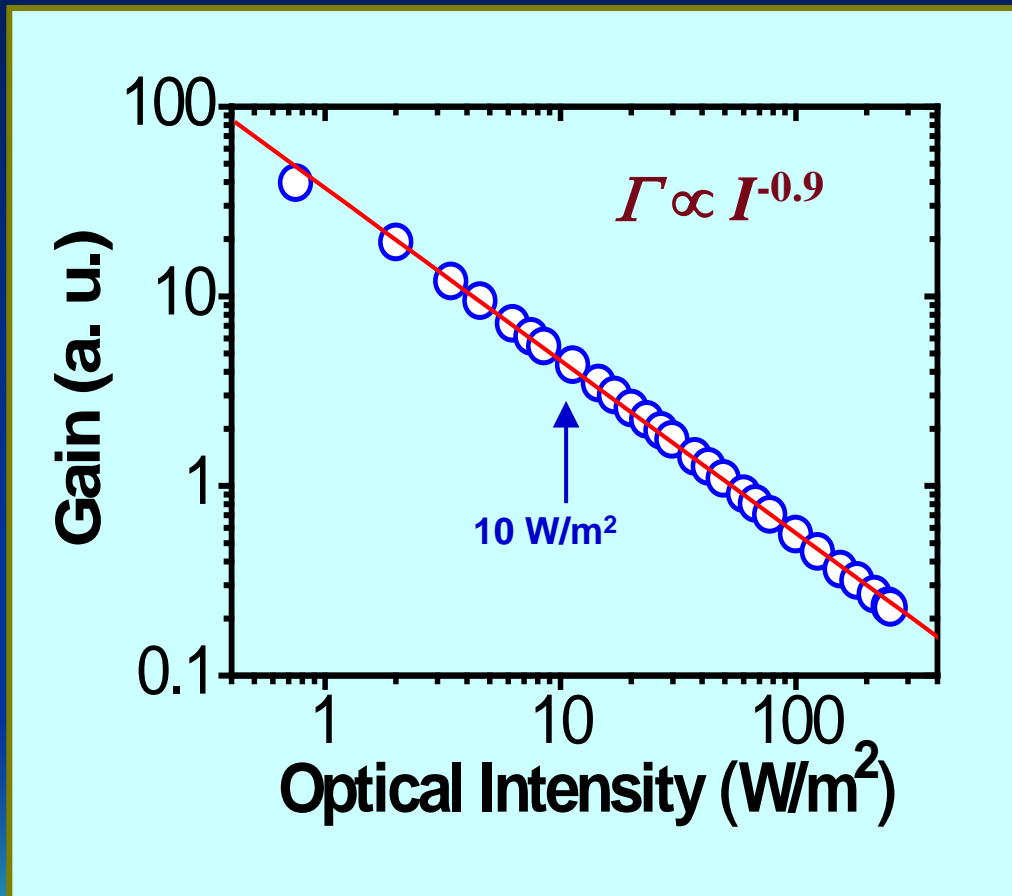
Max $R = 6.9 \text{ A/W}$ at 5V bias

What Happens to Band Structures as Nanowire Going Smaller and Smaller?

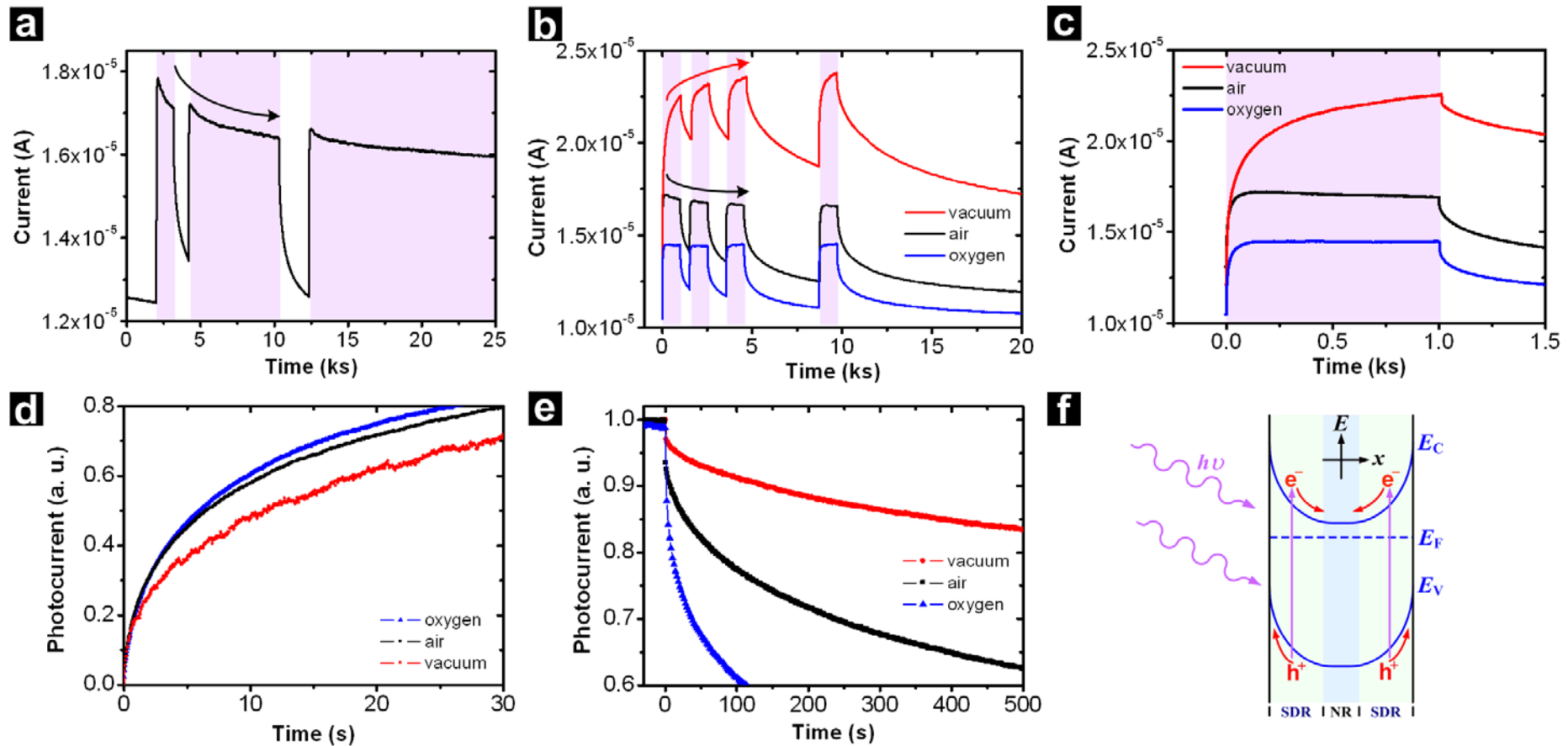


R. Calarco, *et al.*, *Nano Letters* 5 (2005) 981

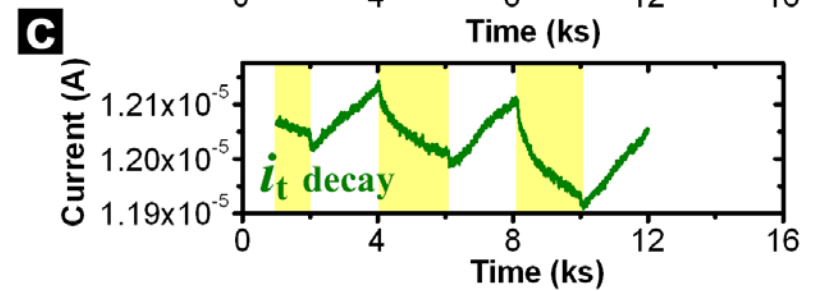
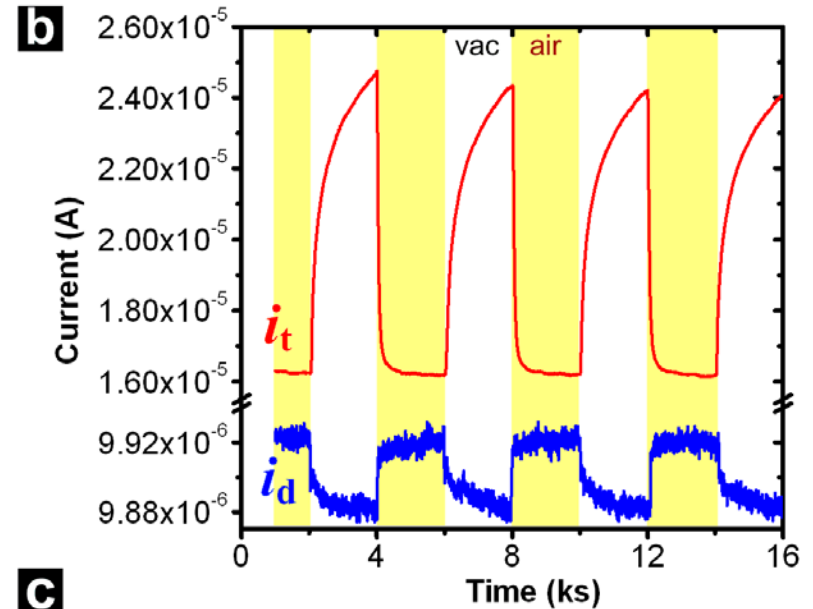
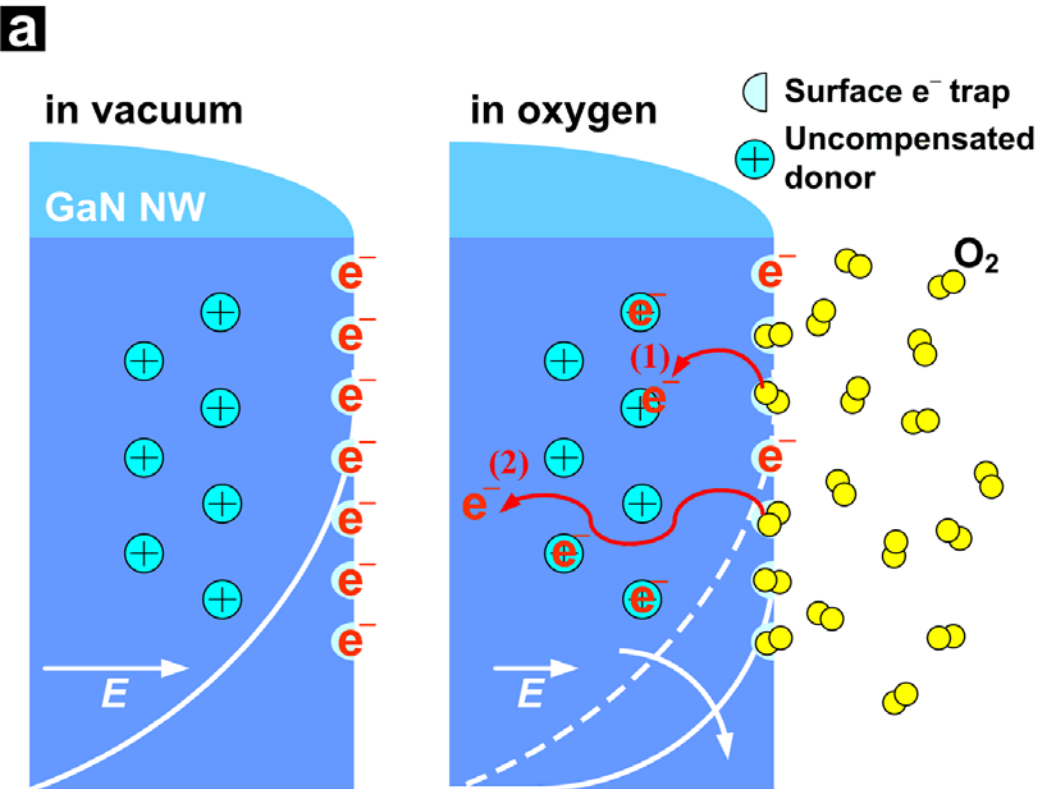
Surface-dominant Photoconductivity & Ultrahigh Gain in GaN Nanowires



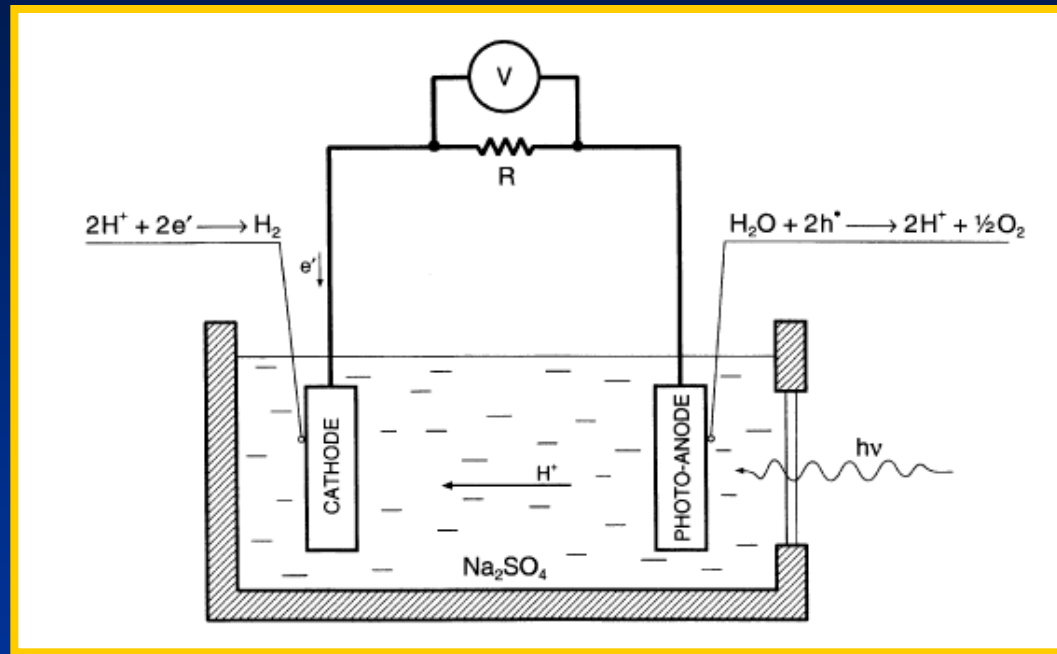
Environment-sensitive Surface Photoconductivity (under 325 nm UV Light)



Molecular Modulation at Surface

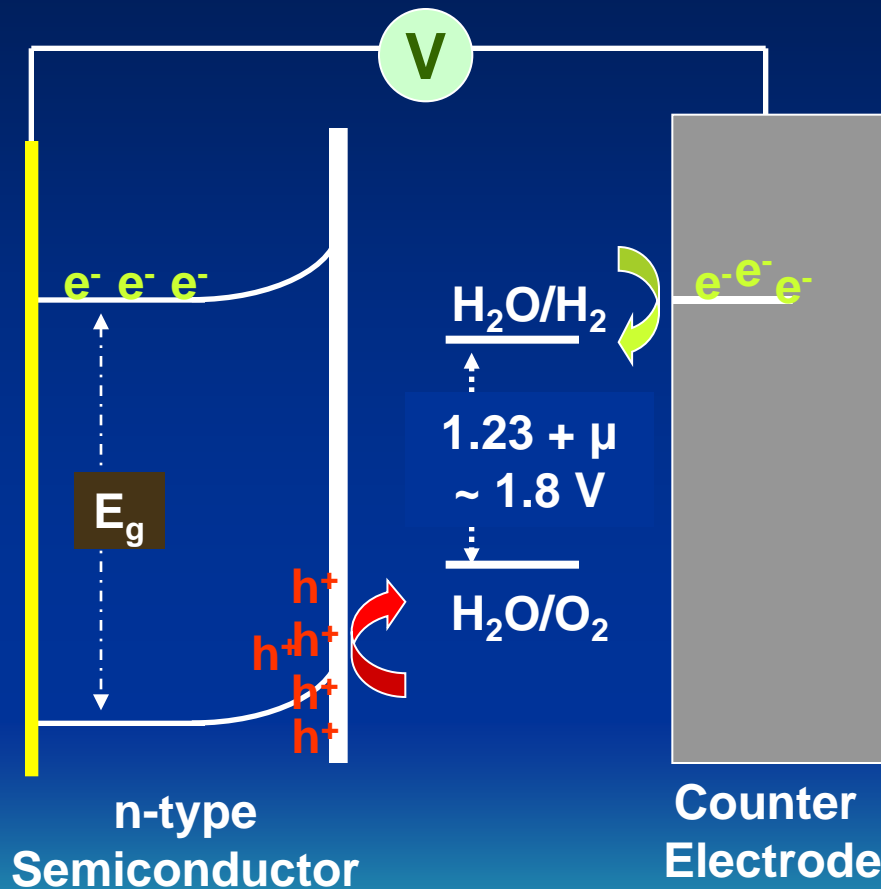


Case II: Photo-electrochemical Process



- (1) Photo-generation of e-h pairs (in photo-anode)
- (2) Charge separation and migration
(hole to anode-electrolyte interface &
electron to counter-electrode thru external circuit)
- (3) Oxidation of water to H^+ and O_2 (at anode) &
Reduction of H^+ to H_2 (at cathode)

Criteria for Effective Water Splitting

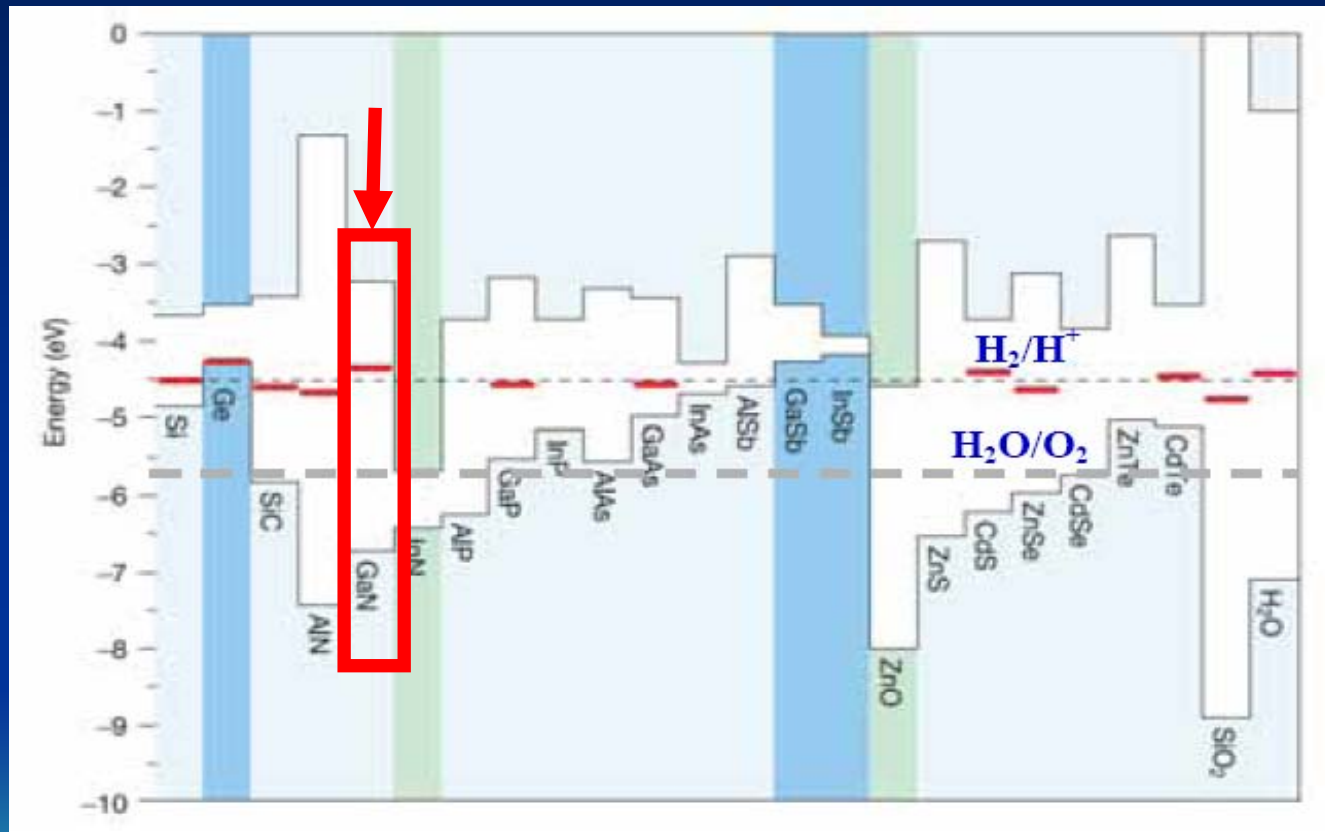


μ is overpotential

- **Photon-to-electron conversion efficiency:**
 $E_g > 1.8$ eV
- **Energetic:**
Band edge potentials to straddle the hydrogen and oxygen redox potentials
- **Material durability:**
Long-term stability in aqueous solution

All must be satisfied simultaneously!

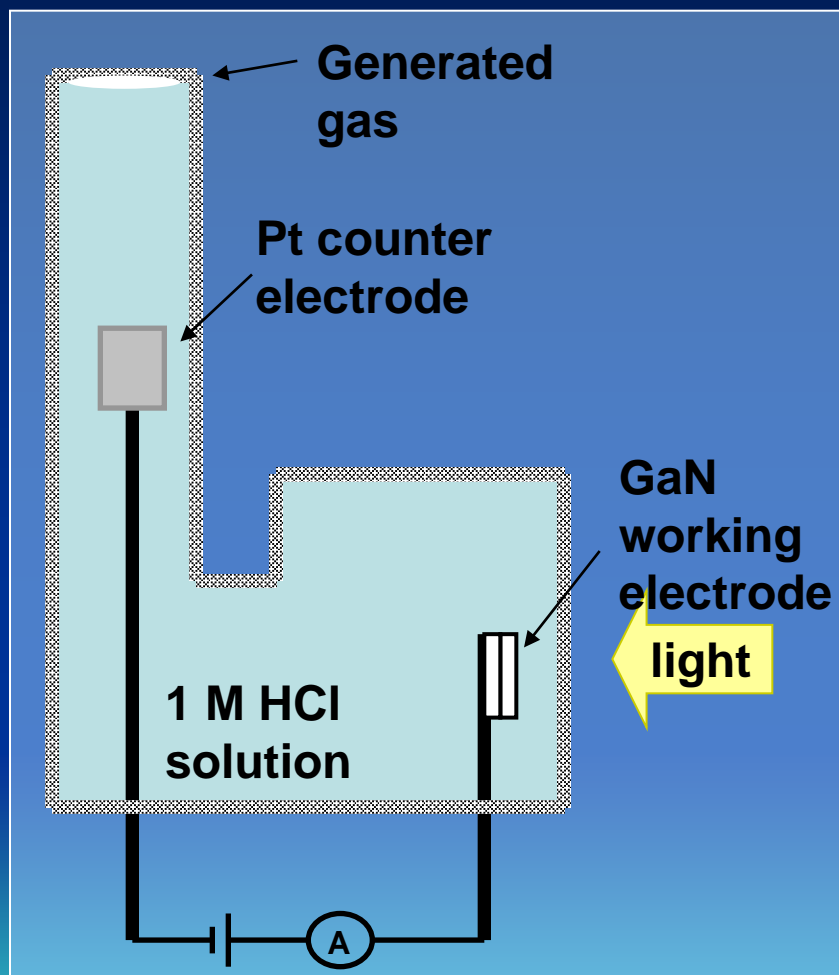
Energy Levels of Semiconductors *versus* Water Splitting



InGaN with tunable band gap

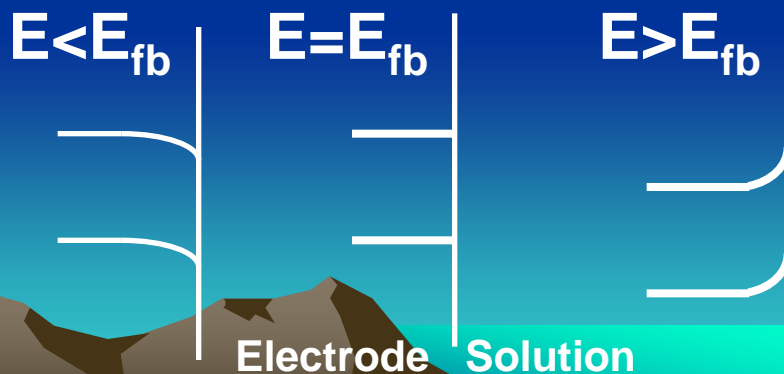
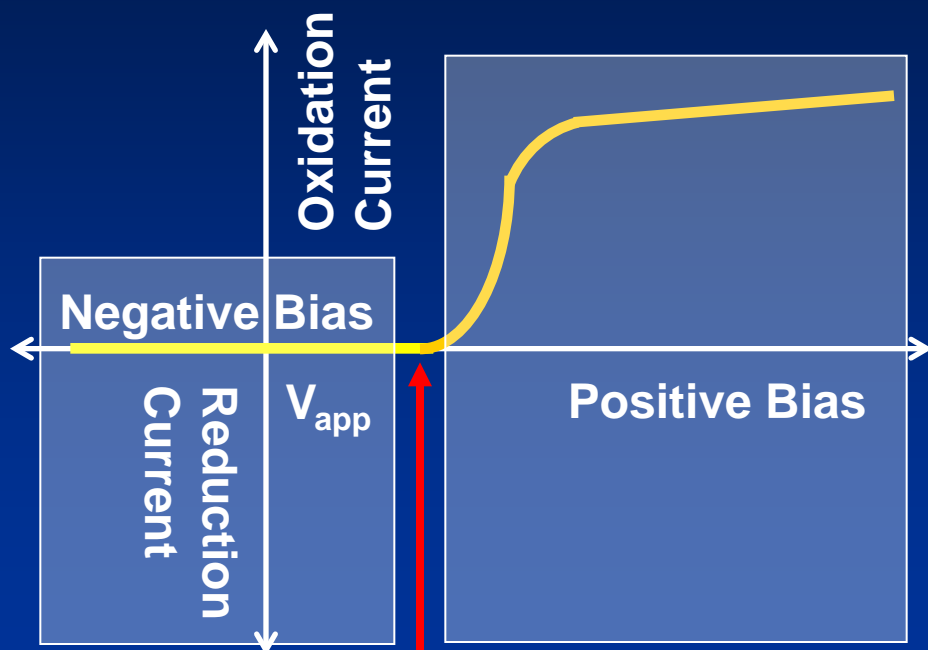
➤ Optimize light harvesting & conversion efficiency

Experimental Setup



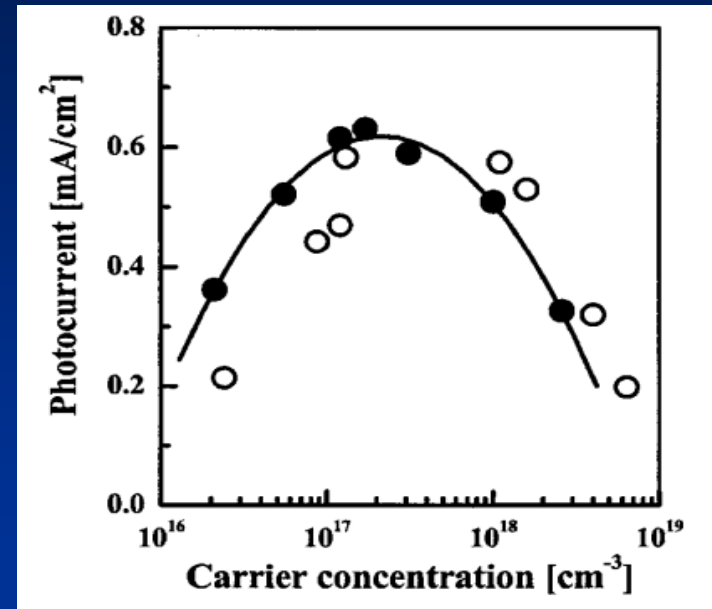
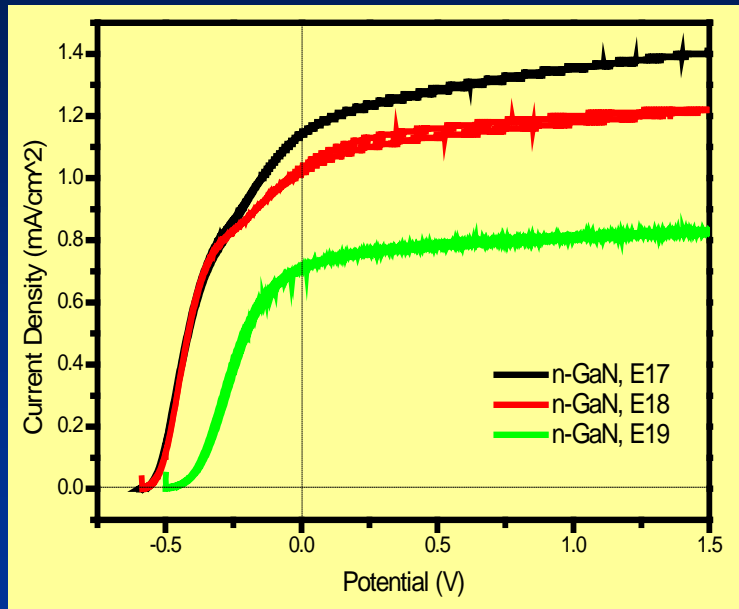
Reference electrode:
Ag/AgCl/NaCl (SSSE)

Photoresponse of N-type Photoanode



Factors Influencing Photo-electrolysis

- **Carrier Concentration**



- **Thin Film Orientation**
(Polar or semi-, non-polar)
- **Surface Treatment of Film**
- **Type of Electrolyte**
- **pH value**

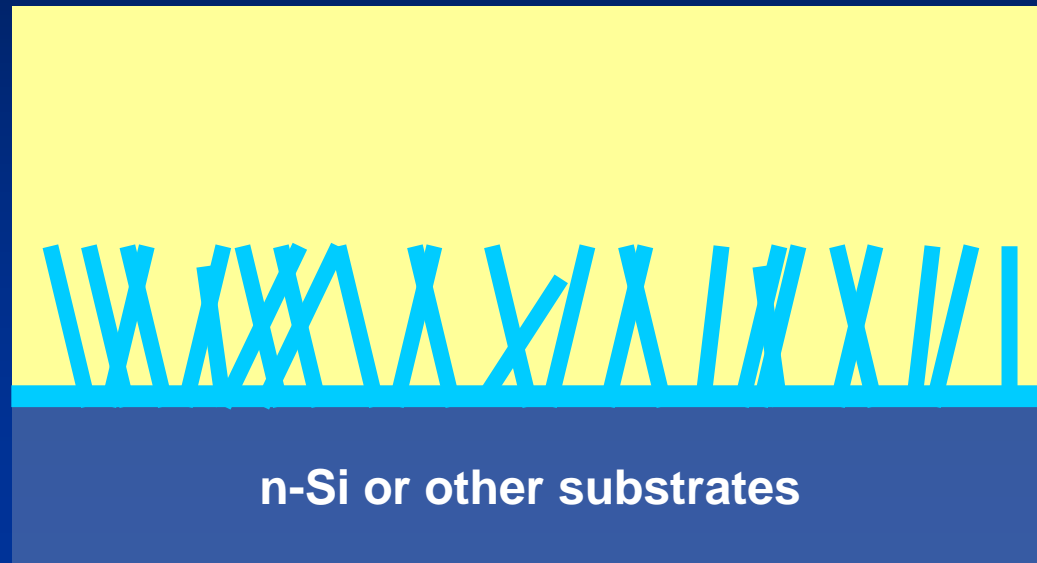
Resistivity ↑

Recombination ↑

*M. Ono, et al., (Tokyo U. Sci. & Tohoku U.)
J. Chem. Phys. 126 (2007) 054708*

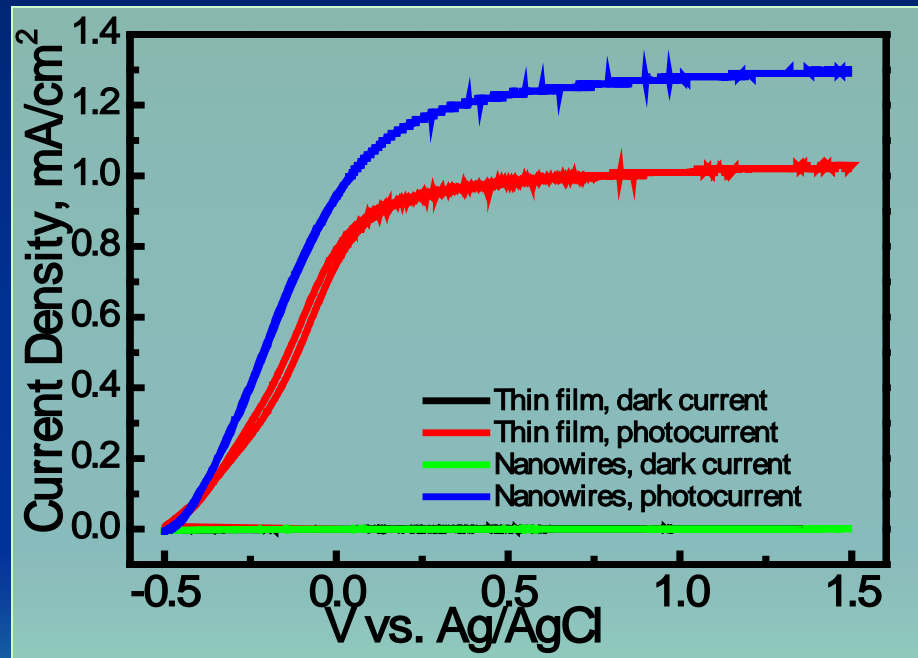
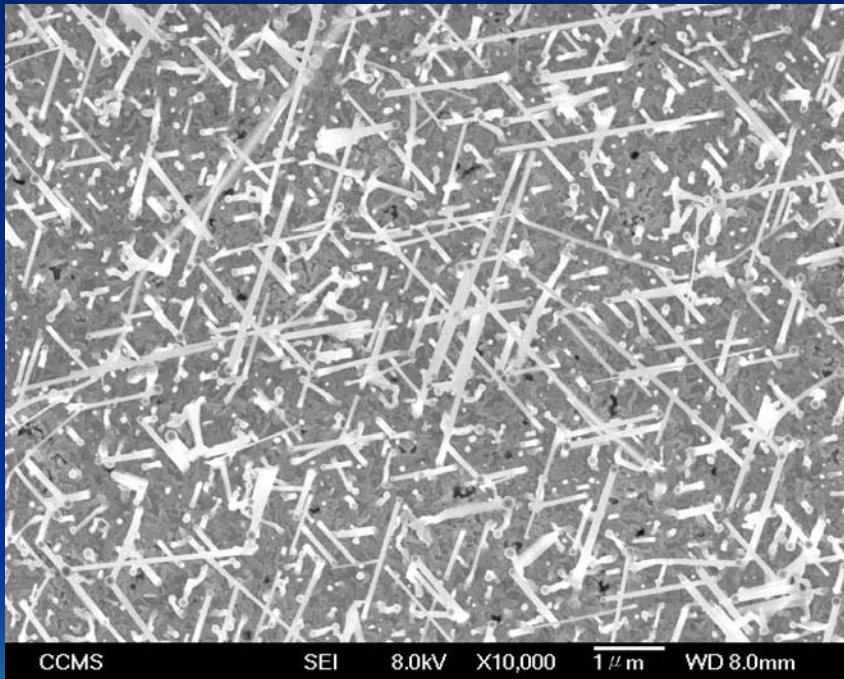
Potential of GaN and InGaN Nanowires in High-efficiency Photo-electrolysis Cells

GaN or InGaN
Nanowires



- Larger surface area
- More efficient charge separation

GaN Nanowires *versus* Thin Film



Outlook of Emerging Materials for Sustainability

Resource-Conscious R & D

Environment-Health-Safety Awareness

*from Nano for the sake of Nano
to Nano for making an impact*

- Hybrids, integrated device design
- Interface controlling/enabling
- IC-compatible, on-chip process
- Adding value to traditional/matured industry
- Next-generation electronic, optoelectronic, spintronic, energy devices operating at RT (or practical T) & lower power/cost

☆ Creativity is the only limit!